I/O INTERFACE

General Theory

As in any computer based system, the 8080 CPU must be able to communicate with devices or structures that exist outside its normal memory array. Devices like keyboards, paper tape, floppy disks, printers, displays and other control structures are used to input information into the 8080 CPU and display or store the results of the computational activity.

Probably the most important and strongest feature of the 8080 Microcomputer System is the flexibility and power of its I/O structure and the components that support it. There are many ways to structure the I/O array so that it will "fit" the total system environment to maximize efficiency and minimize component count.

The basic operation of the I/O structure can best be viewed as an array of single byte memory locations that can be Read from or Written into. The 8080 CPU has special instructions devoted to managing such transfers (IN, OUT). These instructions generally isolate memory and I/O arrays so that memory address space is not effected by the I/O structure and the general concept is that of a simple transfer to or from the Accumulator with an addressed "PORT". Another method of I/O architecture is to treat the I/O structure as part of the Memory array. This is generally referred to as "Memory Mapped I/O" and provides the designer with a powerful new "instruction set" devoted to I/O manipulation.

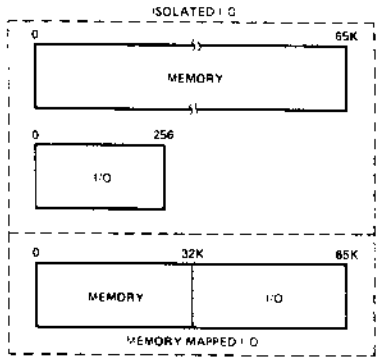


Figure 3-8. Memory/I/O Mapping.

Isolated I/O

In Figure 3-9 the system control signals, previously detailed in this chapter, are shown. This type of I/O architecture separates the memory address space from the I/O address space and uses a conceptually simple transfer to or from Accumulator technique. Such an architecture is easy to understand because I/O communicates only with the Accumulator using the IN or OUT instructions. Also because of the isolation of memory and I/O, the full address space (65K) is uneffected by I/O addressing.

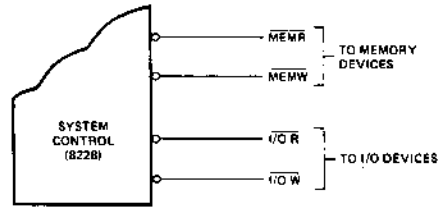


Figure 3-9. Isolated I/O.

Memory Mapped I/O

By assigning an area of memory address space as I/O a powerful architecture can be developed that can manipulate I/O using the same instructions that are used to manipulate memory locations. Thus, a "new" instruction set is created that is devoted to I/O handling.

As shown in Figure 3-10, new control signals are generated by gating the $\overline{MEMR}$ and $\overline{MEMW}$ signals with A_{15}, the most significant address bit. The new I/O control signals connect in exactly the same manner as Isolated I/O, thus the system bus characteristics are unchanged.

By assigning A_{15} as the I/O "flag", a simple method of I/O discipline is maintained:

If A_{15} is a "zero" then Memory is active.
If A_{15} is a "one" then I/O is active.

Other address bits can also be used for this function. A_{15} was chosen because it is the most significant address bit so it is easier to control with software and because it still allows memory addressing of 32K.

I/O devices are still considered addressed "ports" but instead of the Accumulator as the only transfer medium any of the internal registers can be used. All instructions that could be used to operate on memory locations can be used in I/O.

Examples:

MOVr, M	(Input Port to any Register)
MOV M, r	(Output any Register to Port)
MVI M	(Output immediate data to Port)
LDA	(Input to ACC)
STA	(Output from ACC to Port)
LHLD	(16 Bit Input)
SHLD	(16 Bit Output)
ADD M	(Add Port to ACC)
ANA M	("AND" Port with ACC)

It is easy to see that from the list of possible "new" instructions that this type of I/O architecture could have a drastic effect on increased system throughput. It is conceptually more difficult to understand than Isolated I/O and it does limit memory address space, but Memory Mapped I/O can mean a significant increase in overall speed and at the same time reducing required program memory area.

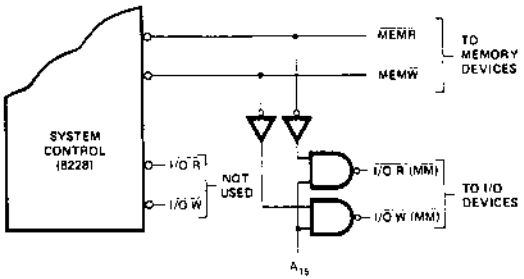


Figure 3-10. Memory Mapped I/O.

I/O Addressing

With both systems of I/O structure the addressing of each device can be configured to optimize efficiency and reduce component count. One method, the most common, is to decode the address bus into exclusive "chip selects" that enable the addressed I/O device, similar to generating chip-selects in memory arrays.

Another method is called "linear select". In this method, instead of decoding the Address Bus, a singular bit from the bus is assigned as the exclusive enable for a specific I/O device. This method, of course, limits the number of I/O devices that can be addressed but eliminates the need for extra decoders, an important consideration in small system design.

A simple example illustrates the power of such a flexible I/O structure. The first example illustrates the format of the second byte of the IN or OUT instruction using the Isolated I/O technique. The devices used are Intel®8255 Programmable Peripheral Interface units and are linear selected. Each device has three ports and from the format it can be seen that six devices can be addressed without additional decoders.

EXAMPLE #1

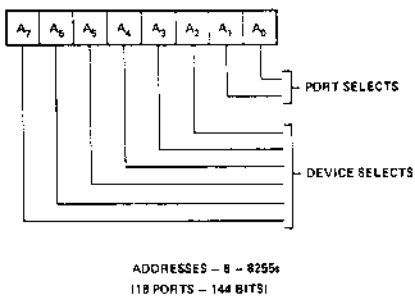


Figure 3-11. Isolated I/O – (Linear Select) (8255)

The second example uses Memory Mapped I/O and linear select to show how thirteen devices (8255) can be addressed without the use of extra decoders. The format shown could be the second and third bytes of the LDA or STA instructions or any other instructions used to manipulate I/O using the Memory Mapped technique.

It is easy to see that such a flexible I/O structure, that can be "tailored" to the overall system environment, provides the designer with a powerful tool to optimize efficiency and minimize component count.

EXAMPLE #2

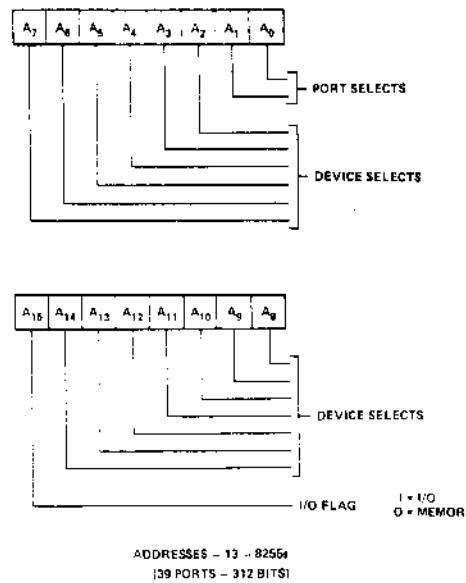


Figure 3-12. Memory Mapped I/O – (Linear Select (8255)

I/O Interface Example

In Figure 3-16 a typical I/O system is shown that uses a variety of devices (8212, 8251 and 8255). It could be used to interface the peripherals around an intelligent CRT terminals; keyboards, display, and communication interface. Another application could be in a process controller to interface sensors, relays, and motor controls. The limitation of the application area for such a circuit is solely that of the designers imagination.

The I/O structure shown interfaces to the 8080 CPU using the bus architecture developed previously in this chapter. Either Isolated or Memory Mapped techniques can be used, depending on the system I/O environment.

The 8251 provides a serial data communication interface so that the system can transmit and receive data over communication links such as telephone lines.

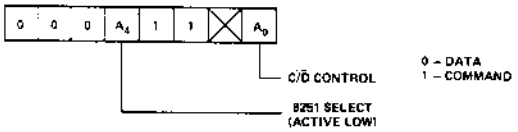


Figure 3-13. 8251 Format.

The two (2) 8255s provide twenty four bits each of programmable I/O data and control so that keyboards, sensors, paper tape, etc., can be interfaced to the system.

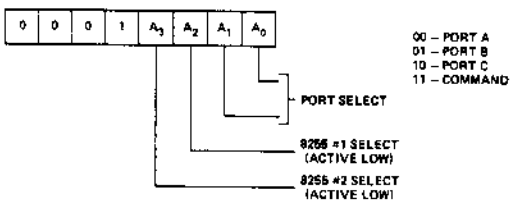


Figure 3-14. 8255 Format.

The three 8212s can be used to drive long lines or LED indicators due to their high drive capability. (15mA)

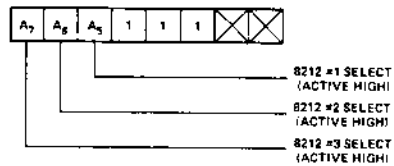


Figure 3-15. 8212 Format.

Addressing the structure is described in the formats illustrated in Figures 3-13, 3-14, 3-15. Linear Select is used so that no decoders are required thus, each device has an exclusive "enable bit".

The example shows how a powerful yet flexible I/O structure can be created using a minimum component count with devices that are all members of the 8080 Microcomputer System.

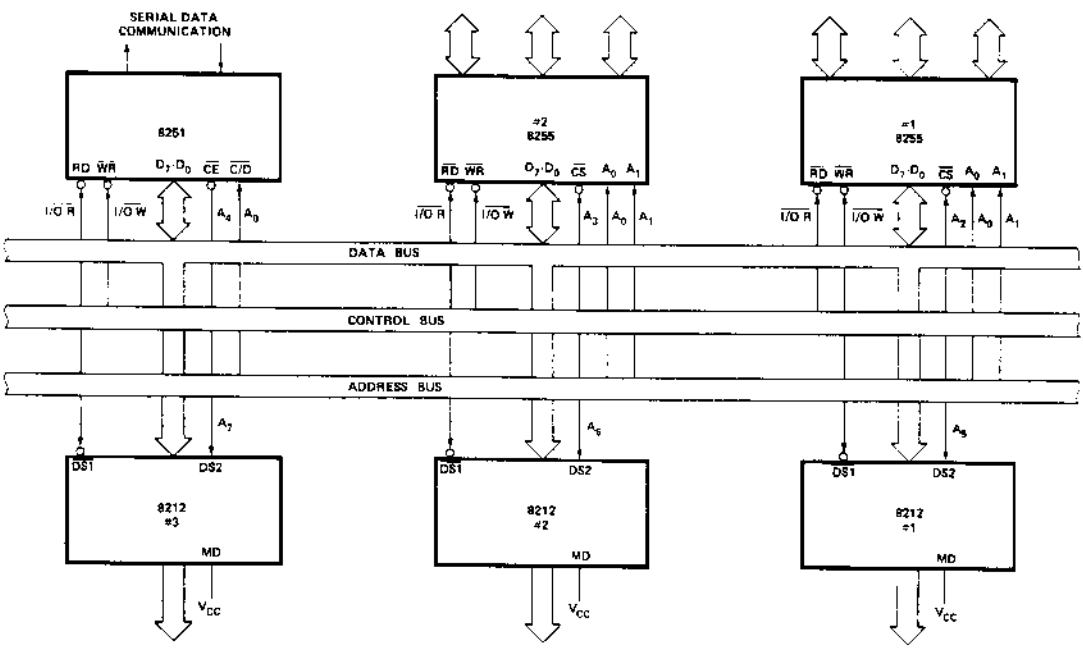


Figure 3-16. Typical I/O Interface.

CHAPTER 4
INSTRUCTION SET

A computer, no matter how sophisticated, can only do what it is "told" to do. One "tells" the computer what to do via a series of coded instructions referred to as a **Program**. The realm of the programmer is referred to as **Software**, in contrast to the **Hardware** that comprises the actual computer equipment. A computer's software refers to all of the programs that have been written for that computer.

When a computer is designed, the engineers provide the Central Processing Unit (CPU) with the ability to perform a particular set of operations. The CPU is designed such that a specific operation is performed when the CPU control logic decodes a particular instruction. Consequently, the operations that can be performed by a CPU define the computer's **Instruction Set**.

Each computer instruction allows the programmer to initiate the performance of a specific operation. All computers implement certain arithmetic operations in their instruction set, such as an instruction to add the contents of two registers. Often logical operations (e.g., OR the contents of two registers) and register operate instructions (e.g., increment a register) are included in the instruction set. A computer's instruction set will also have instructions that move data between registers, between a register and memory, and between a register and an I/O device. Most instruction sets also provide **Conditional Instructions**. A conditional instruction specifies an operation to be performed only if certain conditions have been met; for example, jump to a particular instruction if the result of the last operation was zero. Conditional instructions provide a program with a decision-making capability.

By logically organizing a sequence of instructions into a coherent program, the programmer can "tell" the computer to perform a very specific and useful function.

The computer, however, can only execute programs whose instructions are in a binary coded form (i.e., a series of 1's and 0's), that is called **Machine Code**. Because it would be extremely cumbersome to program in machine code, programming languages have been developed. There are programs available which convert the programming language instructions into machine code that can be interpreted by the processor.

One type of programming language is **Assembly Language**. A unique assembly language mnemonic is assigned to each of the computer's instructions. The programmer can write a program (called the **Source Program**) using these mnemonics and certain operands; the source program is then converted into machine instructions (called the **Object Code**). Each assembly language instruction is converted into one machine code instruction (1 or more bytes) by an **Assembler** program. Assembly languages are usually machine dependent (i.e., they are usually able to run on only one type of computer).

THE 8080 INSTRUCTION SET

The 8080 instruction set includes five different types of instructions:

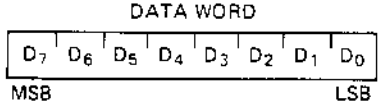
- **Data Transfer Group**—move data between registers or between memory and registers
- **Arithmetic Group** — add, subtract, increment or decrement data in registers or in memory
- **Logical Group** — AND, OR, EXCLUSIVE-OR, compare, rotate or complement data in registers or in memory
- **Branch Group** — conditional and unconditional jump instructions, subroutine call instructions and return instructions
- **Stack, I/O and Machine Control Group** — includes I/O instructions, as well as instructions for maintaining the stack and internal control flags.

Instruction and Data Formats:

Memory for the 8080 is organized into 8-bit quantities, called Bytes. Each byte has a unique 16-bit binary address corresponding to its sequential position in memory.

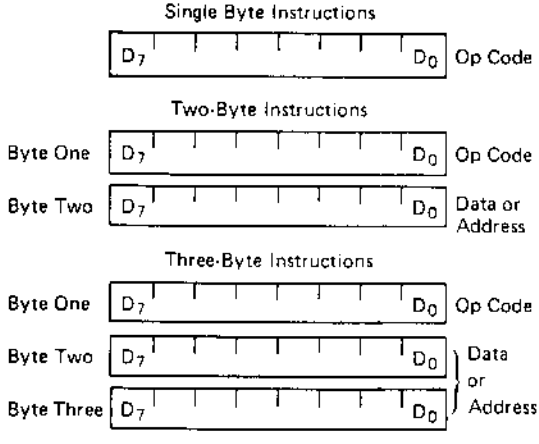
The 8080 can directly address up to 65,536 bytes of memory, which may consist of both read-only memory (ROM) elements and random-access memory (RAM) elements (read/write memory).

Data in the 8080 is stored in the form of 8-bit binary integers:



When a register or data word contains a binary number, it is necessary to establish the order in which the bits of the number are written. In the Intel 8080, BIT 0 is referred to as the **Least Significant Bit (LSB)**, and BIT 7 (of an 8 bit number) is referred to as the **Most Significant Bit (MSB)**.

The 8080 program instructions may be one, two or three bytes in length. Multiple byte instructions must be stored in successive memory locations; the address of the first byte is always used as the address of the instructions. The exact instruction format will depend on the particular operation to be executed.



Addressing Modes:

Often the data that is to be operated on is stored in memory. When multi-byte numeric data is used, the data, like instructions, is stored in successive memory locations, with the least significant byte first, followed by increasingly significant bytes. The 8080 has four different modes for addressing data stored in memory or in registers:

- Direct – Bytes 2 and 3 of the instruction contain the exact memory address of the data item (the low-order bits of the address are in byte 2, the high-order bits in byte 3).
- Register – The instruction specifies the register or register-pair in which the data is located.
- Register Indirect – The instruction specifies a register-pair which contains the memory address where the data is located (the high-order bits of the address are in the first register of the pair, the low-order bits in the second).
- Immediate – The instruction contains the data itself. This is either an 8-bit quantity or a 16-bit quantity (least significant byte first, most significant byte second).

Unless directed by an interrupt or branch instruction, the execution of instructions proceeds through consecutively increasing memory locations. A branch instruction can specify the address of the next instruction to be executed in one of two ways:

- Direct – The branch instruction contains the address of the next instruction to be executed. (Except for the 'RST' instruction, byte 2 contains the low-order address and byte 3 the high-order address.)
- Register Indirect – The branch instruction indicates a register-pair which contains the address of the next instruction to be executed. (The high-order bits of the address are in the first register of the pair, the low-order bits in the second.)

The RST instruction is a special one-byte call instruction (usually used during interrupt sequences). RST includes a three-bit field; program control is transferred to the instruction whose address is eight times the contents of this three-bit field.

Condition Flags:

There are five condition flags associated with the execution of instructions on the 8080. They are Zero, Sign, Parity, Carry, and Auxiliary Carry, and are each represented by a 1-bit register in the CPU. A flag is "set" by forcing the bit to 1; "reset" by forcing the bit to 0.

Unless indicated otherwise, when an instruction affects a flag, it affects it in the following manner:

Zero: If the result of an instruction has the value 0, this flag is set; otherwise it is reset.

Sign: If the most significant bit of the result of the operation has the value 1, this flag is set; otherwise it is reset.

Parity: If the modulo 2 sum of the bits of the result of the operation is 0, (i.e., if the result has even parity), this flag is set; otherwise it is reset (i.e., if the result has odd parity).

Carry: If the instruction resulted in a carry (from addition), or a borrow (from subtraction or a comparison) out of the high-order bit, this flag is set; otherwise it is reset.

Auxiliary Carry: If the instruction caused a carry out of bit 3 and into bit 4 of the resulting value, the auxiliary carry is set; otherwise it is reset. This flag is affected by single precision additions, subtractions, increments, decrements, comparisons, and logical operations, but is principally used with additions and increments preceding a DAA (Decimal Adjust Accumulator) instruction.

Symbols and Abbreviations:

The following symbols and abbreviations are used in the subsequent description of the 8080 instructions:

SYMBOLS	MEANING
accumulator	Register A
addr	16-bit address quantity
data	8-bit data quantity
data 16	16-bit data quantity
byte 2	The second byte of the instruction
byte 3	The third byte of the instruction
port	8-bit address of an I/O device
r,r1,r2	One of the registers A,B,C,D,E,H,L
DDD,SSS	The bit pattern designating one of the registers A,B,C,D,E,H,L (DDD=destination, SSS=source):

DDD or SSS	REGISTER NAME
111	A
000	B
001	C
010	D
011	E
100	H
101	L

rp	One of the register pairs: B represents the B,C pair with B as the high-order register and C as the low-order register; D represents the D,E pair with D as the high-order register and E as the low-order register; H represents the H,L pair with H as the high-order register and L as the low-order register; SP represents the 16-bit stack pointer register.
RP	The bit pattern designating one of the register pairs B,D,H,SP:

RP	REGISTER PAIR
00	B-C
01	D-E
10	H-L
11	SP

rh	The first (high-order) register of a designated register pair.
rl	The second (low-order) register of a designated register pair.
PC	16-bit program counter register (PCH and PCL are used to refer to the high-order and low-order 8 bits respectively).
SP	16-bit stack pointer register (SPH and SPL are used to refer to the high-order and low-order 8 bits respectively).
r_m	Bit m of the register r (bits are number 7 through 0 from left to right).
Z,S,P,CY,AC	The condition flags: Zero, Sign, Parity, Carry, and Auxiliary Carry, respectively.
( )	The contents of the memory location or registers enclosed in the parentheses.
←	"Is transferred to"
∧	Logical AND
∀	Exclusive OR
∨	Inclusive OR
+	Addition
−	Two's complement subtraction
*	Multiplication
↔	"Is exchanged with"
—	The one's complement (e.g., $(\overline{A})$)
n	The restart number 0 through 7
NNN	The binary representation 000 through 111 for restart number 0 through 7 respectively.

Description Format:

The following pages provide a detailed description of the instruction set of the 8080. Each instruction is described in the following manner:

1. The MAC 80 assembler format, consisting of the instruction mnemonic and operand fields, is printed in **BOLDFACE** on the left side of the first line.
2. The name of the instruction is enclosed in parenthesis on the right side of the first line.
3. The next line(s) contain a symbolic description of the operation of the instruction.
4. This is followed by a narative description of the operation of the instruction.
5. The following line(s) contain the binary fields and patterns that comprise the machine instruction.

6. The last four lines contain incidental information about the execution of the instruction. The number of machine cycles and states required to execute the instruction are listed first. If the instruction has two possible execution times, as in a Conditional Jump, both times will be listed, separated by a slash. Next, any significant data addressing modes (see Page 4-2) are listed. The last line lists any of the five Flags that are affected by the execution of the instruction.

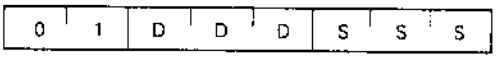
Data Transfer Group:

This group of instructions transfers data to and from registers and memory. **Condition flags are not affected** by any instruction in this group.

MOV r1, r2 (Move Register)

(r1) ← (r2)

The content of register r2 is moved to register r1.

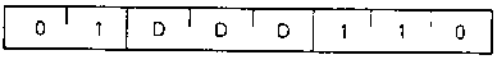


Cycles: 1
States: 5
Addressing: register
Flags: none

MOV r, M (Move from memory)

(r) ← ((H) (L))

The content of the memory location, whose address is in registers H and L, is moved to register r.

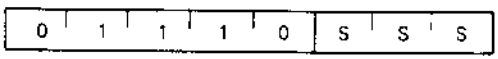


Cycles: 2
States: 7
Addressing: reg. indirect
Flags: none

MOV M, r (Move to memory)

((H) (L)) ← (r)

The content of register r is moved to the memory location whose address is in registers H and L.

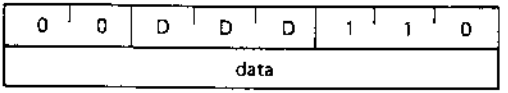


Cycles: 2
States: 7
Addressing: reg. indirect
Flags: none

MVI r, data (Move Immediate)

(r) ← (byte 2)

The content of byte 2 of the instruction is moved to register r.

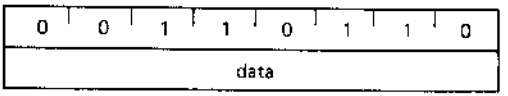


Cycles: 2
States: 7
Addressing: immediate
Flags: none

MVI M, data (Move to memory immediate)

((H) (L)) ← (byte 2)

The content of byte 2 of the instruction is moved to the memory location whose address is in registers H and L.



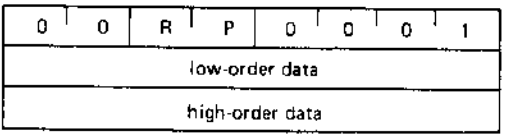
Cycles: 3
States: 10
Addressing: immed./reg. indirect
Flags: none

LXI rp, data 16 (Load register pair immediate)

(rh) ← (byte 3),

(rl) ← (byte 2)

Byte 3 of the instruction is moved into the high-order register (rh) of the register pair rp. Byte 2 of the instruction is moved into the low-order register (rl) of the register pair rp.

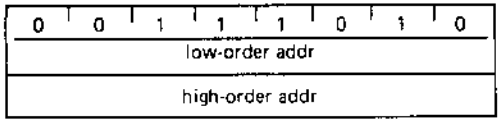


Cycles: 3
States: 10
Addressing: immediate
Flags: none

LDA addr (Load Accumulator direct)

(A) ← ((byte 3)(byte 2))

The content of the memory location, whose address is specified in byte 2 and byte 3 of the instruction, is moved to register A.

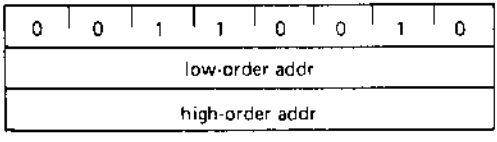


Cycles: 4
States: 13
Addressing: direct
Flags: none

STA addr (Store Accumulator direct)

((byte 3)(byte 2)) ← (A)

The content of the accumulator is moved to the memory location whose address is specified in byte 2 and byte 3 of the instruction.



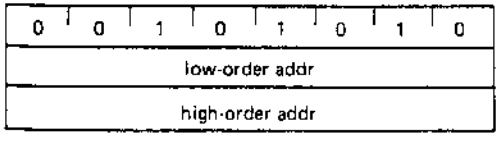
Cycles: 4
States: 13
Addressing: direct
Flags: none

LHLD addr (Load H and L direct)

(L) ← ((byte 3)(byte 2))

(H) ← ((byte 3)(byte 2) + 1)

The content of the memory location, whose address is specified in byte 2 and byte 3 of the instruction, is moved to register L. The content of the memory location at the succeeding address is moved to register H.



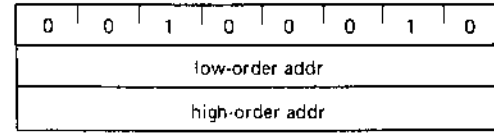
Cycles: 5
States: 16
Addressing: direct
Flags: none

SHLD addr (Store H and L direct)

((byte 3)(byte 2)) ← (L)

((byte 3)(byte 2) + 1) ← (H)

The content of register L is moved to the memory location whose address is specified in byte 2 and byte 3. The content of register H is moved to the succeeding memory location.

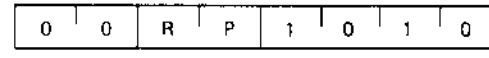


Cycles: 5
States: 16
Addressing: direct
Flags: none

LDAX rp (Load accumulator indirect)

(A) ← ((rp))

The content of the memory location, whose address is in the register pair rp, is moved to register A. Note: only register pairs rp=B (registers B and C) or rp=D (registers D and E) may be specified.

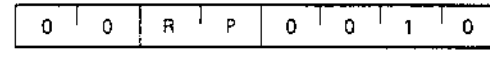


Cycles: 2
States: 7
Addressing: reg. indirect
Flags: none

STAX rp (Store accumulator indirect)

((rp)) ← (A)

The content of register A is moved to the memory location whose address is in the register pair rp. Note: only register pairs rp=B (registers B and C) or rp=D (registers D and E) may be specified.



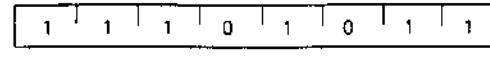
Cycles: 2
States: 7
Addressing: reg. indirect
Flags: none

XCHG (Exchange H and L with D and E)

(H) ⟷ (D)

(L) ⟷ (E)

The contents of registers H and L are exchanged with the contents of registers D and E.



Cycles: 1
States: 4
Addressing: register
Flags: none

Arithmetic Group:

This group of instructions performs arithmetic operations on data in registers and memory.

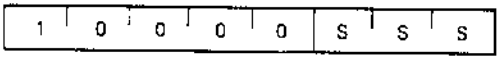
Unless indicated otherwise, all instructions in this group affect the Zero, Sign, Parity, Carry, and Auxiliary Carry flags according to the standard rules.

All subtraction operations are performed via two's complement arithmetic and set the carry flag to one to indicate a borrow and clear it to indicate no borrow.

ADD r (Add Register)

(A) ← (A) + (r)

The content of register r is added to the content of the accumulator. The result is placed in the accumulator.

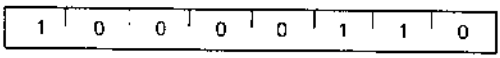


Cycles: 1
States: 4
Addressing: register
Flags: Z,S,P,CY,AC

ADD M (Add memory)

(A) ← (A) + ((H) (L))

The content of the memory location whose address is contained in the H and L registers is added to the content of the accumulator. The result is placed in the accumulator.

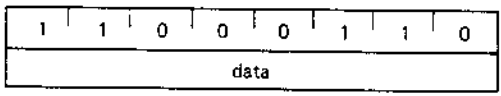


Cycles: 2
States: 7
Addressing: reg. indirect
Flags: Z,S,P,CY,AC

ADI data (Add immediate)

(A) ← (A) + (byte 2)

The content of the second byte of the instruction is added to the content of the accumulator. The result is placed in the accumulator.

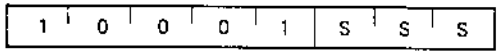


Cycles: 2
States: 7
Addressing: immediate
Flags: Z,S,P,CY,AC

ADC r (Add Register with carry)

(A) ← (A) + (r) + (CY)

The content of register r and the content of the carry bit are added to the content of the accumulator. The result is placed in the accumulator.

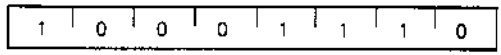


Cycles: 1
States: 4
Addressing: register
Flags: Z,S,P,CY,AC

ADC M (Add memory with carry)

(A) ← (A) + ((H) (L)) + (CY)

The content of the memory location whose address is contained in the H and L registers and the content of the CY flag are added to the accumulator. The result is placed in the accumulator.

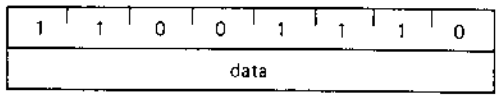


Cycles: 2
States: 7
Addressing: reg. indirect
Flags: Z,S,P,CY,AC

ACI data (Add immediate with carry)

(A) ← (A) + (byte 2) + (CY)

The content of the second byte of the instruction and the content of the CY flag are added to the contents of the accumulator. The result is placed in the accumulator.

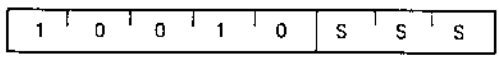


Cycles: 2
States: 7
Addressing: immediate
Flags: Z,S,P,CY,AC

SUB r (Subtract Register)

(A) ← (A) – (r)

The content of register r is subtracted from the content of the accumulator. The result is placed in the accumulator.

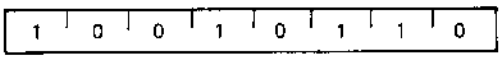


Cycles: 1
States: 4
Addressing: register
Flags: Z,S,P,CY,AC

SUB M (Subtract memory)

(A) ← (A) – ((H) (L))

The content of the memory location whose address is contained in the H and L registers is subtracted from the content of the accumulator. The result is placed in the accumulator.

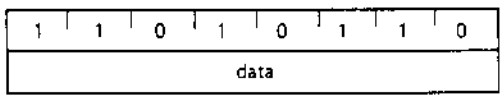


Cycles: 2
States: 7
Addressing: reg. indirect
Flags: Z,S,P,CY,AC

SUI data (Subtract immediate)

(A) ← (A) – (byte 2)

The content of the second byte of the instruction is subtracted from the content of the accumulator. The result is placed in the accumulator.

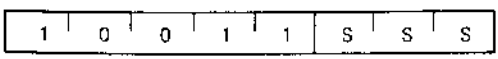


Cycles: 2
States: 7
Addressing: immediate
Flags: Z,S,P,CY,AC

SBB r (Subtract Register with borrow)

(A) ← (A) – (r) – (CY)

The content of register r and the content of the CY flag are both subtracted from the accumulator. The result is placed in the accumulator.

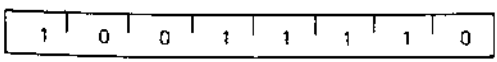


Cycles: 1
States: 4
Addressing: register
Flags: Z,S,P,CY,AC

SBB M (Subtract memory with borrow)

(A) ← (A) – ((H) (L)) – (CY)

The content of the memory location whose address is contained in the H and L registers and the content of the CY flag are both subtracted from the accumulator. The result is placed in the accumulator.

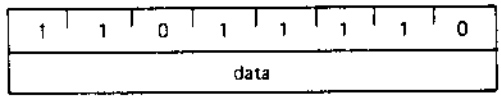


Cycles: 2
States: 7
Addressing: reg. indirect
Flags: Z,S,P,CY,AC

SBI data (Subtract immediate with borrow)

(A) ← (A) – (byte 2) – (CY)

The contents of the second byte of the instruction and the contents of the CY flag are both subtracted from the accumulator. The result is placed in the accumulator.

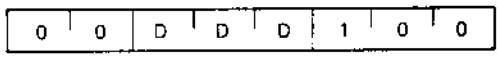


Cycles: 2
States: 7
Addressing: immediate
Flags: Z,S,P,CY,AC

INR r (Increment Register)

(r) ← (r) + 1

The content of register r is incremented by one. Note: All condition flags **except CY** are affected.

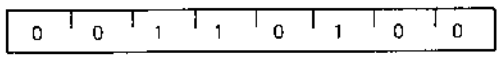


Cycles: 1
States: 5
Addressing: register
Flags: Z,S,P,AC

INR M (Increment memory)

((H) (L)) ← ((H) (L)) + 1

The content of the memory location whose address is contained in the H and L registers is incremented by one. Note: All condition flags **except CY** are affected.

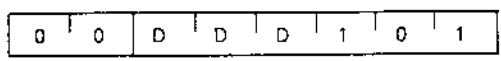


Cycles: 3
States: 10
Addressing: reg. indirect
Flags: Z,S,P,AC

DCR r (Decrement Register)

(r) ← (r) – 1

The content of register r is decremented by one. Note: All condition flags **except CY** are affected.

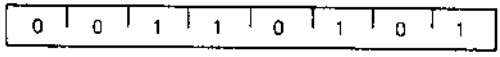


Cycles: 1
States: 5
Addressing: register
Flags: Z,S,P,AC

DCR M (Decrement memory)

((H) (L)) ← ((H) (L)) − 1

The content of the memory location whose address is contained in the H and L registers is decremented by one. Note: All condition flags **except CY** are affected.

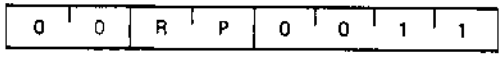


Cycles: 3
States: 10
Addressing: reg. indirect
Flags: Z,S,P,AC

INX rp (Increment register pair)

(rh) (rl) ← (rh) (rl) + 1

The content of the register pair rp is incremented by one. Note: **No condition flags are affected.**

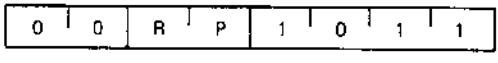


Cycles: 1
States: 5
Addressing: register
Flags: none

DCX rp (Decrement register pair)

(rh) (rl) ← (rh) (rl) − 1

The content of the register pair rp is decremented by one. Note: **No condition flags are affected.**

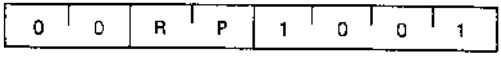


Cycles: 1
States: 5
Addressing: register
Flags: none

DAD rp (Add register pair to H and L)

(H) (L) ← (H) (L) + (rh) (rl)

The content of the register pair rp is added to the content of the register pair H and L. The result is placed in the register pair H and L. Note: **Only the CY flag is affected.** It is set if there is a carry out of the double precision add; otherwise it is reset.



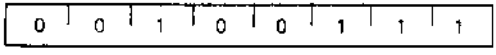
Cycles: 3
States: 10
Addressing: register
Flags: CY

DAA (Decimal Adjust Accumulator)

The eight-bit number in the accumulator is adjusted to form two four-bit Binary-Coded-Decimal digits by the following process:

1. If the value of the least significant 4 bits of the accumulator is greater than 9 **or** if the AC flag is set, 6 is added to the accumulator.
2. If the value of the most significant 4 bits of the accumulator is now greater than 9, or if the CY flag is set, 6 is added to the most significant 4 bits of the accumulator.

NOTE: All flags are affected.



Cycles: 1
States: 4
Flags: Z,S,P,CY,AC

Logical Group:

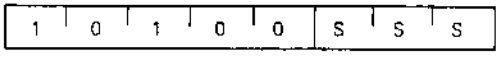
This group of instructions performs logical (Boolean) operations on data in registers and memory and on condition flags.

Unless indicated otherwise, all instructions in this group affect the Zero, Sign, Parity, Auxiliary Carry, and Carry flags according to the standard rules.

ANA r (AND Register)

(A) ← (A) ∧ (r)

The content of register r is logically anded with the content of the accumulator. The result is placed in the accumulator. **The CY flag is cleared.**

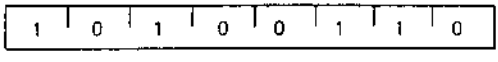


Cycles: 1
States: 4
Addressing: register
Flags: Z,S,P,CY,AC

ANA M (AND memory)

(A) ← (A) ∧ ((H) (L))

The contents of the memory location whose address is contained in the H and L registers is logically anded with the content of the accumulator. The result is placed in the accumulator. **The CY flag is cleared.**

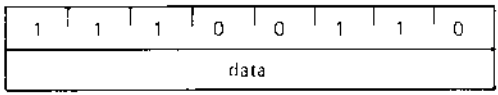


Cycles: 2
States: 7
Addressing: reg. indirect
Flags: Z,S,P,CY,AC

ANI data (AND immediate)

(A) ← (A) ∧ (byte 2)

The content of the second byte of the instruction is logically anded with the contents of the accumulator. The result is placed in the accumulator. **The CY and AC flags are cleared.**

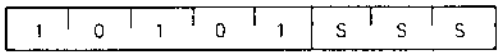


Cycles: 2
States: 7
Addressing: immediate
Flags: Z,S,P,CY,AC

XRA r (Exclusive OR Register)

(A) ← (A) ∀ (r)

The content of register r is exclusive-or'd with the content of the accumulator. The result is placed in the accumulator. **The CY and AC flags are cleared.**

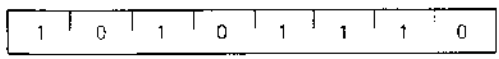


Cycles: 1
States: 4
Addressing: register
Flags: Z,S,P,CY,AC

XRA M (Exclusive OR Memory)

(A) ← (A) ∀ ((H) (L))

The content of the memory location whose address is contained in the H and L registers is exclusive-OR'd with the content of the accumulator. The result is placed in the accumulator. **The CY and AC flags are cleared.**

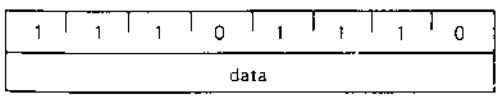


Cycles: 2
States: 7
Addressing: reg. indirect
Flags: Z,S,P,CY,AC

XRI data (Exclusive OR immediate)

(A) ← (A) ∀ (byte 2)

The content of the second byte of the instruction is exclusive-OR'd with the content of the accumulator. The result is placed in the accumulator. **The CY and AC flags are cleared.**

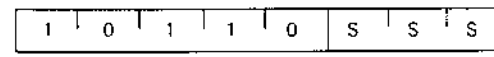


Cycles: 2
States: 7
Addressing: immediate
Flags: Z,S,P,CY,AC

ORA r (OR Register)

(A) ← (A) ∨ (r)

The content of register r is inclusive-OR'd with the content of the accumulator. The result is placed in the accumulator. **The CY and AC flags are cleared.**

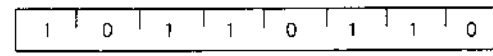


Cycles: 1
States: 4
Addressing: register
Flags: Z,S,P,CY,AC

ORA M (OR memory)

(A) ← (A) ∨ ((H) (L))

The content of the memory location whose address is contained in the H and L registers is inclusive-OR'd with the content of the accumulator. The result is placed in the accumulator. **The CY and AC flags are cleared.**



Cycles: 2
States: 7
Addressing: reg. indirect
Flags: Z,S,P,CY,AC

ORI data (OR Immediate)

(A) ← (A) ∨ (byte 2)

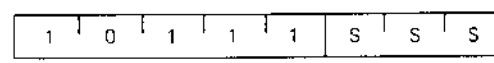
The content of the second byte of the instruction is inclusive-OR'd with the content of the accumulator. The result is placed in the accumulator. **The CY and AC flags are cleared.**

Cycles: 2
States: 7
Addressing: immediate
Flags: Z,S,P,CY,AC

CMP r (Compare Register)

(A) − (r)

The content of register r is subtracted from the accumulator. The accumulator remains unchanged. The condition flags are set as a result of the subtraction. **The Z flag is set to 1 if (A) = (r). The CY flag is set to 1 if (A) < (r).**

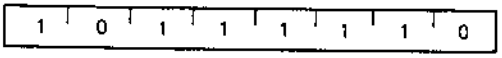


Cycles: 1
States: 4
Addressing: register
Flags: Z,S,P,CY,AC

CMP M (Compare memory)

(A) – ((H) (L))

The content of the memory location whose address is contained in the H and L registers is subtracted from the accumulator. The accumulator remains unchanged. The condition flags are set as a result of the subtraction. The Z flag is set to 1 if (A) = ((H) (L)). The CY flag is set to 1 if (A) < ((H) (L)).

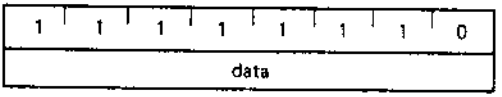


Cycles: 2
States: 7
Addressing: reg. indirect
Flags: Z,S,P,CY,AC

CPI data (Compare immediate)

(A) – (byte 2)

The content of the second byte of the instruction is subtracted from the accumulator. The condition flags are set by the result of the subtraction. The Z flag is set to 1 if (A) = (byte 2). The CY flag is set to 1 if (A) < (byte 2).



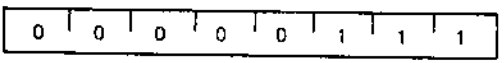
Cycles: 2
States: 7
Addressing: immediate
Flags: Z,S,P,CY,AC

RLC (Rotate left)

$(A_{n+1}) \leftarrow (A_n)$; $(A_0) \leftarrow (A_7)$

$(CY) \leftarrow (A_7)$

The content of the accumulator is rotated left one position. The low order bit and the CY flag are both set to the value shifted out of the high order bit position. **Only the CY flag is affected.**



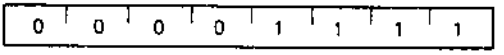
Cycles: 1
States: 4
Flags: CY

RRC (Rotate right)

$(A_n) \leftarrow (A_{n-1})$; $(A_7) \leftarrow (A_0)$

$(CY) \leftarrow (A_0)$

The content of the accumulator is rotated right one position. The high order bit and the CY flag are both set to the value shifted out of the low order bit position. **Only the CY flag is affected.**



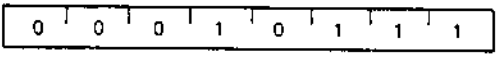
Cycles: 1
States: 4
Flags: CY

RAL (Rotate left through carry)

$(A_{n+1}) \leftarrow (A_n)$; $(CY) \leftarrow (A_7)$

$(A_0) \leftarrow (CY)$

The content of the accumulator is rotated left one position through the CY flag. The low order bit is set equal to the CY flag and the CY flag is set to the value shifted out of the high order bit. **Only the CY flag is affected.**



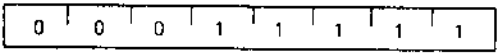
Cycles: 1
States: 4
Flags: CY

RAR (Rotate right through carry)

$(A_n) \leftarrow (A_{n+1})$; $(CY) \leftarrow (A_0)$

$(A_7) \leftarrow (CY)$

The content of the accumulator is rotated right one position through the CY flag. The high order bit is set to the CY flag and the CY flag is set to the value shifted out of the low order bit. **Only the CY flag is affected.**

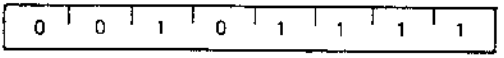


Cycles: 1
States: 4
Flags: CY

CMA (Complement accumulator)

$(A) \leftarrow (\overline{A})$

The contents of the accumulator are complemented (zero bits become 1, one bits become 0). **No flags are affected.**

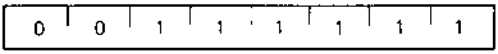


Cycles: 1
States: 4
Flags: none

CMC (Complement carry)

(CY) ← $\overline{(CY)}$

The CY flag is complemented. **No other flags are affected.**

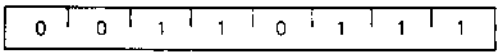


Cycles: 1
States: 4
Flags: CY

STC (Set carry)

(CY) ← 1

The CY flag is set to 1. **No other flags are affected.**



Cycles: 1
States: 4
Flags: CY

Branch Group:

This group of instructions alter normal sequential program flow.

Condition flags are not affected by any instruction in this group.

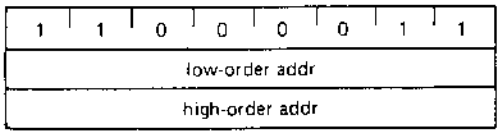
The two types of branch instructions are unconditional and conditional. Unconditional transfers simply perform the specified operation on register PC (the program counter). Conditional transfers examine the status of one of the four processor flags to determine if the specified branch is to be executed. The conditions that may be specified are as follows:

CONDITION		CCC
NZ	– not zero (Z = 0)	000
Z	– zero (Z = 1)	001
NC	– no carry (CY = 0)	010
C	– carry (CY = 1)	011
PO	– parity odd (P = 0)	100
PE	– parity even (P = 1)	101
P	– plus (S = 0)	110
M	– minus (S = 1)	111

JMP addr (Jump)

(PC) ← (byte 3) (byte 2)

Control is transferred to the instruction whose address is specified in byte 3 and byte 2 of the current instruction.



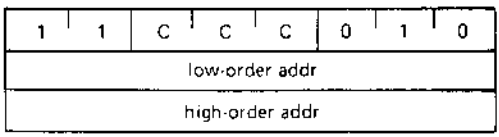
Cycles: 3
States: 10
Addressing: immediate
Flags: none

Jcondition addr (Conditional jump)

If (CCC),

(PC) ← (byte 3) (byte 2)

If the specified condition is true, control is transferred to the instruction whose address is specified in byte 3 and byte 2 of the current instruction; otherwise, control continues sequentially.



Cycles: 3
States: 10
Addressing: immediate
Flags: none

CALL addr (Call)

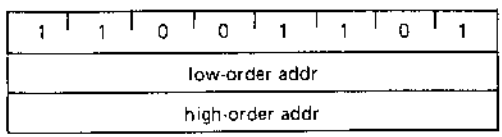
((SP) – 1) ← (PCH)

((SP) – 2) ← (PCL)

(SP) ← (SP) – 2

(PC) ← (byte 3) (byte 2)

The high-order eight bits of the next instruction address are moved to the memory location whose address is one less than the content of register SP. The low-order eight bits of the next instruction address are moved to the memory location whose address is two less than the content of register SP. The content of register SP is decremented by 2. Control is transferred to the instruction whose address is specified in byte 3 and byte 2 of the current instruction.

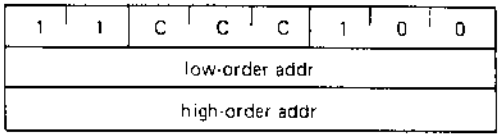


Cycles: 5
States: 17
Addressing: immediate/reg. indirect
Flags: none

Ccondition addr (Condition call)

If (CCC),
((SP) − 1) ← (PCH)
((SP) − 2) ← (PCL)
(SP) ← (SP) − 2
(PC) ← (byte 3) (byte 2)

If the specified condition is true, the actions specified in the CALL instruction (see above) are performed; otherwise, control continues sequentially.

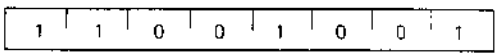


Cycles: 3/5
States: 11/17
Addressing: immediate/reg. indirect
Flags: none

RET (Return)

(PCL) ← ((SP));
(PCH) ← ((SP) + 1);
(SP) ← (SP) + 2;

The content of the memory location whose address is specified in register SP is moved to the low-order eight bits of register PC. The content of the memory location whose address is one more than the content of register SP is moved to the high-order eight bits of register PC. The content of register SP is incremented by 2.

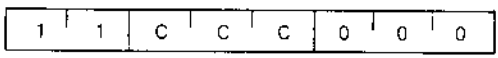


Cycles: 3
States: 10
Addressing: reg. indirect
Flags: none

Rcondition (Conditional return)

If (CCC),
(PCL) ← ((SP))
(PCH) ← ((SP) + 1)
(SP) ← (SP) + 2

If the specified condition is true, the actions specified in the RET instruction (see above) are performed; otherwise, control continues sequentially.

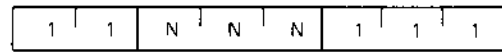


Cycles: 1/3
States: 5/11
Addressing: reg. indirect
Flags: none

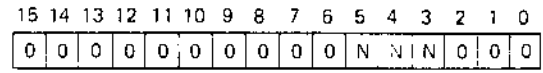
RST n (Restart)

((SP) − 1) ← (PCH)
((SP) − 2) ← (PCL)
(SP) ← (SP) − 2
(PC) ← 8 * (NNN)

The high-order eight bits of the next instruction address are moved to the memory location whose address is one less than the content of register SP. The low-order eight bits of the next instruction address are moved to the memory location whose address is two less than the content of register SP. The content of register SP is decremented by two. Control is transferred to the instruction whose address is eight times the content of NNN.



Cycles: 3
States: 11
Addressing: reg. indirect
Flags: none

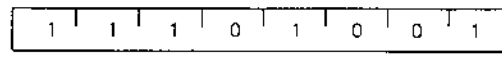


Program Counter After Restart

PCHL (Jump H and L indirect — move H and L to PC)

(PCH) ← (H)
(PCL) ← (L)

The content of register H is moved to the high-order eight bits of register PC. The content of register L is moved to the low-order eight bits of register PC.



Cycles: 1
States: 5
Addressing: register
Flags: none

Stack, I/O, and Machine Control Group:

This group of instructions performs I/O, manipulates the Stack, and alters internal control flags.

Unless otherwise specified, **condition flags are not affected by any instructions in this group.**

FLAG WORD

D_7	D_6	D_5	D_4	D_3	D_2	D_1	D_0
S	Z	0	AC	0	P	1	CY

PUSH rp (Push)

((SP) − 1) ← (rh)
((SP) − 2) ← (rl)
(SP) ← (SP) − 2

The content of the high-order register of register pair rp is moved to the memory location whose address is one less than the content of register SP. The content of the low-order register of register pair rp is moved to the memory location whose address is two less than the content of register SP. The content of register SP is decremented by 2. **Note: Register pair rp = SP may not be specified.**

1	1	R	P	0	1	0	1

Cycles: 3
States: 11
Addressing: reg. indirect
Flags: none

PUSH PSW (Push processor status word)

((SP) − 1) ← (A)
$((SP)-2)_0$ ← (CY), $((SP)-2)_1$ ← 1
$((SP)-2)_2$ ← (P), $((SP)-2)_3$ ← 0
$((SP)-2)_4$ ← (AC), $((SP)-2)_5$ ← 0
$((SP)-2)_6$ ← (Z), $((SP)-2)_7$ ← (S)
(SP) ← (SP) − 2

The content of register A is moved to the memory location whose address is one less than register SP. The contents of the condition flags are assembled into a processor status word and the word is moved to the memory location whose address is two less than the content of register SP. The content of register SP is decremented by two.

1	1	1	1	0	1	0	1

Cycles: 3
States: 11
Addressing: reg. indirect
Flags: none

POP rp (Pop)

(rl) ← ((SP))
(rh) ← ((SP) + 1)
(SP) ← (SP) + 2

The content of the memory location, whose address is specified by the content of register SP, is moved to the low-order register of register pair rp. The content of the memory location, whose address is one more than the content of register SP, is moved to the high-order register of register pair rp. The content of register SP is incremented by 2. **Note: Register pair rp = SP may not be specified.**

1	1	R	P	0	0	0	1

Cycles: 3
States: 10
Addressing: reg. indirect
Flags: none

POP PSW (Pop processor status word)

$(CY) \leftarrow ((SP))_0$
$(P) \leftarrow ((SP))_2$
$(AC) \leftarrow ((SP))_4$
$(Z) \leftarrow ((SP))_6$
$(S) \leftarrow ((SP))_7$
(A) ← ((SP) + 1)
(SP) ← (SP) + 2

The content of the memory location whose address is specified by the content of register SP is used to restore the condition flags. The content of the memory location whose address is one more than the content of register SP is moved to register A. The content of register SP is incremented by 2.

1	1	1	1	0	0	0	1

Cycles: 3
States: 10
Addressing: reg. indirect
Flags: Z,S,P,CY,AC

XTHL (Exchange stack top with H and L)

(L) ⟷ ((SP))
(H) ⟷ ((SP) + 1)

The content of the L register is exchanged with the content of the memory location whose address is specified by the content of register SP. The content of the H register is exchanged with the content of the memory location whose address is one more than the content of register SP.

1	1	1	0	0	0	1	1

Cycles: 5
States: 18
Addressing: reg. indirect
Flags: none

SPHL (Move HL to SP)

(SP) ← (H) (L)

The contents of registers H and L (16 bits) are moved to register SP.

1	1	1	1	1	0	0	1

Cycles: 1
States: 5
Addressing: register
Flags: none

IN port (Input)

(A) ← (data)

The data placed on the eight bit bi-directional data bus by the specified port is moved to register A.

1	1	0	1	1	0	1	1
port							

Cycles: 3
States: 10
Addressing: direct
Flags: none

OUT port (Output)

(data) ← (A)

The content of register A is placed on the eight bit bi-directional data bus for transmission to the specified port.

1	1	0	1	0	0	1	1
port							

Cycles: 3
States: 10
Addressing: direct
Flags: none

EI (Enable interrupts)

The interrupt system is enabled following the execution of the next instruction.

1	1	1	1	1	0	1	1

Cycles: 1
States: 4
Flags: none

DI (Disable interrupts)

The interrupt system is disabled immediately following the execution of the DI instruction.

1	1	1	1	0	0	1	1

Cycles: 1
States: 4
Flags: none

HLT (Halt)

The processor is stopped. The registers and flags are unaffected.

0	1	1	1	0	1	1	0

Cycles: 1
States: 7
Flags: none

NOP (No op)

No operation is performed. The registers and flags are unaffected.

0	0	0	0	0	0	0	0

Cycles: 1
States: 4
Flags: none

INSTRUCTION SET

Summary of Processor Instructions

Mnemonic	Description	Instruction Code[1] D_7	D_6	D_5	D_4	D_3	D_2	D_1	D_0	Clock[2] Cycles
MOV r1,r2	Move register to register	0	1	D	D	D	S	S	S	5
MOV M,r	Move register to memory	0	1	1	1	0	S	S	S	7
MOV r,M	Move memory to register	0	1	D	D	D	1	1	0	7
HLT	Halt	0	1	1	1	0	1	1	0	7
MVI r	Move immediate register	0	0	D	D	D	1	1	0	7
MVI M	Move immediate memory	0	0	1	1	0	1	1	0	10
INR r	Increment register	0	0	D	D	D	1	0	0	5
DCR r	Decrement register	0	0	D	D	D	1	0	1	5
INR M	Increment memory	0	0	1	1	0	1	0	0	10
DCR M	Decrement memory	0	0	1	1	0	1	0	1	10
ADD r	Add register to A	1	0	0	0	0	S	S	S	4
ADC r	Add register to A with carry	1	0	0	0	1	S	S	S	4
SUB r	Subtract register from A	1	0	0	1	0	S	S	S	4
SBB r	Subtract register from A with borrow	1	0	0	1	1	S	S	S	4
ANA r	And register with A	1	0	1	0	0	S	S	S	4
XRA r	Exclusive Or register with A	1	0	1	0	1	S	S	S	4
ORA r	Or register with A	1	0	1	1	0	S	S	S	4
CMP r	Compare register with A	1	0	1	1	1	S	S	S	4
ADD M	Add memory to A	1	0	0	0	0	1	1	0	7
ADC M	Add memory to A with carry	1	0	0	0	1	1	1	0	7
SUB M	Subtract memory from A	1	0	0	1	0	1	1	0	7
SBB M	Subtract memory from A with borrow	1	0	0	1	1	1	1	0	7
ANA M	And memory with A	1	0	1	0	0	1	1	0	7
XRA M	Exclusive Or memory with A	1	0	1	0	1	1	1	0	7
ORA M	Or memory with A	1	0	1	1	0	1	1	0	7
CMP M	Compare memory with A	1	0	1	1	1	1	1	0	7
ADI	Add immediate to A	1	1	0	0	0	1	1	0	7
ACI	Add immediate to A with carry	1	1	0	0	1	1	1	0	7
SUI	Subtract immediate from A	1	1	0	1	0	1	1	0	7
SBI	Subtract immediate from A with borrow	1	1	0	1	1	1	1	0	7
ANI	And immediate with A	1	1	1	0	0	1	1	0	7
XRI	Exclusive Or immediate with A	1	1	1	0	1	1	1	0	7
ORI	Or immediate with A	1	1	1	1	0	1	1	0	7
CPI	Compare immediate with A	1	1	1	1	1	1	1	0	7
RLC	Rotate A left	0	0	0	0	0	1	1	1	4
RRC	Rotate A right	0	0	0	0	1	1	1	1	4
RAL	Rotate A left through carry	0	0	0	1	0	1	1	1	4
RAR	Rotate A right through carry	0	0	0	1	1	1	1	1	4
JMP	Jump unconditional	1	1	0	0	0	0	1	1	10
JC	Jump on carry	1	1	0	1	1	0	1	0	10
JNC	Jump on no carry	1	1	0	1	0	0	1	0	10
JZ	Jump on zero	1	1	0	0	1	0	1	0	10
JNZ	Jump on no zero	1	1	0	0	0	0	1	0	10
JP	Jump on positive	1	1	1	1	0	0	1	0	10
JM	Jump on minus	1	1	1	1	1	0	1	0	10
JPE	Jump on parity even	1	1	1	0	1	0	1	0	10
JPO	Jump on parity odd	1	1	1	0	0	0	1	0	10
CALL	Call unconditional	1	1	0	0	1	1	0	1	17
CC	Call on carry	1	1	0	1	1	1	0	0	11/17
CNC	Call on no carry	1	1	0	1	0	1	0	0	11/17
CZ	Call on zero	1	1	0	0	1	1	0	0	11/17
CNZ	Call on no zero	1	1	0	0	0	1	0	0	11/17
CP	Call on positive	1	1	1	1	0	1	0	0	11/17
CM	Call on minus	1	1	1	1	1	1	0	0	11/17
CPE	Call on parity even	1	1	1	0	1	1	0	0	11/17
CPO	Call on parity odd	1	1	1	0	0	1	0	0	11/17
RET	Return	1	1	0	0	1	0	0	1	10
RC	Return on carry	1	1	0	1	1	0	0	0	5/11
RNC	Return on no carry	1	1	0	1	0	0	0	0	5/11
RZ	Return on zero	1	1	0	0	1	0	0	0	5/11
RNZ	Return on no zero	1	1	0	0	0	0	0	0	5/11
RP	Return on positive	1	1	1	1	0	0	0	0	5/11
RM	Return on minus	1	1	1	1	1	0	0	0	5/11
RPE	Return on parity even	1	1	1	0	1	0	0	0	5/11
RPO	Return on parity odd	1	1	1	0	0	0	0	0	5/11
RST	Restart	1	1	A	A	A	1	1	1	11
IN	Input	1	1	0	1	1	0	1	1	10
OUT	Output	1	1	0	1	0	0	1	1	10
LXI B	Load immediate register Pair B & C	0	0	0	0	0	0	0	1	10
LXI D	Load immediate register Pair D & E	0	0	0	1	0	0	0	1	10
LXI H	Load immediate register Pair H & L	0	0	1	0	0	0	0	1	10
LXI SP	Load immediate stack pointer	0	0	1	1	0	0	0	1	10
PUSH B	Push register Pair B & C on stack	1	1	0	0	0	1	0	1	11
PUSH D	Push register Pair D & E on stack	1	1	0	1	0	1	0	1	11
PUSH H	Push register Pair H & L on stack	1	1	1	0	0	1	0	1	11
PUSH PSW	Push A and Flags on stack	1	1	1	1	0	1	0	1	11
POP B	Pop register pair B & C off stack	1	1	0	0	0	0	0	1	10
POP D	Pop register pair D & E off stack	1	1	0	1	0	0	0	1	10
POP H	Pop register pair H & L off stack	1	1	1	0	0	0	0	1	10
POP PSW	Pop A and Flags off stack	1	1	1	1	0	0	0	1	10
STA	Store A direct	0	0	1	1	0	0	1	0	13
LDA	Load A direct	0	0	1	1	1	0	1	0	13
XCHG	Exchange D & E, H & L Registers	1	1	1	0	1	0	1	1	4
XTHL	Exchange top of stack H & L	1	1	1	0	0	0	1	1	18
SPHL	H & L to stack pointer	1	1	1	1	1	0	0	1	5
PCHL	H & L to program counter	1	1	1	0	1	0	0	1	5
DAD B	Add B & C to H & L	0	0	0	0	1	0	0	1	10
DAD D	Add D & E to H & L	0	0	0	1	1	0	0	1	10
DAD H	Add H & L to H & L	0	0	1	0	1	0	0	1	10
DAD SP	Add stack pointer to H & L	0	0	1	1	1	0	0	1	10
STAX B	Store A indirect	0	0	0	0	0	0	1	0	7
STAX D	Store A indirect	0	0	0	1	0	0	1	0	7
LDAX B	Load A indirect	0	0	0	0	1	0	1	0	7
LDAX D	Load A indirect	0	0	0	1	1	0	1	0	7
INX B	Increment B & C registers	0	0	0	0	0	0	1	1	5
INX D	Increment D & E registers	0	0	0	1	0	0	1	1	5
INX H	Increment H & L registers	0	0	1	0	0	0	1	1	5
INX SP	Increment stack pointer	0	0	1	1	0	0	1	1	5
DCX B	Decrement B & C	0	0	0	0	1	0	1	1	5
DCX D	Decrement D & E	0	0	0	1	1	0	1	1	5
DCX H	Decrement H & L	0	0	1	0	1	0	1	1	5
DCX SP	Decrement stack pointer	0	0	1	1	1	0	1	1	5
CMA	Complement A	0	0	1	0	1	1	1	1	4
STC	Set carry	0	0	1	1	0	1	1	1	4
CMC	Complement carry	0	0	1	1	1	1	1	1	4
DAA	Decimal adjust A	0	0	1	0	0	1	1	1	4
SHLD	Store H & L direct	0	0	1	0	0	0	1	0	16
LHLD	Load H & L direct	0	0	1	0	1	0	1	0	16
EI	Enable Interrupts	1	1	1	1	1	0	1	1	4
DI	Disable interrupt	1	1	1	1	0	0	1	1	4
NOP	No-operation	0	0	0	0	0	0	0	0	4

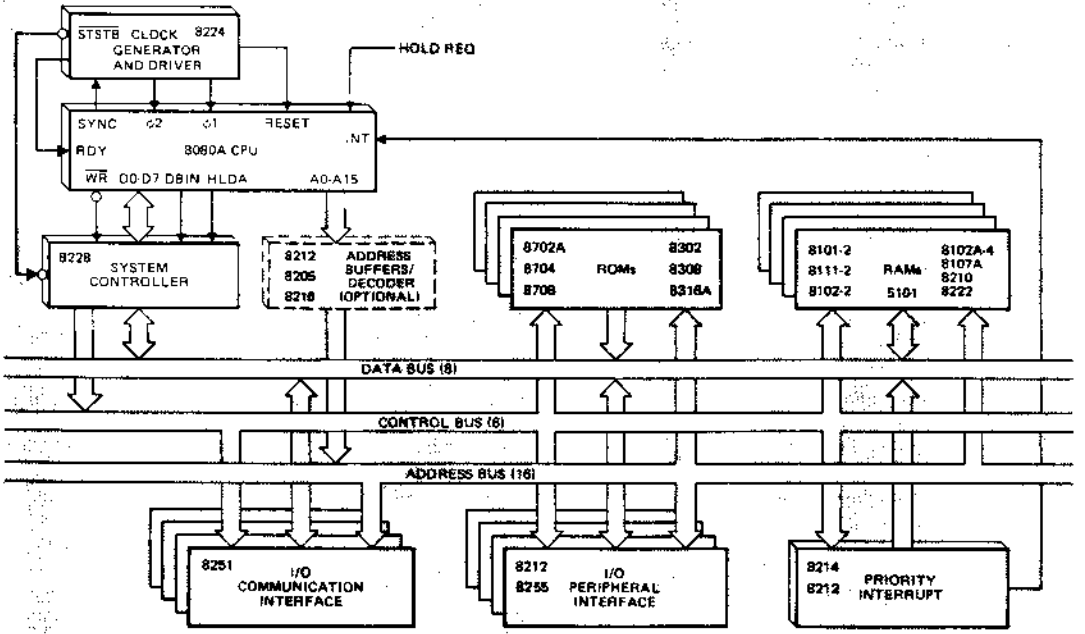
NOTES: 1. DDD or SSS - 000 B 001 C - 010 D - 011 E 100 H - 101 L - 110 Memory - 111 A.
2. Two possible cycle times, (5/11) indicate instruction cycles dependent on condition flags.

CHAPTER 5
MCS-80 COMPONENT FAMILY

intel®
Microcomputer Systems

CPU Group

8224 8080A-1
8228 8080A-2
8080A M8080-A



Schottky Bipolar 8224

CLOCK GENERATOR AND DRIVER FOR 8080A CPU

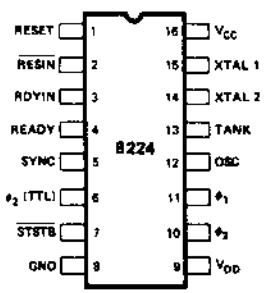
- **Single Chip Clock Generator/Driver for 8080A CPU**
- **Power-Up Reset for CPU**
- **Ready Synchronizing Flip-Flop**
- **Advanced Status Strobe**
- **Oscillator Output for External System Timing**
- **Crystal Controlled for Stable System Operation**
- **Reduces System Package Count**

The 8224 is a single chip clock generator/driver for the 8080A CPU. It is controlled by a crystal, selected by the designer, to meet a variety of system speed requirements.

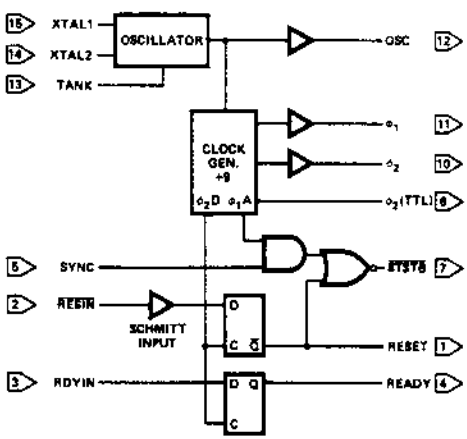
Also included are circuits to provide power-up reset, advance status strobe and synchronization of ready.

The 8224 provides the designer with a significant reduction of packages used to generate clocks and timing for 8080A.

PIN CONFIGURATION



BLOCK DIAGRAM



PIN NAMES

RESIN	RESET INPUT
RESET	RESET OUTPUT
RDYIN	READY INPUT
READY	READY OUTPUT
SYNC	SYNC INPUT
STSTB	STATUS STB (ACTIVE LOW)
φ1	8080 CLOCKS
φ2	8080 CLOCKS

XTAL 1	CONNECTIONS FOR CRYSTAL
XTAL 2	CONNECTIONS FOR CRYSTAL
TANK	USED WITH OVERTONE XTAL
OSC	OSCILLATOR OUTPUT
φ2 (TTL)	φ2 CLK (TTL LEVEL)
V_{CC}	+5V
V_{DD}	+12V
GND	0V

FUNCTIONAL DESCRIPTION

General

The 8224 is a single chip Clock Generator/Driver for the 8080A CPU. It contains a crystal-controlled oscillator, a "divide by nine" counter, two high-level drivers and several auxiliary logic functions.

Oscillator

The oscillator circuit derives its basic operating frequency from an external, series resonant, fundamental mode crystal. Two inputs are provided for the crystal connections (XTAL1, XTAL2).

The selection of the external crystal frequency depends mainly on the speed at which the 8080A is to be run at. Basically, the oscillator operates at 9 times the desired processor speed.

A simple formula to guide the crystal selection is:

$$\text{Crystal Frequency} = \frac{1}{t_{CY}} \text{ times } 9$$

Example 1: (500ns t_{CY})
2mHz times 9 = 18mHz*

Example 2: (800ns t_{CY})
1.25mHz times 9 = 11.25mHz

Another input to the oscillator is TANK. This input allows the use overtone mode crystals. This type of crystal generally has much lower "gain" than the fundamental type so an external LC network is necessary to provide the additional "gain" for proper oscillator operation. The external LC network is connected to the TANK input and is AC coupled to ground. See Figure 4.

The formula for the LC network is:

$$F = \frac{1}{2\pi\sqrt{LC}}$$

The output of the oscillator is buffered and brought out on OSC (pin 12) so that other system timing signals can be derived from this stable, crystal-controlled source.

*When using crystals above 10mHz a small amount of frequency "trimming" may be necessary to produce the exact desired frequency. The addition of a small selected capacitance (3pF - 10pF) in series with the crystal will accomplish this function.

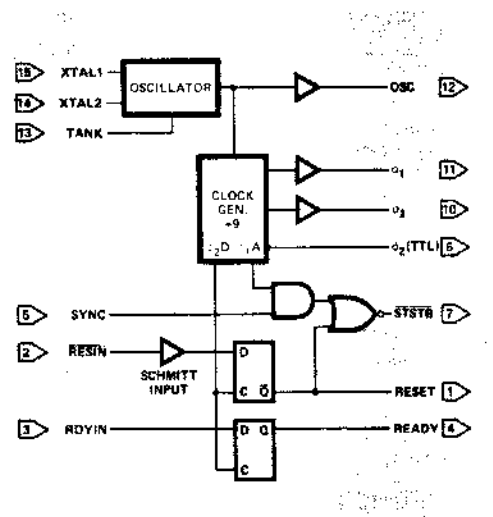
Clock Generator

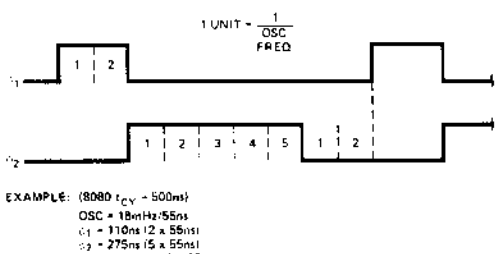
The Clock Generator consists of a synchronous "divide by nine" counter and the associated decode gating to create the waveforms of the two 8080A clocks and auxiliary timing signals.

The waveforms generated by the decode gating follow a simple 2-5-2 digital pattern. See Figure 2. The clocks generated; phase 1 and phase 2, can best be thought of as consisting of "units" based on the oscillator frequency. Assume that one "unit" equals the period of the oscillator frequency. By multiplying the number of "units" that are contained in a pulse width or delay, times the period of the oscillator frequency, the approximate time in nanoseconds can be derived.

The outputs of the clock generator are connected to two high level drivers for direct interface to the 8080A CPU. A TTL level phase 2 is also brought out ϕ_2 (TTL) for external timing purposes. It is especially useful in DMA dependant activities. This signal is used to gate the requesting device onto the bus once the 8080A CPU issues the Hold Acknowledgement (HLDA).

Several other signals are also generated internally so that optimum timing of the auxiliary flip-flops and status strobe ($\overline{STSTB}$) is achieved.





$\overline{\text{STSTB}}$ (Status Strobe)

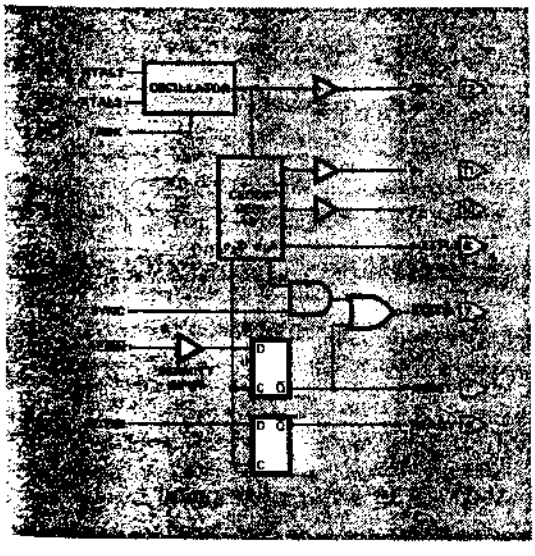
At the beginning of each machine cycle the 8080A CPU issues status information on its data bus. This information tells what type of action will take place during that machine cycle. By bringing in the SYNC signal from the CPU, and gating it with an internal timing signal (ϕ1A), an active low strobe can be derived that occurs at the start of each machine cycle at the earliest possible moment that status data is stable on the bus. The $\overline{\text{STSTB}}$ signal connects directly to the 8228 System Controller.

The power-on Reset also generates $\overline{\text{STSTB}}$, but of course, for a longer period of time. This feature allows the 8228 to be automatically reset without additional pins devoted for this function.

Power-On Reset and Ready Flip-Flops

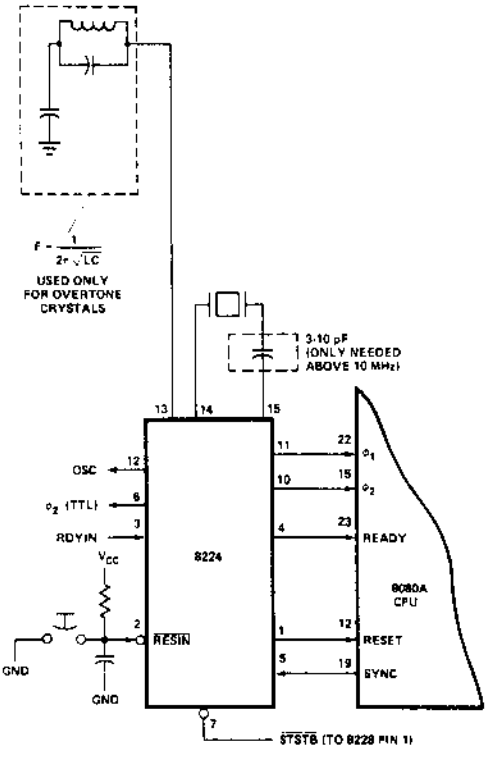
A common function in 8080A Microcomputer systems is the generation of an automatic system reset and start-up upon initial power-on. The 8224 has a built in feature to accomplish this feature.

An external RC network is connected to the $\overline{\text{RESIN}}$ input. The slow transition of the power supply rise is sensed by an internal Schmitt Trigger. This circuit converts the slow transition into a clean, fast edge when its input level reaches a predetermined value. The output of the Schmitt Trigger is connected to a "D" type flip-flop that is clocked with ϕ2D (an internal timing signal). The flip-flop is synchronously reset and an active high level that complies with the 8080A input spec is generated. For manual switch type system Reset circuits, an active low switch closing can be connected to the $\overline{\text{RESIN}}$ input in addition to the power-on RC netnetwork.



The READY input to the 8080A CPU has certain timing specifications such as "set-up and hold" thus, an external synchronizing flip-flop is required. The 8224 has this feature built-in. The RDYIN input presents the asynchronous "wait request" to the "D" type flip-flop. By clocking the flip-flop with ϕ2D, a synchronized READY signal at the correct input level, can be connected directly to the 8080A.

The reason for requiring an external flip-flop to synchronize the "wait request" rather than internally in the 8080 CPU is that due to the relatively long delays of MOS logic such an implementation would "rob" the designer of about 200ns during the time his logic is determining if a "wait" is necessary. An external bipolar circuit built into the clock generator eliminates most of this delay and has no effect on component count.



D.C. Characteristics

T_A = 0°C to 70°C; V_{CC} = +5.0V ±5%; V_{DD} = +12V ±5%.

Symbol	Parameter	Limits Min.	Typ.	Max.	Units	Test Conditions
I_F	Input Current Loading			-.25	mA	V_F = .45V
I_R	Input Leakage Current			10	μA	V_R = 5.25V
V_C	Input Forward Clamp Voltage			1.0	V	I_C = -5mA
V_{IL}	Input "Low" Voltage			.8	V	V_{CC} = 5.0V
V_{IH}	Input "High" Voltage	2.6 2.0			V	Reset Input All Other Inputs
V_{IH}-V_{IL}	RESIN Input Hysteresis	.25			mV	V_{CC} = 5.0V
V_{OL}	Output "Low" Voltage			.45 .45	V V	(ϕ_1,ϕ_2), Ready, Reset, $\overline{STSTB}$ I_{OL} =2.5mA All Other Outputs I_{OL} = 15mA
V_{OH}	Output "High" Voltage ϕ_1 , ϕ_2 READY, RESET All Other Outputs	 9.4 3.6 2.4			 V V V	 I_{OH} = -100μA I_{OH} = -100μA I_{OH} = -1mA
I_{SC}[1]	Output Short Circuit Current (All Low Voltage Outputs Only)	-10		-60	mA	V_O = 0V V_{CC} = 5.0V
I_{CC}	Power Supply Current			115	mA	
I_{DD}	Power Supply Current			12	mA	

Note: 1. Caution, ϕ_1 and ϕ_2 output drivers do not have short circuit protection

CRYSTAL REQUIREMENTS

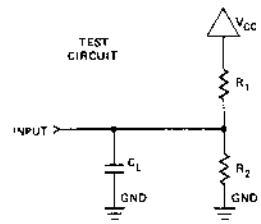
Tolerance: .005% at 0°C -70°C
Resonance: Series (Fundamental)*
Load Capacitance: 20-35pF
Equivalent Resistance: 75-20 ohms
Power Dissipation (Min): 4mW

*With tank circuit use 3rd overtone mode.

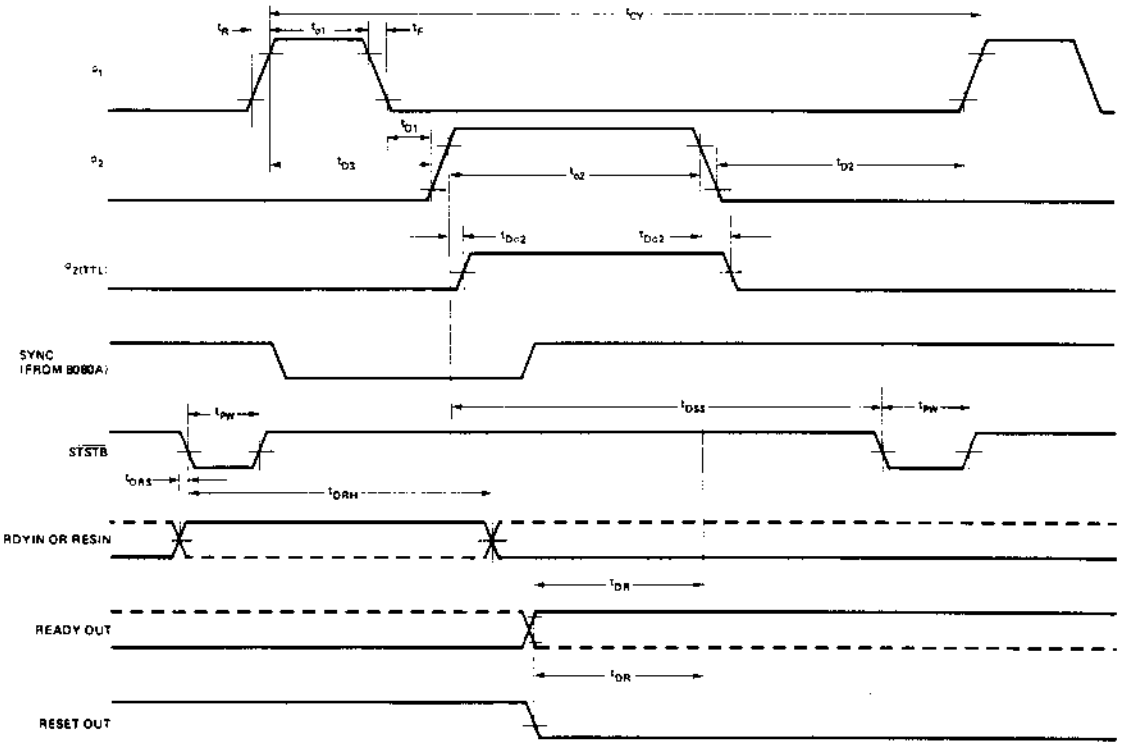
A.C. Characteristics

V_{CC} = +5.0V ± 5%; V_{DD} = +12.0V ± 5%; T_A = 0°C to 70°C

Symbol	Parameter	Limits Min.	Limits Typ.	Limits Max.	Units	Test Conditions
$t_{\phi 1}$	ϕ_1 Pulse Width	$\frac{2tcy}{9}$ - 20ns			ns	C_L = 20pF to 50pF
$t_{\phi 2}$	ϕ_2 Pulse Width	$\frac{5tcy}{9}$ - 35ns				
t_{D1}	ϕ_1 to ϕ_2 Delay	0				
t_{D2}	ϕ_2 to ϕ_1 Delay	$\frac{2tcy}{9}$ - 14ns				
t_{D3}	ϕ_1 to ϕ_2 Delay	$\frac{2tcy}{9}$		$\frac{2tcy}{9}$ + 20ns		
t_R	ϕ_1 and ϕ_2 Rise Time			20		
t_F	ϕ_1 and ϕ_2 Fall Time			20		
$t_{D\phi 2}$	ϕ_2 to ϕ_2 (TTL) Delay	-5		+15	ns	ϕ_2TTL,CL=30 R_1=300Ω R_2=600Ω
t_{DSS}	ϕ_2 to $\overline{STSTB}$ Delay	$\frac{6tcy}{9}$ - 30ns		$\frac{6tcy}{9}$		
t_{PW}	$\overline{STSTB}$ Pulse Width	$\frac{tcy}{9}$ - 15ns				$\overline{STSTB}$, CL=15pF R_1 = 2K R_2 = 4K
t_{DRS}	RDYIN Setup Time to Status Strobe	50ns - $\frac{4tcy}{9}$				
t_{DRH}	RDYIN Hold Time After $\overline{STSTB}$	$\frac{4tcy}{9}$				
t_{DR}	RDYIN or RESIN to ϕ_2 Delay	$\frac{4tcy}{9}$ - 25ns				Ready & Reset CL=10pF R_1=2K R_2=4K
t_{CLK}	CLK Period		$\frac{tcy}{9}$			
f_{max}	Maximum Oscillating Frequency	27			MHz	
C_{in}	Input Capacitance			8	pF	V_{CC}=+5.0V V_{DD}=+12V V_{BIAS}=2.5V f=1MHz



WAVEFORMS



VOLTAGE MEASUREMENT POINTS: ϕ_1, ϕ_2 Logic "0" = 1.0V, Logic "1" = 8.0V. All other signals measured at 1.5V.

EXAMPLE:

A.C. Characteristics (For t_{CY} = 488.28 ns)

T_A = 0°C to 70°C; V_{DD} = +5V ±5%; V_{DD} = +12V ±5%.

Symbol	Parameter	Limits Min.	Limits Typ.	Limits Max.	Units	Test Conditions
$t_{\phi 1}$	ϕ_1 Pulse Width	89			ns	t_{CY}=488.28ns
$t_{\phi 2}$	ϕ_2 Pulse Width	236			ns	
t_{D1}	Delay ϕ_1 to ϕ_2	0			ns	
t_{D2}	Delay ϕ_2 to ϕ_1	95			ns	ϕ_1 & ϕ_2 Loaded to C_L = 20 to 50pF
t_{D3}	Delay ϕ_1 to ϕ_2 Leading Edges	109		129	ns	
t_r	Output Rise Time			20	ns	
t_f	Output Fall Time			20	ns	
t_{DSS}	ϕ_2 to $\overline{STSTB}$ Delay	296		326	ns	
$t_{D\phi 2}$	ϕ_2 to ϕ_2 (TTL) Delay	-5		+15	ns	
t_{PW}	Status Strobe Pulse Width	40			ns	Ready & Reset Loaded to 2mA/10pF
t_{DRS}	RDYIN Setup Time to $\overline{STSTB}$	-167			ns	
t_{DRH}	RDYIN Hold Time after $\overline{STSTB}$	217			ns	All measurements referenced to 1.5V unless specified otherwise.
t_{DR}	READY or RESET to ϕ_2 Delay	192			ns	
f_{MAX}	Oscillator Frequency			18.432	MHz	

Schottky Bipolar 8228

SYSTEM CONTROLLER AND BUS DRIVER FOR 8080A CPU

- **Single Chip System Control for MCS-80 Systems**
- **Built-in Bi-Directional Bus Driver for Data Bus Isolation**
- **Allows the use of Multiple Byte Instructions (e.g. CALL) for Interrupt Acknowledge**
- **User Selected Single Level Interrupt Vector (RST 7)**
- **28 Pin Dual In-Line Package**
- **Reduces System Package Count**

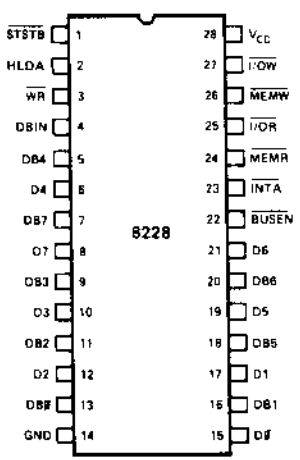
The 8228 is a single chip system controller and bus driver for MCS-80. It generates all signals required to directly interface MCS-80 family RAM, ROM, and I/O components.

A bi-directional bus driver is included to provide high system TTL fan-out. It also provides isolation of the 8080 data bus from memory and I/O. This allows for the optimization of control signals, enabling the systems deisgner to use slower memory and I/O. The isolation of the bus driver also provides for enhanced system noise immunity.

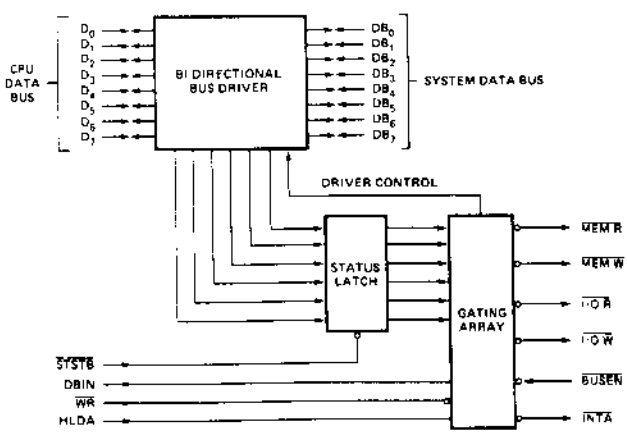
A user selected single level interrupt vector (RST 7) is provided to simplify real time, interrupt driven, small system requirements. The 8228 also generates the correct control signals to allow the use of multiple byte instructions (e.g., CALL) in response to an INTERRUPT ACKNOWLEDGE by the 8080A. This feature permits large, interrupt driven systems to have an unlimited number of interrupt levels.

The 8228 is designed to support a wide variety of system bus structures and also reduce system package count for cost effective, reliable, design of the MCS-80 systems.

PIN CONFIGURATION



8228 BLOCK DIAGRAM



PIN NAMES

D7 D0	DATA BUS (8080 SIDE)	INTA	INTERRUPT ACKNOWLEDGE
DB7-DB0	DATA BUS (SYSTEM SIDE)	HLDA	HLDA (FROM 8080)
I/OR	I/O READ	WR	WR (FROM 8080)
I/OW	I/O WRITE	BUSEN	BUS ENABLE INPUT
MEMR	MEMORY READ	STSTB	STATUS STROBE (FROM 8224)
MEMW	MEMORY WRITE	Vcc	+5V
DBIN	DBIN (FROM 8080)	GND	0 VOLTS

FUNCTIONAL DESCRIPTION

General

The 8228 is a single chip System Controller and Data Bus driver for the 8080 Microcomputer System. It generates all control signals required to directly interface MCS-80™ family RAM, ROM, and I/O components.

Schottky Bipolar technology is used to maintain low delay times and provide high output drive capability to support small to medium systems.

Bi-Directional Bus Driver

An eight bit, bi-directional bus driver is provided to buffer the 8080 data bus from Memory and I/O devices. The 8080A data bus has an input requirement of 3.3 volts (min) and can drive (sink) a maximum current of 1.9mA. The 8228 data bus driver assures that these input requirements will be not only met but exceeded for enhanced noise immunity. Also, on the system side of the driver adequate drive current is available (10mA Typ.) so that a large number of Memory and I/O devices can be directly connected to the bus.

The Bi-Directional Bus Driver is controlled by signals from the Gating Array so that proper bus flow is maintained and its outputs can be forced into their high impedance state (3-state) for DMA activities.

Status Latch

At the beginning of each machine cycle the 8080 CPU issues "status" information on its data bus that indicates the type of activity that will occur during the cycle. The 8228 stores this information in the Status Latch when the $\overline{STSTB}$ input goes "low". The output of the Status Latch is connected to the Gating Array and is part of the Control Signal generation.

Gating Array

The Gating Array generates control signals ($\overline{MEM\ R}$, $\overline{MEM\ W}$, $\overline{I/O\ R}$, $\overline{I/O\ W}$ and $\overline{INTA}$) by gating the outputs of the Status Latch with signals from the 8080 CPU (DBIN, $\overline{WR}$, and HLDA).

The "read" control signals ($\overline{MEM\ R}$, $\overline{I/O\ R}$ and $\overline{INTA}$) are derived from the logical combination of the appropriate Status Bit (or bits) and the DBIN input from the 8080 CPU.

The "write" control signals ($\overline{MEM\ W}$, $\overline{I/O\ W}$) are derived from the logical combination of the appropriate Status Bit (or bits) and the $\overline{WR}$ input from the 8080 CPU.

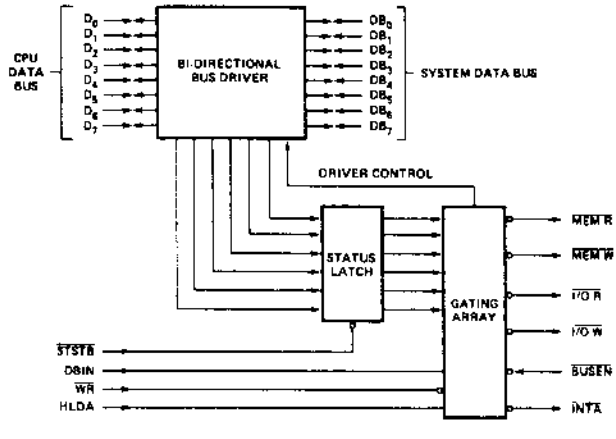
All Control Signals are "active low" and directly interface to MCS-80 family RAM, ROM and I/O components.

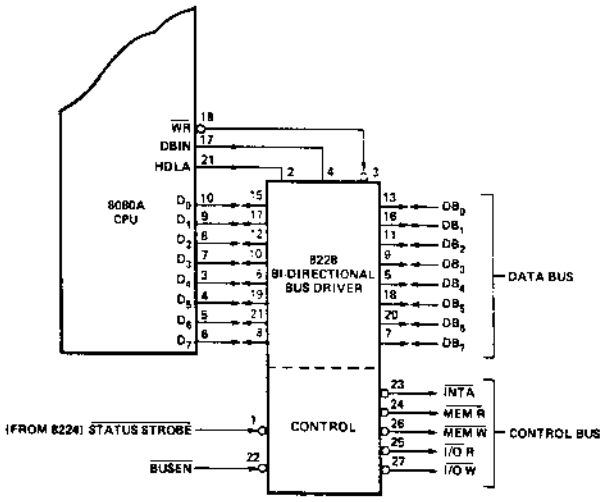
The $\overline{INTA}$ control signal is normally used to gate the "interrupt instruction port" onto the bus. It also provides a special feature in the 8228. If only one basic vector is needed in the interrupt structure, such as in small systems, the 8228 can automatically insert a RST 7 instruction onto the bus at the proper time. To use this option, simply connect the $\overline{INTA}$ output of the 8228 (pin 23) to the +12 volt supply through a series resistor (1K ohms). The voltage is sensed internally by the 8228 and logic is "set-up" so that when the DBIN input is active a RST 7 instruction is gated on to the bus when an interrupt is acknowledged. This feature provides a single interrupt vector with no additional components, such as an interrupt instruction port.

When using CALL as an Interrupt instruction the 8228 will generate an $\overline{INTA}$ pulse for each of the three bytes.

The $\overline{BUSEN}$ (Bus Enable) input to the Gating Array is an asynchronous input that forces the data bus output buffers and control signal buffers into their high-impedance state if it is a "one". If $\overline{BUSEN}$ is a "zero" normal operation of the data buffer and control signals take place.

8228 BLOCK DIAGRAM





STATUS WORD CHART

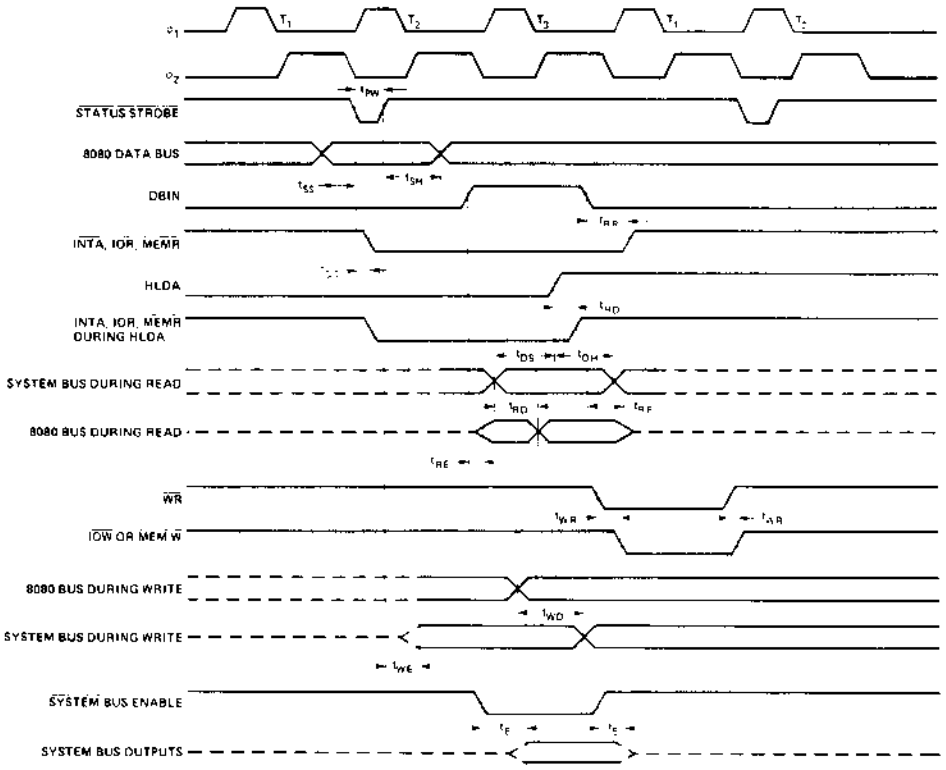
TYPE OF MACHINE CYCLE

DATA BUS BIT	STATUS INFORMATION	INSTRUCTION FETCH	MEMORY READ	MEMORY WRITE	STACK READ	STACK WRITE	INPUT READ	OUTPUT WRITE	INTERRUPT ACKNOWLEDGE	HALT ACKNOWLEDGE	INTERRUPT ACKNOWLEDGE WHILE HALT
		(1)	(2)	(3)	(4)	(5)	(6)	(7)	(8)	(9)	(10)
D_0	INTA	0	0	0	0	0	0	0	1	0	1
D_1	$\overline{WO}$	1	1	0	1	0	1	0	1	1	1
D_2	STACK	0	0	0	1	1	0	0	0	0	0
D_3	HLTA	0	0	0	0	0	0	0	0	1	1
D_4	OUT	0	0	0	0	0	0	1	0	0	0
D_5	M_1	1	0	0	0	0	0	0	1	0	1
D_6	INP	0	0	0	0	0	1	0	0	0	0
D_7	MEMR	1	1	0	1	0	0	0	0	1	0

(N) STATUS WORD

CONTROL SIGNALS:
- $\overline{INTA}$
- (NONE)
- $\overline{INTA}$
- $\overline{I/O\ W}$
- $\overline{I/O\ R}$
- $\overline{MEM\ W}$
- $\overline{MEM\ R}$
- $\overline{MEM\ W}$
- $\overline{MEM\ R}$
- $\overline{MEM\ R}$

WAVEFORMS



VOLTAGE MEASUREMENT POINTS: D_0-D_7 (when outputs) Logic "0" = 0.8V, Logic "1" = 3.0V. All other signals measured at 1.5V.

A.C. Characteristics $T_A = 0°C$ to $70°C$; $V_{CC} = 5V \pm 5\%$.

Symbol	Parameter	Limits Min.	Limits Max.	Units	Condition
t_{PW}	Width of Status Strobe	22		ns	
t_{SS}	Setup Time, Status Inputs D_0-D_7	8		ns	
t_{SH}	Hold Time, Status Inputs D_0-D_7	5		ns	
t_{DC}	Delay from $\overline{STSTB}$ to any Control Signal	20	60	ns	C_L = 100pF
t_{RR}	Delay from DBIN to Control Outputs		30	ns	C_L = 100pF
t_{RE}	Delay from DBIN to Enable/Disable 8080 Bus		45	ns	C_L = 25pF
t_{RD}	Delay from System Bus to 8080 Bus during Read		30	ns	C_L = 25pF
t_{WR}	Delay from $\overline{WR}$ to Control Outputs	5	45	ns	C_L = 100pF
t_{WE}	Delay to Enable System Bus DB_0-DB_7 after $\overline{STSTB}$		30	ns	C_L = 100pF
t_{WD}	Delay from 8080 Bus D_0-D_7 to System Bus DB_0-DB_7 during Write	5	40	ns	C_L = 100pF
t_E	Delay from System Bus Enable to System Bus DB_0-DB_7		30	ns	C_L = 100pF
t_{HD}	HLDA to Read Status Outputs		25	ns	
t_{DS}	Setup Time, System Bus Inputs to HLDA	10		ns	
t_{DH}	Hold Time, System Bus Inputs to HLDA	20		ns	C_L = 100pF

D.C. Characteristics $T_A = 0°C$ to $70°C$; $V_{CC} = 5V \pm 5\%$.

Symbol	Parameter	Limits Min.	Typ.[1]	Max.	Unit	Test Conditions
V_C	Input Clamp Voltage, All Inputs		.75	-1.0	V	V_{CC}=4.75V; I_C=-5mA
I_F	Input Load Current, $\overline{STSTB}$			500	μA	V_{CC} = 5.25V
	D_2 & D_6			750	μA	V_F = 0.45V
	D_0, D_1, D_4, D_5, & D_7			250	μA	
	All Other Inputs			250	μA	
I_R	Input Leakage Current $\overline{STSTB}$			100	μA	V_{CC} = 5.25V
	DB_0-DB_7			20	μA	V_R = 5.25V
	All Other Inputs			100	μA	
V_{TH}	Input Threshold Voltage, All Inputs	0.8		2.0	V	V_{CC} = 5V
I_{CC}	Power Supply Current		140	190	mA	V_{CC}=5.25V
V_{OL}	Output Low Voltage, D_0-D_7			.45	V	V_{CC}=4.75V; I_{OL}=2mA
	All Other Outputs			.45	V	I_{OL} = 10mA
V_{OH}	Output High Voltage, D_0-D_7	3.6	3.8		V	V_{CC}=4.75V; I_{OH}=-10μA
	All Other Outputs	2.4			V	I_{OH} = -1mA
I_{OS}	Short Circuit Current, All Outputs	15		90	mA	V_{CC}=5V
$I_{O(off)}$	Off State Output Current, All Control Outputs			100	μA	V_{CC}=5.25V; V_O=5.25
				-100	μA	V_O=.45V
I_{INT}	INTA Current			5	mA	(See Figure below)

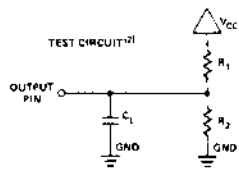
Note 1: Typical values are for T_A = 25°C and nominal supply voltages.

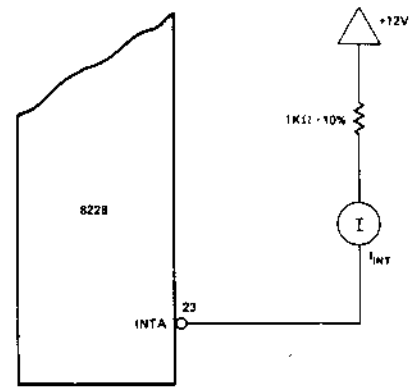
Capacitance This parameter is periodically sampled and not 100% tested.

Symbol	Parameter	Limits Min.	Typ.[1]	Max.	Unit
C_{IN}	Input Capacitance		8	12	pF
C_{OUT}	Output Capacitance Control Signals		7	15	pF
I/O	I/O Capacitance (D or DB)		8	15	pF

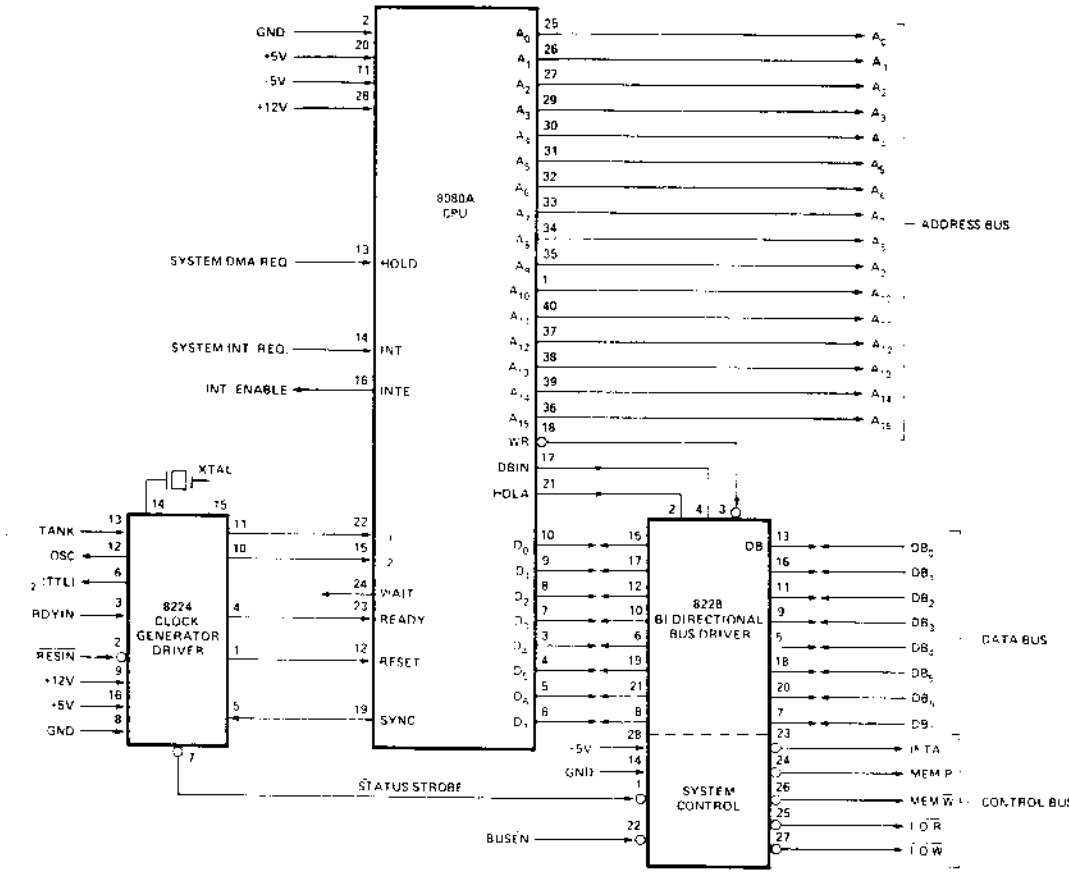
TEST CONDITIONS: V_{BIAS} = 2.5V, V_{CC} = 5.0V, T_A = 25°C, f = 1MHz.

Note 2: For D_0-D_7: R_1 = 4KΩ, R_2 = ∞Ω, C_L = 25pF. For all other outputs: R_1 = 500Ω, R_2 = 1KΩ, C_L = 100pF.





INTA Test Circuit (for RST 7)



8080A CPU Standard Interface

Silicon Gate MOS 8080A

SINGLE CHIP 8-BIT N-CHANNEL MICROPROCESSOR

The 8080A is functionally and electrically compatible with the Intel® 8080.

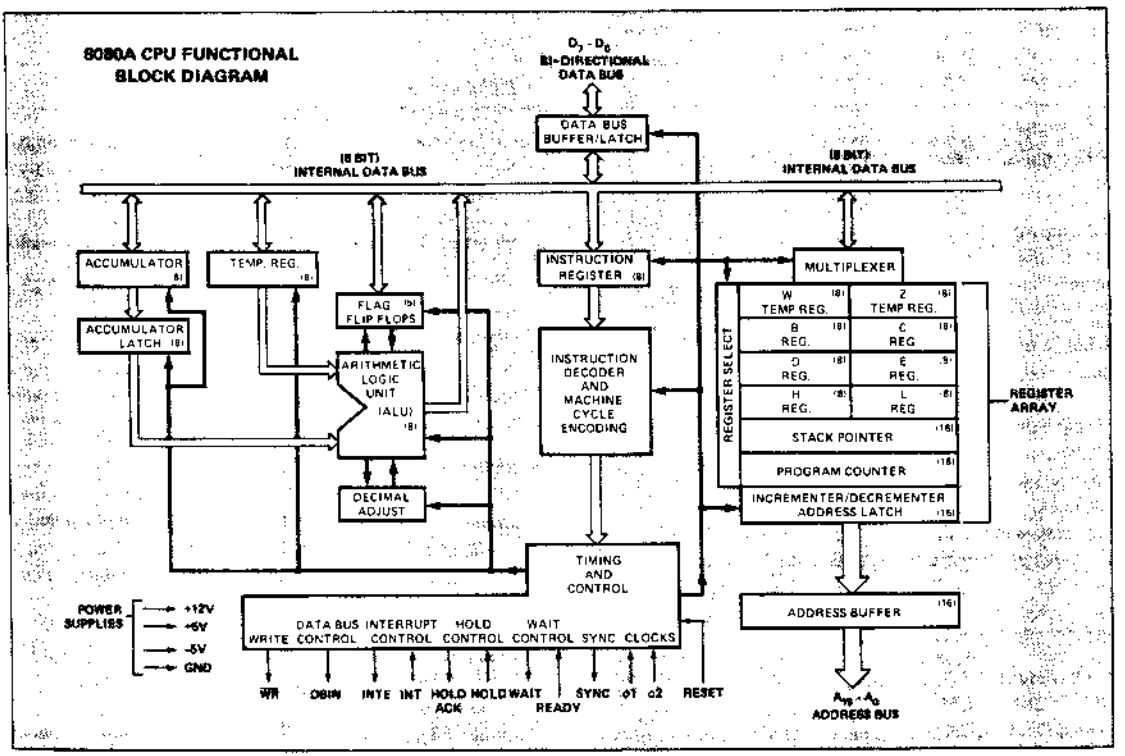
- **TTL Drive Capability**
- **2 μs Instruction Cycle**
- **Powerful Problem Solving Instruction Set**
- **Six General Purpose Registers and an Accumulator**
- **Sixteen Bit Program Counter for Directly Addressing up to 64K Bytes of Memory**
- **Sixteen Bit Stack Pointer and Stack Manipulation Instructions for Rapid Switching of the Program Environment**
- **Decimal, Binary and Double Precision Arithmetic**
- **Ability to Provide Priority Vectored Interrupts**
- **512 Directly Addressed I/O Ports**

The Intel® 8080A is a complete 8-bit parallel central processing unit (CPU). It is fabricated on a single LSI chip using Intel's n-channel silicon gate MOS process. This offers the user a high performance solution to control and processing applications.

The 8080A contains six 8-bit general purpose working registers and an accumulator. The six general purpose registers may be addressed individually or in pairs providing both single and double precision operators. Arithmetic and logical instructions set or reset four testable flags. A fifth flag provides decimal arithmetic operation.

The 8080A has an external stack feature wherein any portion of memory may be used as a last in/first out stack to store/retrieve the contents of the accumulator, flags, program counter and all of the six general purpose registers. The sixteen bit stack pointer controls the addressing of this external stack. This stack gives the 8080A the ability to easily handle multiple level priority interrupts by rapidly storing and restoring processor status. It also provides almost unlimited subroutine nesting.

This microprocessor has been designed to simplify systems design. Separate 16-line address and 8-line bi-directional data busses are used to facilitate easy interface to memory and I/O. Signals to control the interface to memory and I/O are provided directly by the 8080A. Ultimate control of the address and data busses resides with the HOLD signal. It provides the ability to suspend processor operation and force the address and data busses into a high impedance state. This permits OR-tying these busses with other controlling devices for (DMA) direct memory access or multi-processor operation.



8080A FUNCTIONAL PIN DEFINITION

The following describes the function of all of the 8080A I/O pins. Several of the descriptions refer to internal timing periods.

A_{15}-A_0 (output three-state)
ADDRESS BUS; the address bus provides the address to memory (up to 64K 8-bit words) or denotes the I/O device number for up to 256 input and 256 output devices. A_0 is the least significant address bit.

D_7-D_0 (input/output three-state)
DATA BUS; the data bus provides bi-directional communication between the CPU, memory, and I/O devices for instructions and data transfers. Also, during the first clock cycle of each machine cycle, the 8080A outputs a status word on the data bus that describes the current machine cycle. D_0 is the least significant bit.

SYNC (output)
SYNCHRONIZING SIGNAL; the SYNC pin provides a signal to indicate the beginning of each machine cycle.

DBIN (output)
DATA BUS IN; the DBIN signal indicates to external circuits that the data bus is in the input mode. This signal should be used to enable the gating of data onto the 8080A data bus from memory or I/O.

READY (input)
READY; the READY signal indicates to the 8080A that valid memory or input data is available on the 8080A data bus. This signal is used to synchronize the CPU with slower memory or I/O devices. If after sending an address out the 8080A does not receive a READY input, the 8080A will enter a WAIT state for as long as the READY line is low. READY can also be used to single step the CPU.

WAIT (output)
WAIT; the WAIT signal acknowledges that the CPU is in a WAIT state.

$\overline{WR}$ (output)
WRITE; the $\overline{WR}$ signal is used for memory WRITE or I/O output control. The data on the data bus is stable while the $\overline{WR}$ signal is active low ($\overline{WR}$ = 0).

HOLD (input)
HOLD; the HOLD signal requests the CPU to enter the HOLD state. The HOLD state allows an external device to gain control of the 8080A address and data bus as soon as the 8080A has completed its use of these buses for the current machine cycle. It is recognized under the following conditions:

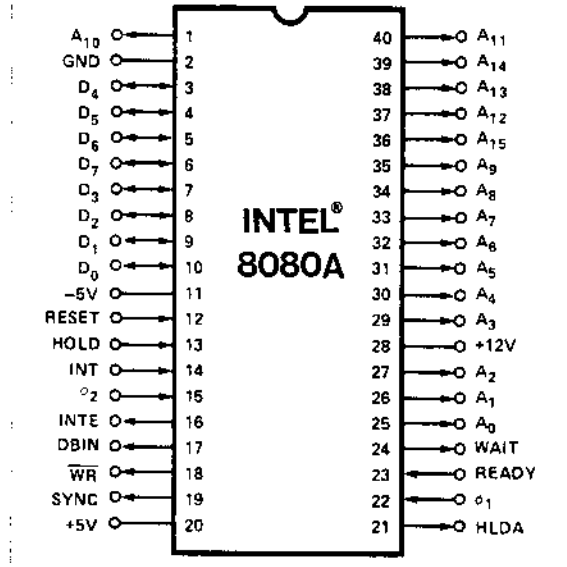
- the CPU is in the HALT state.
- the CPU is in the T2 or TW state and the READY signal is active.

As a result of entering the HOLD state the CPU ADDRESS BUS (A_{15}-A_0) and DATA BUS (D_7-D_0) will be in their high impedance state. The CPU acknowledges its state with the HOLD ACKNOWLEDGE (HLDA) pin.

HLDA (output)
HOLD ACKNOWLEDGE; the HLDA signal appears in response to the HOLD signal and indicates that the data and address bus will go to the high impedance state. The HLDA signal begins at

- T3 for READ memory or input.
- The Clock Period following T3 for WRITE memory or OUTPUT operation.

In either case, the HLDA signal appears after the rising edge of ϕ and high impedance occurs after the rising edge of ϕ_2.



Pin Configuration

INTE (output)
INTERRUPT ENABLE; indicates the content of the internal interrupt enable flip/flop. This flip/flop may be set or reset by the Enable and Disable Interrupt instructions and inhibits interrupts from being accepted by the CPU when it is reset. It is automatically reset (disabling further interrupts) at time T1 of the instruction fetch cycle (M1) when an interrupt is accepted and is also reset by the RESET signal.

INT (input)
INTERRUPT REQUEST; the CPU recognizes an interrupt request on this line at the end of the current instruction or while halted. If the CPU is in the HOLD state or if the Interrupt Enable flip/flop is reset it will not honor the request.

RESET (input)[1]
RESET; while the RESET signal is activated, the content of the program counter is cleared. After RESET, the program will start at location 0 in memory. The INTE and HLDA flip/flops are also reset. Note that the flags, accumulator, stack pointer, and registers are not cleared.

V_{SS}	Ground Reference.
V_{DD}	+12 ± 5% Volts.
V_{CC}	+5 ± 5% Volts.
V_{BB}	-5 ±5% Volts (substrate bias).
ϕ_1, ϕ_2	2 externally supplied clock phases. (non TTL compatible

ABSOLUTE MAXIMUM RATINGS*

Temperature Under Bias	0°C to +70° C
Storage Temperature	-65°C to +150°C
All Input or Output Voltages With Respect to V_{BB}	-0.3V to +20V
V_{CC}, V_{DD} and V_{SS} With Respect to V_{BB}	-0.3V to +20V
Power Dissipation	1.5W

*COMMENT: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

D.C. CHARACTERISTICS

T_A = 0°C to 70°C, V_{DD} = +12V ± 5%, V_{CC} = +5V ± 5%, V_{BB} = -5V ± 5%, V_{SS} = 0V, Unless Otherwise Noted.

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Condition
V_{ILC}	Clock Input Low Voltage	V_{SS}-1		V_{SS}+0.8	V	
V_{IHC}	Clock Input High Voltage	9.0		V_{DD}+1	V	
V_{IL}	Input Low Voltage	V_{SS}-1		V_{SS}+0.8	V	
V_{IH}	Input High Voltage	3.3		V_{CC}+1	V	
V_{OL}	Output Low Voltage			0.45	V	I_{OL} = 1.9mA on all outputs, I_{OH} = -150μA.
V_{OH}	Output High Voltage	3.7			V	
$I_{DD(AV)}$	Avg. Power Supply Current (V_{DD})		40	70	mA	Operation T_{CY} = .48 μsec
$I_{CC(AV)}$	Avg. Power Supply Current (V_{CC})		60	80	mA	
$I_{BB(AV)}$	Avg. Power Supply Current (V_{BB})		.01	1	mA	
I_{IL}	Input Leakage			±10	μA	$V_{SS} \leq V_{IN} \leq V_{CC}$
I_{CL}	Clock Leakage			±10	μA	$V_{SS} \leq V_{CLOCK} \leq V_{DD}$
I_{DL} [2]	Data Bus Leakage in Input Mode			-100 -2.0	μA mA	$V_{SS} \leq V_{IN} \leq V_{SS}$ + 0.8V V_{SS} + 0.8V $\leq V_{IN} \leq V_{CC}$
I_{FL}	Address and Data Bus Leakage During HOLD			+10 -100	μA	$V_{ADDR/DATA} = V_{CC}$ $V_{ADDR/DATA} = V_{SS}$ + 0.45V

CAPACITANCE

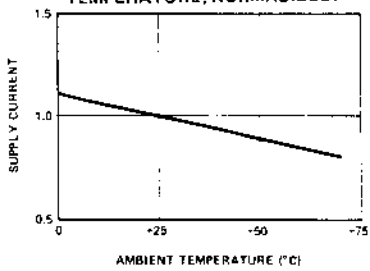
T_A = 25°C $V_{CC} = V_{DD} = V_{SS}$ = 0V, V_{BB} = -5V

Symbol	Parameter	Typ.	Max.	Unit	Test Condition
C_ϕ	Clock Capacitance	17	25	pf	f_c = 1 MHz
C_{IN}	Input Capacitance	6	10	pf	Unmeasured Pins
C_{OUT}	Output Capacitance	10	20	pf	Returned to V_{SS}

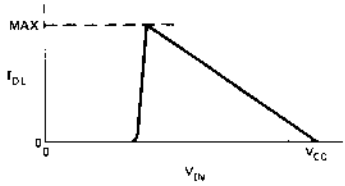
NOTES:

1. The RESET signal must be active for a minimum of 3 clock cycles.
2. When DBIN is high and $V_{IN} > V_{IH}$ an internal active pull up will be switched onto the Data Bus.
3. ΔI supply / ΔT_A = -0.45%/°C.

TYPICAL SUPPLY CURRENT VS. TEMPERATURE, NORMALIZED.[3]



DATA BUS CHARACTERISTIC DURING DBIN



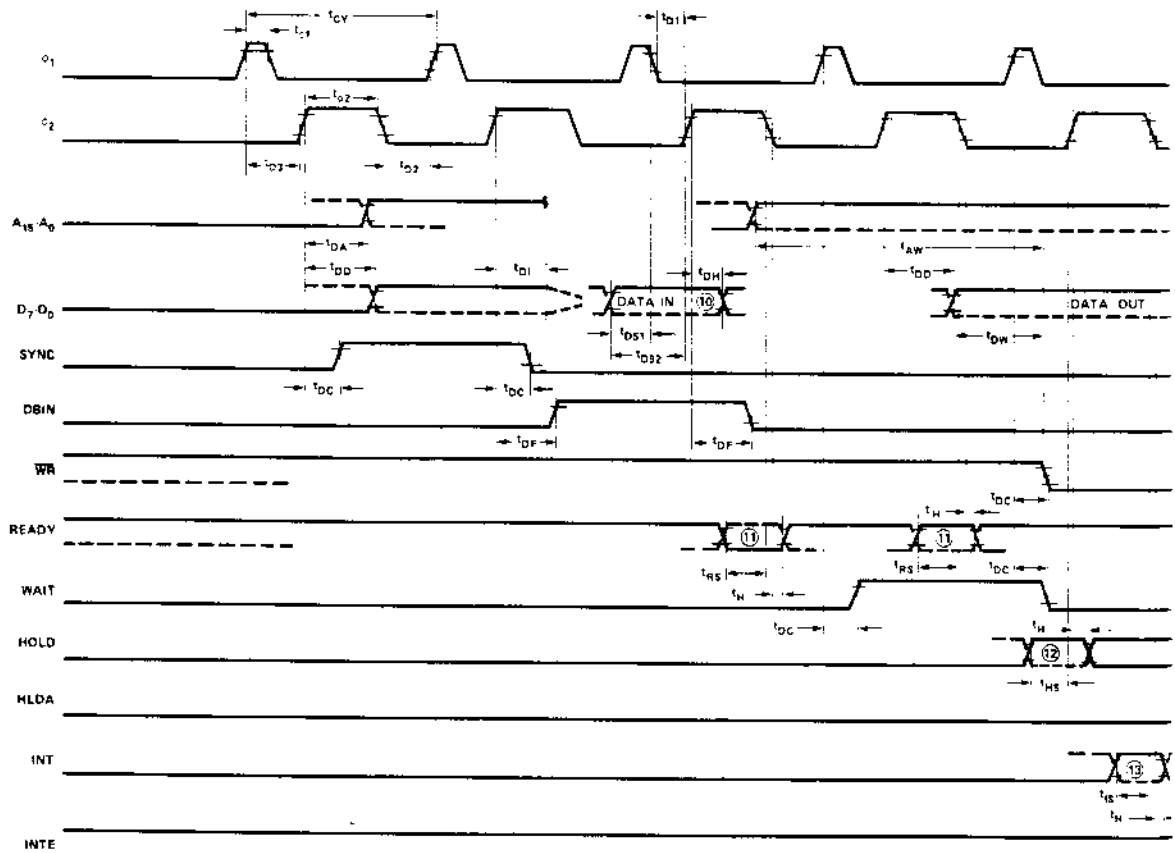
A.C. CHARACTERISTICS

T_A = 0°C to 70°C, V_{DD} = +12V ± 5%, V_{CC} = +5V ± 5%, V_{BB} = -5V ± 5%, V_{SS} = 0V, Unless Otherwise Noted

Symbol	Parameter	Min.	Max.	Unit	Test Condition
t_{CY}[3]	Clock Period	0.48	2.0	μsec	
t_r, t_f	Clock Rise and Fall Time	0	50	nsec	
$t_{\phi 1}$	ϕ_1 Pulse Width	60		nsec	
$t_{\phi 2}$	ϕ_2 Pulse Width	220		nsec	
t_{D1}	Delay ϕ_1 to ϕ_2	0		nsec	
t_{D2}	Delay ϕ_2 to ϕ_1	70		nsec	
t_{D3}	Delay ϕ_1 to ϕ_2 Leading Edges	80		nsec	
t_{DA}[2]	Address Output Delay From ϕ_2		200	nsec	C_L = 100pf
t_{DD}[2]	Data Output Delay From ϕ_2		220	nsec	
t_{DC}[2]	Signal Output Delay From ϕ_1, or ϕ_2 (SYNC, $\overline{WR}$,WAIT,HLDA)		120	nsec	C_L = 50pf
t_{DF}[2]	DBIN Delay From ϕ_2	25	140	nsec	
t_{DI}[1]	Delay for Input Bus to Enter Input Mode		t_{DF}	nsec	
t_{DS1}	Data Setup Time During ϕ_1 and DBIN	30		nsec	

TIMING WAVEFORMS [14]

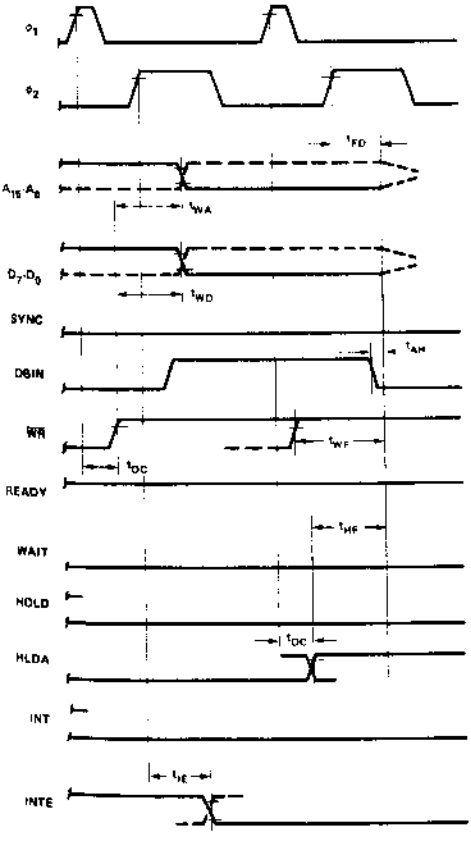
(Note: Timing measurements are made at the following reference voltages: CLOCK "1" = 8.0V "0" = 1.0V; INPUTS "1" = 3.3V, "0" = 0.8V; OUTPUTS "1" = 2.0V, "0" = 0.8V.)



A.C. CHARACTERISTICS (Continued)

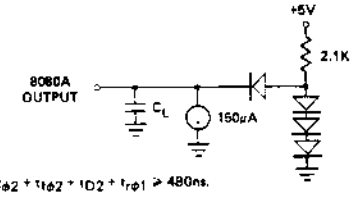
T_A = 0°C to 70°C, V_{DD} = +12V ± 5%, V_{CC} = +5V ± 5%, V_{BB} = -5V ± 5%, V_{SS} = 0V, Unless Otherwise Noted

Symbol	Parameter	Min.	Max.	Unit	Test Condition
t_{DS2}	Data Setup Time to ϕ_2 During DBIN	150		nsec	
t_{DH} [1]	Data Hold Time From ϕ_2 During DBIN	[1]		nsec	
t_{IE} [2]	INTE Output Delay From ϕ_2		200	nsec	C_L = 50pf
t_{RS}	READY Setup Time During ϕ_2	120		nsec	
t_{HS}	HOLD Setup Time to ϕ_2	140		nsec	
t_{IS}	INT Setup Time During ϕ_2 (During ϕ_1 in Halt Mode)	120		nsec	
t_H	Hold Time From ϕ_2 (READY, INT, HOLD)	0		nsec	
t_{FD}	Delay to Float During Hold (Address and Data Bus)		120	nsec	
t_{AW} [2]	Address Stable Prior to $\overline{WR}$	[5]		nsec	C_L = 100pf: Address, Data C_L = 50pf: $\overline{WR}$, HLDA, DBIN
t_{DW} [2]	Output Data Stable Prior to $\overline{WR}$	[6]		nsec	
t_{WD} [2]	Output Data Stable From $\overline{WR}$	[7]		nsec	
t_{WA} [2]	Address Stable From $\overline{WR}$	[7]		nsec	
t_{HF} [2]	HLDA to Float Delay	[8]		nsec	
t_{WF} [2]	$\overline{WR}$ to Float Delay	[9]		nsec	
t_{AH} [2]	Address Hold Time After DBIN During HLDA	-20		nsec	



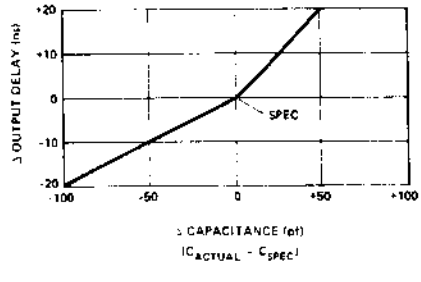
NOTES:

1. Data input should be enabled with DBIN status. No bus conflict can then occur and data hold time is assured. t_{DH} = 50 ns or t_{DF}, whichever is less
2. Load Circuit.



3. $t_{CY} = t_{D3} + t_{r\phi2} + t_{\phi2} + t_{t\phi2} + t_{D2} + t_{r\phi1} \geq 480$ns.

TYPICAL Δ OUTPUT DELAY VS. Δ CAPACITANCE



4. The following are relevant when interfacing the 8080A to devices having V_{IH} = 3.3V:
   a) Maximum output rise time from .8V to 3.3V = 100ns @ C_L = SPEC.
   b) Output delay when measured to 3.0V = SPEC +60ns @ C_L = SPEC.
   c) If $C_L \neq$ SPEC, add .6ns/pF if $C_L > C_{SPEC}$, subtract .3ns/pF (from modified delay) if $C_L < C_{SPEC}$.
5. $t_{AW} = 2\,t_{CY} - t_{D3} - t_{r\phi2} - 140$nsec
6. $t_{DW} = t_{CY} - t_{D3} - t_{r\phi2} - 170$nsec.
7. If not HLDA, $t_{WD} = t_{WA} = t_{D3} + t_{r\phi2} + 10$ns. If HLDA, $t_{WD} = t_{WA} = t_{WF}$.
8. $t_{HF} = t_{D3} + t_{\phi2} - 50$ns.
9. $t_{WF} = t_{D3} + t_{r\phi2} - 10$ns
10. Data in must be stable for this period during DBIN $\cdot T_3$. Both t_{DS1} and t_{DS2} must be satisfied.
11. Ready signal must be stable for this period during T_2 or T_W. (Must be externally synchronized.)
12. Hold signal must be stable for this period during T_2 or T_W when entering hold mode, and during T_3, T_4, T_5 and T_{WH} when in hold mode. (External synchronization is not required.)
13. Interrupt signal must be stable during this period of the last clock cycle of any instruction in order to be recognized on the following instruction. (External synchronization is not required.)
14. This timing diagram shows timing relationships only; it does not represent any specific machine cycle.

INSTRUCTION SET

The accumulator group instructions include arithmetic and logical operators with direct, indirect, and immediate addressing modes.

Move, load, and store instruction groups provide the ability to move either 8 or 16 bits of data between memory, the six working registers and the accumulator using direct, indirect, and immediate addressing modes.

The ability to branch to different portions of the program is provided with jump, jump conditional, and computed jumps. Also the ability to call to and return from subroutines is provided both conditionally and unconditionally. The RESTART (or single byte call instruction) is useful for interrupt vector operation.

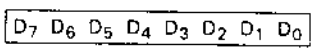
Double precision operators such as stack manipulation and double add instructions extend both the arithmetic and interrupt handling capability of the 8080A. The ability to increment and decrement memory, the six general registers and the accumulator is provided as well as extended increment and decrement instructions to operate on the register pairs and stack pointer. Further capability is provided by the ability to rotate the accumulator left or right through or around the carry bit.

Input and output may be accomplished using memory addresses as I/O ports or the directly addressed I/O provided for in the 8080A instruction set.

The following special instruction group completes the 8080A instruction set: the NOP instruction, HALT to stop processor execution and the DAA instructions provide decimal arithmetic capability. STC allows the carry flag to be directly set, and the CMC instruction allows it to be complemented. CMA complements the contents of the accumulator and XCHG exchanges the contents of two 16-bit register pairs directly.

Data and Instruction Formats

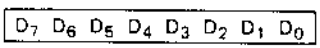
Data in the 8080A is stored in the form of 8-bit binary integers. All data transfers to the system data bus will be in the same format.



DATA WORD

The program instructions may be one, two, or three bytes in length. Multiple byte instructions must be stored in successive words in program memory. The instruction formats then depend on the particular operation executed.

One Byte Instructions

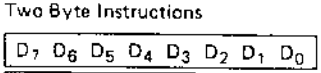


OP CODE

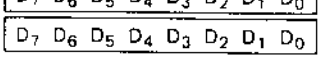
TYPICAL INSTRUCTIONS

Register to register, memory reference, arithmetic or logical, rotate, return, push, pop, enable or disable interrupt instructions

Two Byte Instructions



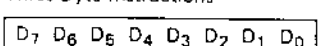
OP CODE



OPERAND

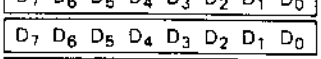
Immediate mode or I/O instructions

Three Byte Instructions

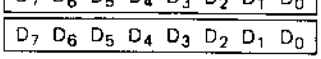


OP CODE

Jump, call or direct load and store instructions



LOW ADDRESS OR OPERAND 1



HIGH ADDRESS OR OPERAND 2

For the 8080A a logic "1" is defined as a high level and a logic "0" is defined as a low level.

INSTRUCTION SET

Summary of Processor Instructions

Mnemonic	Description	Instruction Code[1] D_7	D_6	D_5	D_4	D_3	D_2	D_1	D_0	Clock[2] Cycles
MOV$_{r1, r2}$	Move register to register	0	1	0	0	0	S	S	S	5
MOV M, r	Move register to memory	0	1	1	1	0	S	S	S	7
MOV r, M	Move memory to register	0	1	0	0	0	1	1	0	7
HLT	Halt	0	1	1	1	0	1	1	0	7
MVI r	Move immediate register	0	0	0	D	D	D	1	0	7
MVI M	Move immediate memory	0	0	1	1	0	1	1	0	10
INR r	Increment register	0	0	0	D	D	D	1	0	5
DCR r	Decrement register	0	0	0	D	D	D	1	1	5
INR M	Increment memory	0	0	1	1	0	1	0	0	10
DCR M	Decrement memory	0	0	1	1	0	1	0	1	10
ADD r	Add register to A	1	0	0	0	0	S	S	S	4
ADC r	Add register to A with carry	1	0	0	0	1	S	S	S	4
SUB r	Subtract register from A	1	0	0	1	0	S	S	S	4
SBB r	Subtract register from A with borrow	1	0	0	1	1	S	S	S	4
ANA r	And register with A	1	0	1	0	0	S	S	S	4
XRA r	Exclusive Or register with A	1	0	1	0	1	S	S	S	4
ORA r	Or register with A	1	0	1	1	0	S	S	S	4
CMP r	Compare register with A	1	0	1	1	1	S	S	S	4
ADD M	Add memory to A	1	0	0	0	0	1	1	0	7
ADC M	Add memory to A with carry	1	0	0	0	1	1	1	0	7
SUB M	Subtract memory from A	1	0	0	1	0	1	1	0	7
SBB M	Subtract memory from A with borrow	1	0	0	1	1	1	1	0	7
ANA M	And memory with A	1	0	1	0	0	1	1	0	7
XRA M	Exclusive Or memory with A	1	0	1	0	1	1	1	0	7
ORA M	Or memory with A	1	0	1	1	0	1	1	0	7
CMP M	Compare memory with A	1	0	1	1	1	1	1	0	7
ADI	Add immediate to A	1	1	0	0	0	1	1	0	7
ACI	Add immediate to A with carry	1	1	0	0	1	1	1	0	7
SUI	Subtract immediate from A	1	1	0	1	0	1	1	0	7
SBI	Subtract immediate from A with borrow	1	1	0	1	1	1	1	0	7
ANI	And immediate with A	1	1	1	0	0	1	1	0	7
XRI	Exclusive Or immediate with A	1	1	1	0	1	1	1	0	7
ORI	Or immediate with A	1	1	1	1	0	1	1	0	7
CPI	Compare immediate with A	1	1	1	1	1	1	1	0	7
RLC	Rotate A left	0	0	0	0	0	1	1	1	4
RRC	Rotate A right	0	0	0	0	1	1	1	1	4
RAL	Rotate A left through carry	0	0	0	1	0	1	1	1	4
RAR	Rotate A right through carry	0	0	0	1	1	1	1	1	4
JMP	Jump unconditional	1	1	0	0	0	0	1	1	10
JC	Jump on carry	1	1	0	1	1	0	1	0	10
JNC	Jump on no carry	1	1	0	1	0	0	1	0	10
JZ	Jump on zero	1	1	0	0	1	0	1	0	10
JNZ	Jump on no zero	1	1	0	0	0	0	1	0	10
JP	Jump on positive	1	1	1	1	0	0	1	0	10
JM	Jump on minus	1	1	1	1	1	0	1	0	10
JPE	Jump on parity even	1	1	1	0	1	0	1	0	10
JPO	Jump on parity odd	1	1	1	0	0	0	1	0	10
CALL	Call unconditional	1	1	0	0	1	1	0	1	17
CC	Call on carry	1	1	0	1	1	1	0	0	11/17
CNC	Call on no carry	1	1	0	1	0	1	0	0	11/17
CZ	Call on zero	1	1	0	0	1	1	0	0	11/17
CNZ	Call on no zero	1	1	0	0	0	1	0	0	11/17
CP	Call on positive	1	1	1	1	0	1	0	0	11/17
CM	Call on minus	1	1	1	1	1	1	0	0	11/17
CPE	Call on parity even	1	1	1	0	1	1	0	0	11/17
CPO	Call on parity odd	1	1	1	0	0	1	0	0	11/17
RET	Return	1	1	0	0	1	0	0	1	10
RC	Return on carry	1	1	0	1	1	0	0	0	5/11
RNC	Return on no carry	1	1	0	1	0	0	0	0	5/11
RZ	Return on zero	1	1	0	0	1	0	0	0	5/11
RNZ	Return on no zero	1	1	0	0	0	0	0	0	5/11
RP	Return on positive	1	1	1	1	0	0	0	0	5/11
RM	Return on minus	1	1	1	1	1	0	0	0	5/11
RPE	Return on parity even	1	1	1	0	1	0	0	0	5/11
RPO	Return on parity odd	1	1	1	0	0	0	0	0	5/11
RST	Restart	1	1	A	A	A	1	1	1	11
IN	Input	1	1	0	1	1	0	1	1	10
OUT	Output	1	1	0	1	0	0	1	1	10
LXI B	Load immediate register Pair B & C	0	0	0	0	0	0	0	1	10
LXI D	Load immediate register Pair D & E	0	0	0	1	0	0	0	1	10
LXI H	Load immediate register Pair H & L	0	0	1	0	0	0	0	1	10
LXI SP	Load immediate stack pointer	0	0	1	1	0	0	0	1	10
PUSH B	Push register Pair B & C on stack	1	1	0	0	0	1	0	1	11
PUSH D	Push register Pair D & E on stack	1	1	0	1	0	1	0	1	11
PUSH H	Push register Pair H & L on stack	1	1	1	0	0	1	0	1	11
PUSH PSW	Push A and Flags on stack	1	1	1	1	0	1	0	1	11
POP B	Pop register pair B & C off stack	1	1	0	0	0	0	0	1	10
POP D	Pop register pair D & E off stack	1	1	0	1	0	0	0	1	10
POP H	Pop register pair H & L off stack	1	1	1	0	0	0	0	1	10
POP PSW	Pop A and Flags off stack	1	1	1	1	0	0	0	1	10
STA	Store A direct	0	0	1	1	0	0	1	0	13
LDA	Load A direct	0	0	1	1	1	0	1	0	13
XCHG	Exchange D & E, H & L Registers	1	1	1	0	1	0	1	1	4
XTHL	Exchange top of stack, H & L	1	1	1	0	0	0	1	1	18
SPHL	H & L to stack pointer	1	1	1	1	1	0	0	1	5
PCHL	H & L to program counter	1	1	1	0	1	0	0	1	5
DAD B	Add B & C to H & L	0	0	0	0	1	0	0	1	10
DAD D	Add D & E to H & L	0	0	0	1	1	0	0	1	10
DAD H	Add H & L to H & L	0	0	1	0	1	0	0	1	10
DAD SP	Add stack pointer to H & L	0	0	1	1	1	0	0	1	10
STAX B	Store A indirect	0	0	0	0	0	0	1	0	7
STAX D	Store A indirect	0	0	0	1	0	0	1	0	7
LDAX B	Load A indirect	0	0	0	0	1	0	1	0	7
LDAX D	Load A indirect	0	0	0	1	1	0	1	0	7
INX B	Increment B & C registers	0	0	0	0	0	0	1	1	5
INX D	Increment D & E registers	0	0	0	1	0	0	1	1	5
INX H	Increment H & L registers	0	0	1	0	0	0	1	1	5
INX SP	Increment stack pointer	0	0	1	1	0	0	1	1	5
DCX B	Decrement B & C	0	0	0	0	1	0	1	1	5
DCX D	Decrement D & E	0	0	0	1	1	0	1	1	5
DCX H	Decrement H & L	0	0	1	0	1	0	1	1	5
DCX SP	Decrement stack pointer	0	0	1	1	1	0	1	1	5
CMA	Complement A	0	0	1	0	1	1	1	1	4
STC	Set carry	0	0	1	1	0	1	1	1	4
CMC	Complement carry	0	0	1	1	1	1	1	1	4
DAA	Decimal adjust A	0	0	1	0	0	1	1	1	4
SHLD	Store H & L direct	0	0	1	0	0	0	1	0	16
LHLD	Load H & L direct	0	0	1	0	1	0	1	0	16
EI	Enable Interrupts	1	1	1	1	1	0	1	1	4
DI	Disable interrupt	1	1	1	1	0	0	1	1	4
NOP	No-operation	0	0	0	0	0	0	0	0	4

NOTES: 1. DDD or SSS – 000 B – 001 C – 010 D – 011 E – 100 H – 101 L – 110 Memory – 111 A.
2. Two possible cycle times, (5/11) indicate instruction cycles dependent on condition flags.

Silicon Gate MOS 8080A-1

SINGLE CHIP 8-BIT N-CHANNEL MICROPROCESSOR

The 8080A is functionally and electrically compatible with the Intel® 8080.

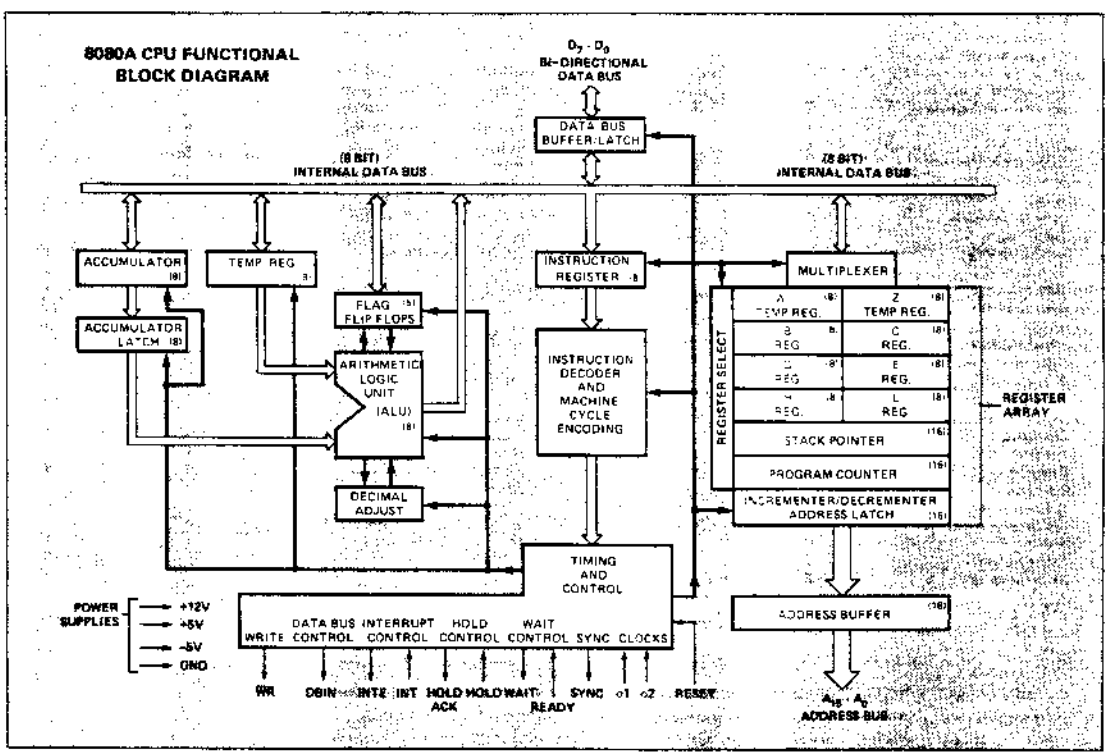
- **TTL Drive Capability**
- **1.3 μs Instruction Cycle**
- **Powerful Problem Solving Instruction Set**
- **Six General Purpose Registers and an Accumulator**
- **Sixteen Bit Program Counter for Directly Addressing up to 64K Bytes of Memory**
- **Sixteen Bit Stack Pointer and Stack Manipulation Instructions for Rapid Switching of the Program Environment**
- **Decimal, Binary and Double Precision Arithmetic**
- **Ability to Provide Priority Vectored Interrupts**
- **512 Directly Addressed I/O Ports**

The Intel® 8080A is a complete 8-bit parallel central processing unit (CPU). It is fabricated on a single LSI chip using Intel's n-channel silicon gate MOS process. This offers the user a high performance solution to control and processing applications.

The 8080A contains six 8-bit general purpose working registers and an accumulator. The six general purpose registers may be addressed individually or in pairs providing both single and double precision operators. Arithmetic and logical instructions set or reset four testable flags. A fifth flag provides decimal arithmetic operation.

The 8080A has an external stack feature wherein any portion of memory may be used as a last in/first out stack to store/retrieve the contents of the accumulator, flags, program counter and all of the six general purpose registers. The sixteen bit stack pointer controls the addressing of this external stack. This stack gives the 8080A the ability to easily handle multiple level priority interrupts by rapidly storing and restoring processor status. It also provides almost unlimited subroutine nesting.

This microprocessor has been designed to simplify systems design. Separate 16-line address and 8-line bi-directional data busses are used to facilitate easy interface to memory and I/O. Signals to control the interface to memory and I/O are provided directly by the 8080A. Ultimate control of the address and data busses resides with the HOLD signal. It provides the ability to suspend processor operation and force the address and data busses into a high impedance state. This permits OR-tying these busses with other controlling devices for (DMA) direct memory access or multi-processor operation.



ABSOLUTE MAXIMUM RATINGS*

Temperature Under Bias	0°C to +70° C
Storage Temperature	-65°C to +150°C
All Input or Output Voltages With Respect to V_{BB}	-0.3V to +20V
V_{CC}, V_{DD} and V_{SS} With Respect to V_{BB}	-0.3V to +20V
Power Dissipation	1.5W

**COMMENT: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.*

D.C. CHARACTERISTICS

T_A = 0°C to 70°C, V_{DD} = +12V ± 5%, V_{CC} = +5V ± 5%, V_{BB} = -5V ± 5%, V_{SS} = 0V, Unless Otherwise Noted.

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Condition
V_{ILC}	Clock Input Low Voltage	$V_{SS}-1$		$V_{SS}+0.8$	V	
V_{IHC}	Clock Input High Voltage	9.0		$V_{DD}+1$	V	
V_{IL}	Input Low Voltage	$V_{SS}-1$		$V_{SS}+0.8$	V	
V_{IH}	Input High Voltage	3.3		$V_{CC}+1$	V	
V_{OL}	Output Low Voltage			0.45	V	I_{OL} = 1.9mA on all outputs, I_{OH} = 150μA.
V_{OH}	Output High Voltage	3.7			V	
$I_{DD(AV)}$	Avg. Power Supply Current (V_{DD})		40	70	mA	Operation T_{CY} = .32μsec
$I_{CC(AV)}$	Avg. Power Supply Current (V_{CC})		60	80	mA	
$I_{BB(AV)}$	Avg. Power Supply Current (V_{BB})		.01	1	mA	
I_{IL}	Input Leakage			±10	μA	$V_{SS} \leq V_{IN} \leq V_{CC}$
I_{CL}	Clock Leakage			±10	μA	$V_{SS} \leq V_{CLOCK} \leq V_{DD}$
I_{DL}[2]	Data Bus Leakage in Input Mode			-100 -2.0	μA mA	$V_{SS} \leq V_{IN} \leq V_{SS}+0.8V$ $V_{SS}+0.8V \leq V_{IN} \leq V_{CC}$
I_{FL}	Address and Data Bus Leakage During HOLD			+10 -100	μA	$V_{ADDR/DATA} = V_{CC}$ $V_{ADDR/DATA} = V_{SS} + 0.45V$

CAPACITANCE

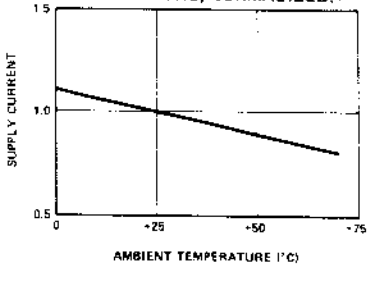
T_A = 25°C $V_{CC} = V_{DD} = V_{SS} = 0V$, $V_{BB} = -5V$

Symbol	Parameter	Typ.	Max.	Unit	Test Condition
C_ϕ	Clock Capacitance	17	25	pf	f_c = 1 MHz
C_{IN}	Input Capacitance	6	10	pf	Unmeasured Pins
C_{OUT}	Output Capacitance	10	20	pf	Returned to V_{SS}

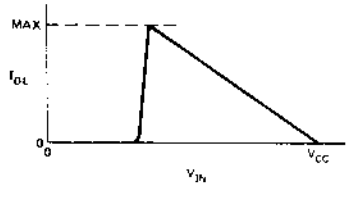
NOTES:

1. The RESET signal must be active for a minimum of 3 clock cycles.
2. When DBIN is high and $V_{IN} > V_{IH}$ an internal active pull up will be switched onto the Data Bus.
3. ΔI supply / ΔT_A = -0.45%/°C.

TYPICAL SUPPLY CURRENT VS. TEMPERATURE, NORMALIZED.[3]



DATA BUS CHARACTERISTIC DURING DBIN



A.C. CHARACTERISTICS

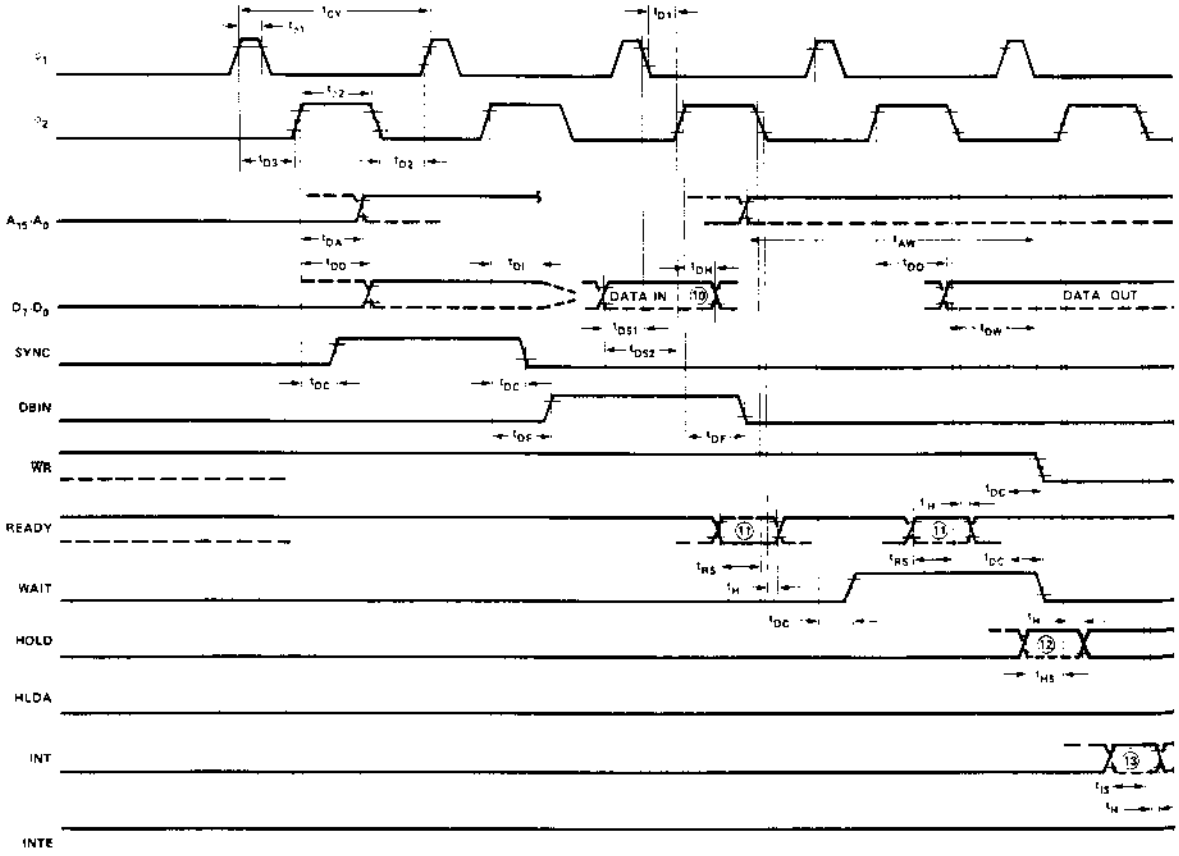
CAUTION: When operating the 8080A-1 at or near full speed, care must be taken to assure precise timing compatibility between 8080A-1, 8224 and 8

T_A = 0°C to 70°C, V_{DD} = +12V ± 5%, V_{CC} = +5V ± 5%, V_{BB} = -5V ± 5%, V_{SS} = 0V, Unless Otherwise Noted

Symbol	Parameter	Min.	Max.	Unit	Test Condition
t_{CY}[3]	Clock Period	320	2.0	μsec	
t_r, t_f	Clock Rise and Fall Time	0	25	nsec	
$t_{\phi 1}$	ϕ_1 Pulse Width	50		nsec	
$t_{\phi 2}$	ϕ_2 Pulse Width	145		nsec	
t_{D1}	Delay ϕ_1 to ϕ_2	0		nsec	
t_{D2}	Delay ϕ_2 to ϕ_1	60		nsec	
t_{D3}	Delay ϕ_1 to ϕ_2 Leading Edges	60		nsec	
t_{DA} [2]	Address Output Delay From ϕ_2		150	nsec	C_L = 50pf
t_{DD} [2]	Data Output Delay From ϕ_2		180	nsec	
t_{DC} [2]	Signal Output Delay From ϕ_1, or ϕ_2 (SYNC, $\overline{WR}$,WAIT,HLDA)		110	nsec	C_L = 50pf
t_{DF} [2]	DBIN Delay From ϕ_2	25	130	nsec	
t_{DI}[1]	Delay for Input Bus to Enter Input Mode		t_{DF}	nsec	
t_{DS1}	Data Setup Time During ϕ_1 and DBIN	10		nsec	

TIMING WAVEFORMS [14]

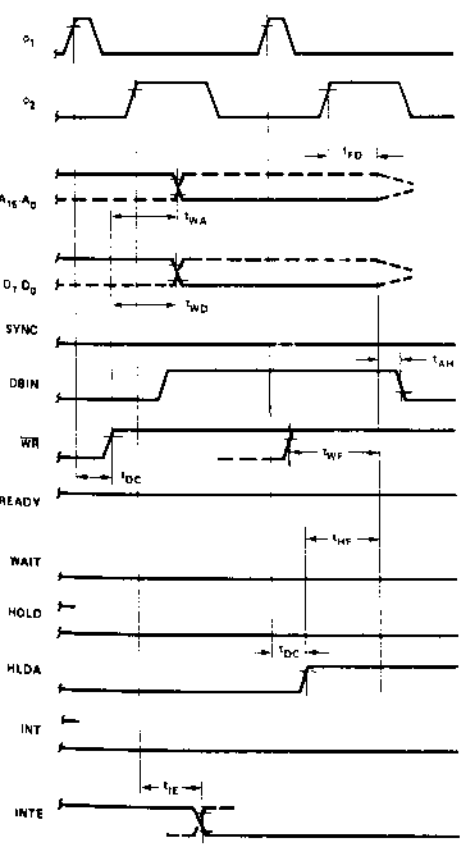
(Note: Timing measurements are made at the following reference voltages: CLOCK "1" = 8.0V "0" = 1.0V; INPUTS "1" = 3.3V, "0" = 0.8V; OUTPUTS "1" = 2.0V, "0" = 0.8V.)



A.C. CHARACTERISTICS (Continued)

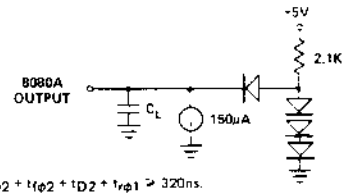
T_A = 0°C to 70°C, V_{DD} = +12V ± 5%, V_{CC} = +5V ± 5%, V_{BB} = -5V ± 5%, V_{SS} = 0V, Unless Otherwise Noted

Symbol	Parameter	Min.	Max.	Unit	Test Condition
t_{DS2}	Data Setup Time to ϕ_2 During DBIN	120		nsec	
t_{DH} [1]	Data Hold Time From ϕ_2 During DBIN	[1]		nsec	
t_{IE} [2]	INTE Output Delay From ϕ_2		200	nsec	C_L = 50pf
t_{RS}	READY Setup Time During ϕ_2	90		nsec	
t_{HS}	HOLD Setup Time to ϕ_2	120		nsec	
t_{IS}	INT Setup Time During ϕ_2 (During ϕ_1 in Halt Mode)	100		nsec	
t_H	Hold Time From ϕ_2 (READY, INT, HOLD)	0		nsec	
t_{FD}	Delay to Float During Hold (Address and Data Bus)		120	nsec	
t_{AW} [2]	Address Stable Prior to $\overline{WR}$	[5]		nsec	C_L = 50pf: Address, Data C_L = 50pf: $\overline{WR}$, HLDA, DBIN
t_{DW} [2]	Output Data Stable Prior to $\overline{WR}$	[6]		nsec	
t_{WD} [2]	Output Data Stable From $\overline{WR}$	[7]		nsec	
t_{WA} [2]	Address Stable From $\overline{WR}$	[7]		nsec	
t_{HF} [2]	HLDA to Float Delay	[8]		nsec	
t_{WF} [2]	$\overline{WR}$ to Float Delay	[9]		nsec	
t_{AH} [2]	Address Hold Time After DBIN During HLDA	-20		nsec	



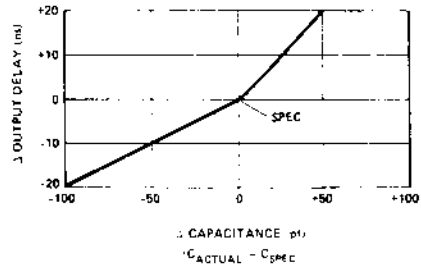
NOTES:

1. Data input should be enabled with DBIN status. No bus conflict can then occur and data hold time is assured. t_{DH} = 50 ns or t_{DF}, whichever is less.
2. Load Circuit.



3. $t_{CY} = t_{D3} + t_{r\phi2} + t_{\phi2} + t_{f\phi2} + t_{D2} + t_{r\phi1} \geq 320$ns.

TYPICAL Δ OUTPUT DELAY VS. Δ CAPACITANCE



4. The following are relevant when interfacing the 8080A to devices having V_{IH} = 3.3V:
   a) Maximum output rise time from .8V to 3.3V = 100ns @ C_L = SPEC.
   b) Output delay when measured to 3.0V = SPEC +60ns @ C_L = SPEC.
   c) If C_L ≠ SPEC, add .6ns/pF if $C_L > C_{SPEC}$, subtract .3ns/pF if from modified delay) if $C_L < C_{SPEC}$.
5. $t_{AW} = 2\,t_{CY} - t_{D3} - t_{r\phi2}$ -110nsec.
6. $t_{DW} = t_{CY} - t_{D3} - t_{r\phi2}$ -150nsec.
7. If not HLDA, $t_{WD} = t_{WA} = t_{D3} + t_{r\phi2}$ +10ns. If HLDA, $t_{WD} = t_{WA} = t_{WF}$.
8. $t_{HF} = t_{D3} + t_{r\phi2}$ -50ns.
9. $t_{WF} = t_{D3} + t_{r\phi2}$ -10ns
10. Data in must be stable for this period during DBIN ·T_3. Both t_{DS1} and t_{DS2} must be satisfied.
11. Ready signal must be stable for this period during T_2 or T_W. (Must be externally synchronized.)
12. Hold signal must be stable for this period during T_2 or T_W when entering hold mode, and during T_3, T_4, T_5 and T_{WH} when in hold mode. (External synchronization is not required.)
13. Interrupt signal must be stable during this period of the last clock cycle of any instruction in order to be recognized on the following instruction. (External synchronization is not required.)
14. This timing diagram shows timing relationships only; it does not represent any specific machine cycle.

Silicon Gate MOS 8080A-2

SINGLE CHIP 8-BIT N-CHANNEL MICROPROCESSOR

The 8080A is functionally and electrically compatible with the Intel® 8080.

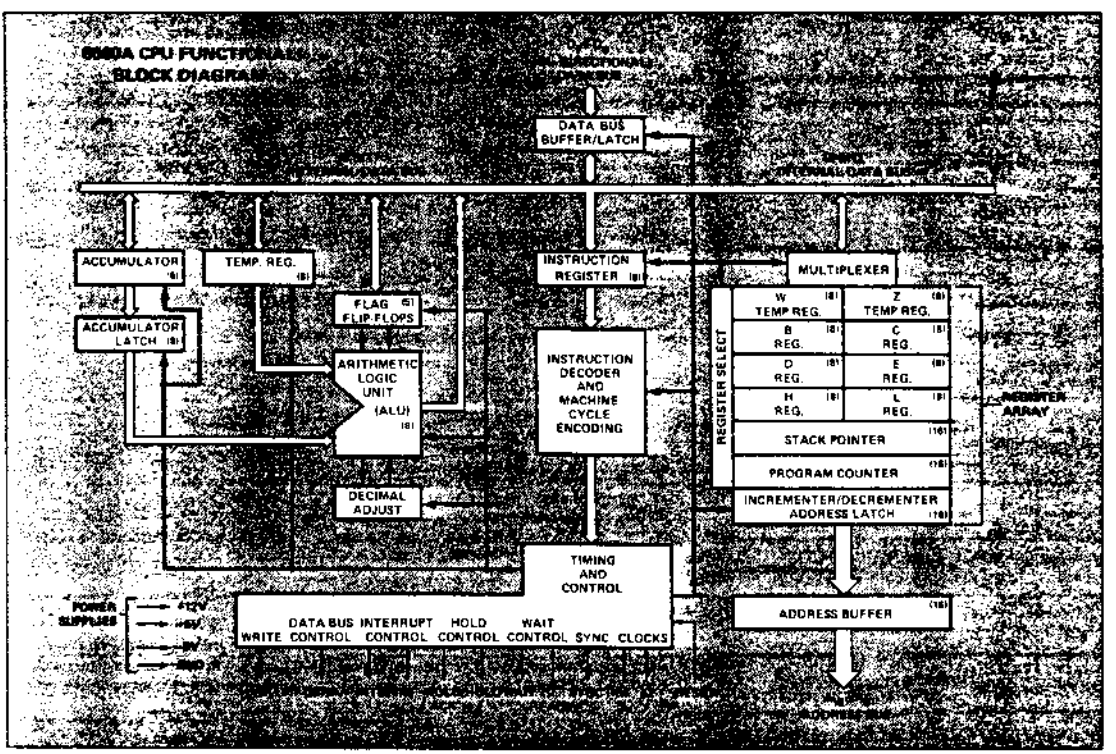
- **TTL Drive Capability**
- **1.5 μs Instruction Cycle**
- **Powerful Problem Solving Instruction Set**
- **Six General Purpose Registers and an Accumulator**
- **Sixteen Bit Program Counter for Directly Addressing up to 64K Bytes of Memory**
- **Sixteen Bit Stack Pointer and Stack Manipulation Instructions for Rapid Switching of the Program Environment**
- **Decimal, Binary and Double Precision Arithmetic**
- **Ability to Provide Priority Vectored Interrupts**
- **512 Directly Addressed I/O Ports**

The Intel® 8080A is a complete 8-bit parallel central processing unit (CPU). It is fabricated on a single LSI chip using Intel's n-channel silicon gate MOS process. This offers the user a high performance solution to control and processing applications.

The 8080A contains six 8-bit general purpose working registers and an accumulator. The six general purpose registers may be addressed individually or in pairs providing both single and double precision operators. Arithmetic and logical instructions set or reset four testable flags. A fifth flag provides decimal arithmetic operation.

The 8080A has an external stack feature wherein any portion of memory may be used as a last in/first out stack to store/retrieve the contents of the accumulator, flags, program counter and all of the six general purpose registers. The sixteen bit stack pointer controls the addressing of this external stack. This stack gives the 8080A the ability to easily handle multiple level priority interrupts by rapidly storing and restoring processor status. It also provides almost unlimited subroutine nesting.

This microprocessor has been designed to simplify systems design. Separate 16-line address and 8-line bi-directional data busses are used to facilitate easy interface to memory and I/O. Signals to control the interface to memory and I/O are provided directly by the 8080A. Ultimate control of the address and data busses resides with the HOLD signal. It provides the ability to suspend processor operation and force the address and data busses into a high impedance state. This permits OR-tying these busses with other controlling devices for (DMA) direct memory access or multi-processor operation.



ABSOLUTE MAXIMUM RATINGS*

Temperature Under Bias	0°C to +70°C
Storage Temperature	-65°C to +150°C
All Input or Output Voltages With Respect to V_{BB}	-0.3V to +20V
V_{CC}, V_{DD} and V_{SS} With Respect to V_{BB}	-0.3V to +20V
Power Dissipation	1.5W

**COMMENT: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.*

D.C. CHARACTERISTICS

T_A = 0°C to 70°C, V_{DD} = +12V ± 5%, V_{CC} = +5V ± 5%, V_{BB} = -5V ± 5%, V_{SS} = 0V, Unless Otherwise Noted.

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Condition
V_{ILC}	Clock Input Low Voltage	V_{SS}-1		V_{SS}+0.8	V	
V_{IHC}	Clock Input High Voltage	9.0		V_{DD}+1	V	
V_{IL}	Input Low Voltage	V_{SS}-1		V_{SS}+0.8	V	
V_{IH}	Input High Voltage	3.3		V_{CC}+1	V	
V_{OL}	Output Low Voltage			0.45	V	I_{OL} = 1.9mA on all outputs, I_{OH} = 150μA.
V_{OH}	Output High Voltage	3.7			V	
$I_{DD(AV)}$	Avg. Power Supply Current (V_{DD})		40	70	mA	Operation T_{CY} = .38μsec
$I_{CC(AV)}$	Avg. Power Supply Current (V_{CC})		60	80	mA	
$I_{BB(AV)}$	Avg. Power Supply Current (V_{BB})		.01	1	mA	
I_{IL}	Input Leakage			±10	μA	$V_{SS} \leq V_{IN} \leq V_{CC}$
I_{CL}	Clock Leakage			±10	μA	$V_{SS} \leq V_{CLOCK} \leq V_{DD}$
I_{DL} [2]	Data Bus Leakage in Input Mode			-100 -2.0	μA mA	$V_{SS} \leq V_{IN} \leq V_{SS}$ +0.8V V_{SS} +0.8V $\leq V_{IN} \leq V_{CC}$
I_{FL}	Address and Data Bus Leakage During HOLD			+10 -100	μA	$V_{ADDR/DATA} = V_{CC}$ $V_{ADDR/DATA} = V_{SS}$ + 0.45V

CAPACITANCE

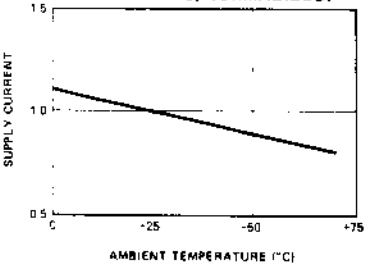
T_A = 25°C $V_{CC} = V_{DD} = V_{SS}$ = 0V, V_{BB} = -5V

Symbol	Parameter	Typ.	Max.	Unit	Test Condition
C_Φ	Clock Capacitance	17	25	pf	f_c = 1 MHz
C_{IN}	Input Capacitance	6	10	pf	Unmeasured Pins
C_{OUT}	Output Capacitance	10	20	pf	Returned to V_{SS}

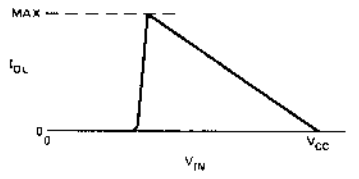
NOTES:

1. The RESET signal must be active for a minimum of 3 clock cycles.
2. When DBIN is high and $V_{IN} > V_{IH}$ an internal active pull up will be switched onto the Data Bus.
3. ΔI supply / ΔT_A = -0.45%/°C.

TYPICAL SUPPLY CURRENT VS. TEMPERATURE, NORMALIZED.[3]



DATA BUS CHARACTERISTIC DURING DBIN



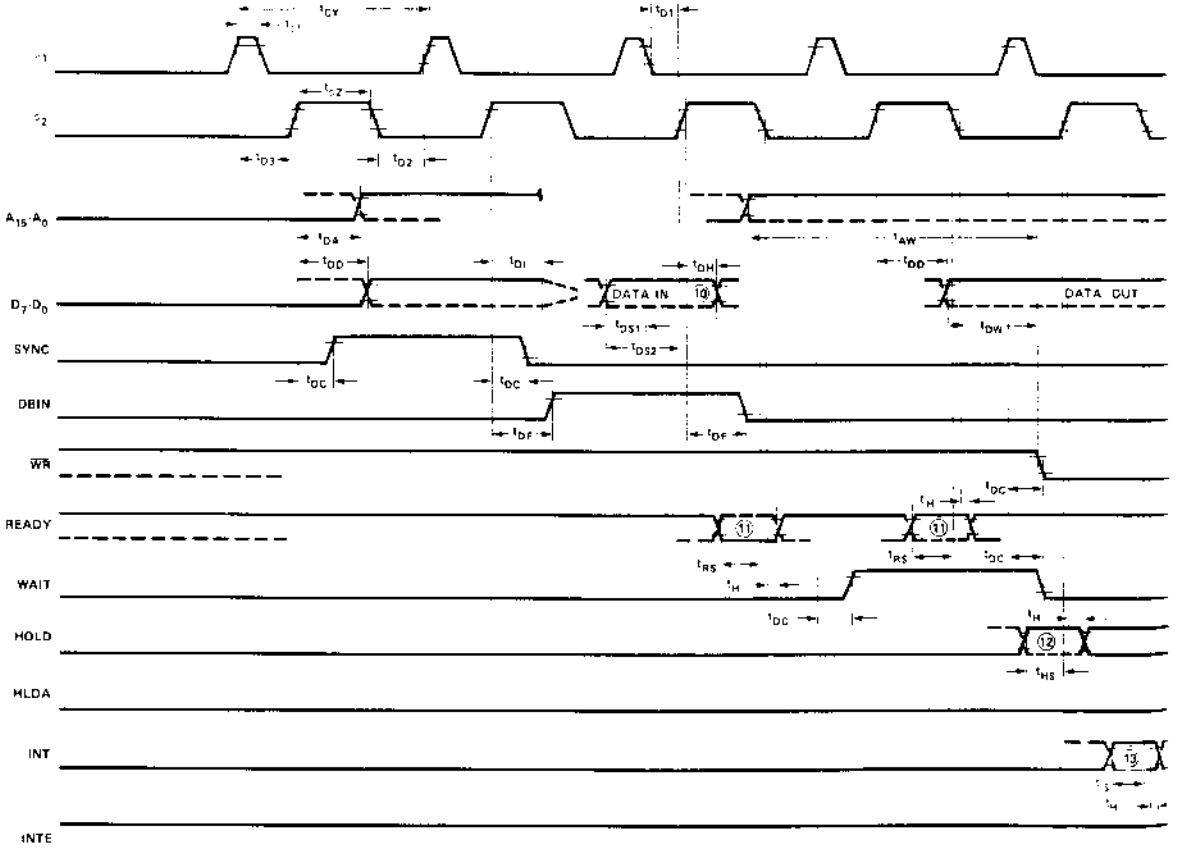
A.C. CHARACTERISTICS

T_A = 0°C to 70°C, V_{DD} = +12V ± 5%, V_{CC} = +5V ± 5%, V_{BB} = -5V ± 5%, V_{SS} = 0V, Unless Otherwise Noted

Symbol	Parameter	Min.	Max.	Unit	Test Condition
t_{CY}[3]	Clock Period	.38	2.0	μsec	
t_r, t_f	Clock Rise and Fall Time	0	50	nsec	
$t_{\phi 1}$	ϕ_1 Pulse Width	60		nsec	
$t_{\phi 2}$	ϕ_2 Pulse Width	175		nsec	
t_{D1}	Delay ϕ_1 to ϕ_2	0		nsec	
t_{D2}	Delay ϕ_2 to ϕ_1	70		nsec	
t_{D3}	Delay ϕ_1 to ϕ_2 Leading Edges	70		nsec	
t_{DA}[2]	Address Output Delay From ϕ_2		175	nsec	C_L = 100pf
t_{DD}[2]	Data Output Delay From ϕ_2		200	nsec	C_L = 100pf
t_{DC}[2]	Signal Output Delay From ϕ_1, or ϕ_2 (SYNC, $\overline{WR}$, WAIT, HLDA)		120	nsec	C_L = 50pf
t_{DF}[2]	DBIN Delay From ϕ_2	25	140	nsec	C_L = 50pf
t_{DI}[1]	Delay for Input Bus to Enter Input Mode		t_{DF}	nsec	
t_{DS1}	Data Setup Time During ϕ_1 and DBIN	20		nsec	

TIMING WAVEFORMS [14]

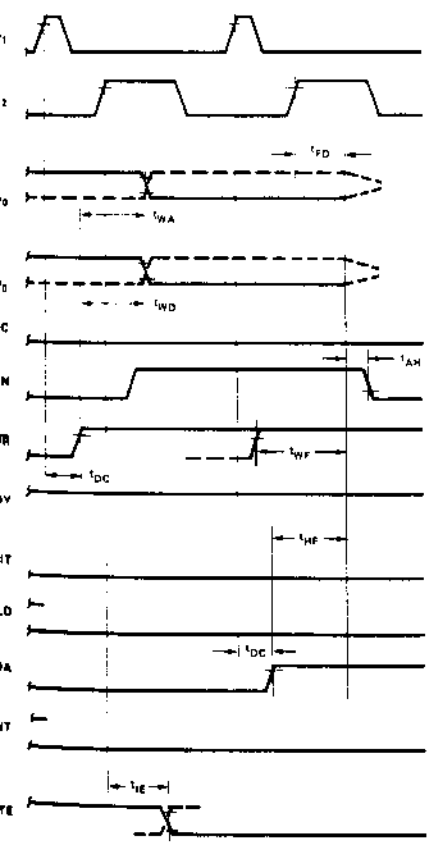
(Note: Timing measurements are made at the following reference voltages: CLOCK "1" = 8.0V "0" = 1.0V; INPUTS "1" = 3.3V, "0" = 0.8V; OUTPUTS "1" = 2.0V, "0" = 0.8V.)



A.C. CHARACTERISTICS (Continued)

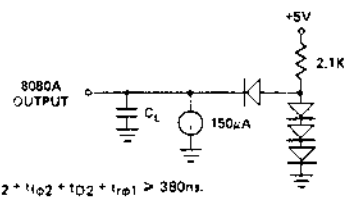
T_A = 0°C to 70°C, V_{DD} = +12V ± 5%, V_{CC} = +5V ± 5%, V_{BB} = -5V ± 5%, V_{SS} = 0V, Unless Otherwise Noted

Symbol	Parameter	Min.	Max.	Unit	Test Condition
t_{DS2}	Data Setup Time to ϕ_2 During DBIN	130		nsec	
t_{DH} [1]	Data Hold Time From ϕ_2 During DBIN	[1]		nsec	
t_{IE} [2]	INTE Output Delay From ϕ_2		200	nsec	C_L = 50pf
t_{RS}	READY Setup Time During ϕ_2	90		nsec	
t_{HS}	HOLD Setup Time to ϕ_2	120		nsec	
t_{IS}	INT Setup Time During ϕ_2 (During ϕ_1 in Halt Mode)	100		nsec	
t_H	Hold Time From ϕ_2 (READY, INT, HOLD)	0		nsec	
t_{FD}	Delay to Float During Hold (Address and Data Bus)		120	nsec	
t_{AW} [2]	Address Stable Prior to $\overline{WR}$	[5]		nsec	C_L = 100pf: Address, Data C_L = 50pf: $\overline{WR}$, HLDA, DBIN
t_{DW} [2]	Output Data Stable Prior to $\overline{WR}$	[6]		nsec	
t_{WD} [2]	Output Data Stable From $\overline{WR}$	[7]		nsec	
t_{WA} [2]	Address Stable From $\overline{WR}$	[7]		nsec	
t_{HF} [2]	HLDA to Float Delay	[8]		nsec	
t_{WF} [2]	$\overline{WR}$ to Float Delay	[9]		nsec	
t_{AH} [2]	Address Hold Time After DBIN During HLDA	-20		nsec	



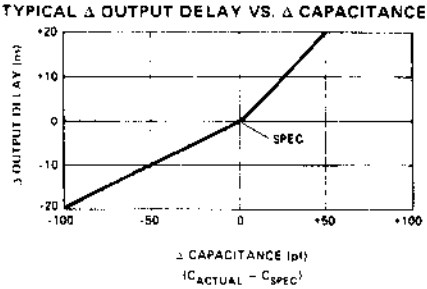
NOTES:

1. Data input should be enabled with DBIN status. No bus conflict can then occur and data hold time is assured t_{DH} = 50ns or t_{DF}, whichever is less.
2. Load Circuit



3. $t_{CY} = t_{D3} + t_{r\phi2} + t_{\phi2} + t_{f\phi2} + t_{D2} + t_{r\phi1} \geq 380$ns.

TYPICAL Δ OUTPUT DELAY VS. Δ CAPACITANCE



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5. $t_{AW} = 2\,t_{CY} - t_{D3} - t_{r\phi2} - 130$nsec.
6. $t_{DW} = t_{CY} - t_{D3} - t_{r\phi2} - 170$nsec.
7. If not HLDA, $t_{WD} = t_{WA} = t_{D3} + t_{r\phi2} + 10$ns. If HLDA, $t_{WD} = t_{WA} = t_{WF}$.
8. $t_{HF} = t_{D3} + t_{r\phi2} - 50$ns.
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Silicon Gate MOS **M8080A**

SINGLE CHIP 8-BIT N-CHANNEL MICROPROCESSOR

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- **Full Military Temperature Range −55°C to +125°C**
- **±10% Power Supply Tolerance**
- **2 μs Instruction Cycle**
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- **Decimal, Binary and Double Precision Arithmetic**
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- **TTL Drive Capability**

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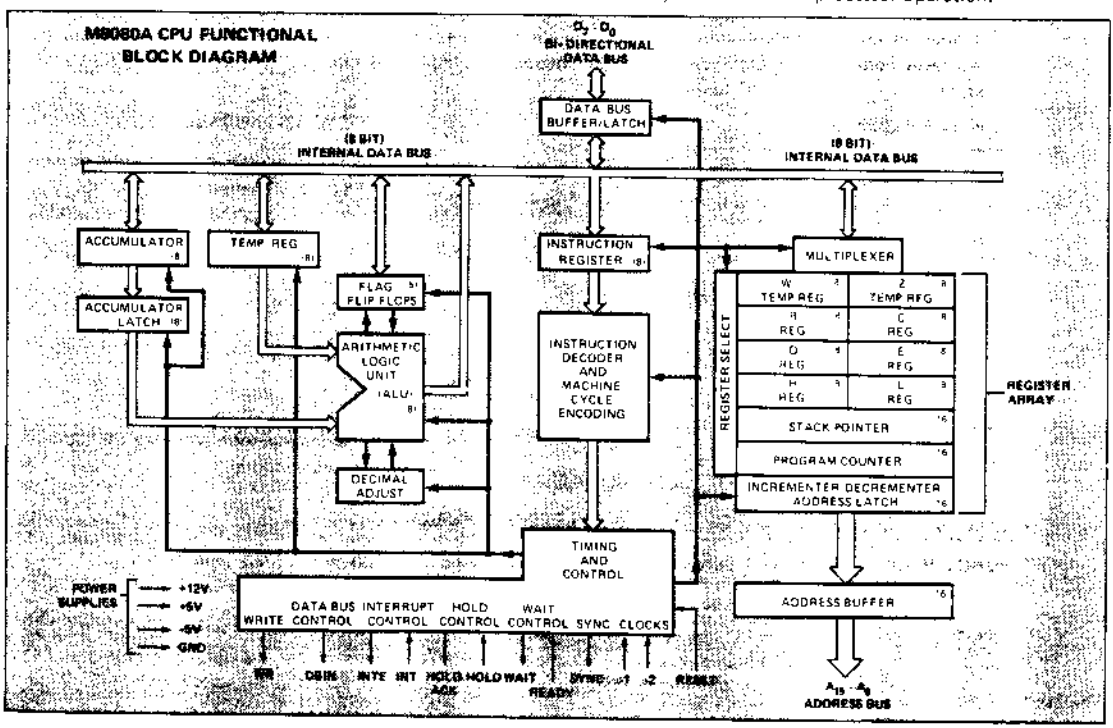


INSTRUCTION SET

The accumulator group instructions include arithmetic and logical operators with direct, indirect, and immediate addressing modes.

Move, load, and store instruction groups provide the ability to move either 8 or 16 bits of data between memory, the six working registers and the accumulator using direct, indirect, and immediate addressing modes.

The ability to branch to different portions of the program is provided with jump, jump conditional, and computed jumps. Also the ability to call to and return from subroutines is provided both conditionally and unconditionally. The RESTART (or single byte call instruction) is useful for interrupt vector operation.

Double precision operators such as stack manipulation and double add instructions extend both the arithmetic and interrupt handling capability of the M8080A. The ability to increment and decrement memory, the six general registers and the accumulator is provided as well as extended increment and decrement instructions to operate on the register pairs and stack pointer. Further capability is provided by the ability to rotate the accumulator left or right through or around the carry bit.

Input and output may be accomplished using memory addresses as I/O ports or the directly addressed I/O provided for in the M8080A instruction set.

The following special instruction group completes the M8080A instruction set: the NOP instruction, HALT to stop processor execution and the DAA instructions provide decimal arithmetic capability. STC allows the carry flag to be directly set, and the CMC instruction allows it to be complemented. CMA complements the contents of the accumulator and XCHG exchanges the contents of two 16-bit register pairs directly.

Data and Instruction Formats

Data in the M8080A is stored in the form of 8-bit binary integers. All data transfers to the system data bus will be in the same format.

D_7	D_6	D_5	D_4	D_3	D_2	D_1	D_0

DATA WORD

The program instructions may be one, two, or three bytes in length. Multiple byte instructions must be stored in successive words in program memory. The instruction formats then depend on the particular operation executed.

One Byte Instructions

D_7	D_6	D_5	D_4	D_3	D_2	D_1	D_0	OP CODE

TYPICAL INSTRUCTIONS

Register to register, memory reference, arithmetic or logical, rotate, return, push, pop, enable or disable Interrupt instructions

Two Byte Instructions

D_7	D_6	D_5	D_4	D_3	D_2	D_1	D_0	OP CODE
D_7	D_6	D_5	D_4	D_3	D_2	D_1	D_0	OPERAND

Immediate mode or I/O instructions

Three Byte Instructions

D_7	D_6	D_5	D_4	D_3	D_2	D_1	D_0	OP CODE
D_7	D_6	D_5	D_4	D_3	D_2	D_1	D_0	LOW ADDRESS OR OPERAND 1
D_7	D_6	D_5	D_4	D_3	D_2	D_1	D_0	HIGH ADDRESS OR OPERAND 2

Jump, call or direct load and store instructions

For the M8080A a logic "1" is defined as a high level and a logic "0" is defined as a low level.

INSTRUCTION SET

Summary of Processor Instructions

Mnemonic	Description	Instruction Code[1] D_7	D_6	D_5	D_4	D_3	D_2	D_1	D_0	Clock[2] Cycles
MOV r2,r1	Move register to register	0	1	D	D	D	S	S	S	5
MOV M,r	Move register to memory	0	1	1	1	0	S	S	S	7
MOV r,M	Move memory to register	0	1	D	D	D	1	1	0	7
HLT	Halt	0	1	1	1	0	1	1	0	7
MVI r	Move immediate register	0	0	D	D	D	1	1	0	7
MVI M	Move immediate memory	0	0	1	1	0	1	1	0	10
INR r	Increment register	0	0	D	D	D	1	0	0	5
DCR r	Decrement register	0	0	D	D	D	1	0	1	5
INR M	Increment memory	0	0	1	1	0	1	0	0	10
DCR M	Decrement memory	0	0	1	1	0	1	0	1	10
ADD r	Add register to A	1	0	0	0	0	S	S	S	4
ADC r	Add register to A with carry	1	0	0	0	1	S	S	S	4
SUB r	Subtract register from A	1	0	0	1	0	S	S	S	4
SBB r	Subtract register from A with borrow	1	0	0	1	1	S	S	S	4
ANA r	And register with A	1	0	1	0	0	S	S	S	4
XRA r	Exclusive Or register with A	1	0	1	0	1	S	S	S	4
ORA r	Or register with A	1	0	1	1	0	S	S	S	4
CMP r	Compare register with A	1	0	1	1	1	S	S	S	4
ADD M	Add memory to A	1	0	0	0	0	1	1	0	7
ADC M	Add memory to A with carry	1	0	0	0	1	1	1	0	7
SUB M	Subtract memory from A	1	0	0	1	0	1	1	0	7
SBB M	Subtract memory from A with borrow	1	0	0	1	1	1	1	0	7
ANA M	And memory with A	1	0	1	0	0	1	1	0	7
XRA M	Exclusive Or memory with A	1	0	1	0	1	1	1	0	7
ORA M	Or memory with A	1	0	1	1	0	1	1	0	7
CMP M	Compare memory with A	1	0	1	1	1	1	1	0	7
ADI	Add immediate to A	1	1	0	0	0	1	1	0	7
ACI	Add immediate to A with carry	1	1	0	0	1	1	1	0	7
SUI	Subtract immediate from A	1	1	0	1	0	1	1	0	7
SBI	Subtract immediate from A with borrow	1	1	0	1	1	1	1	0	7
ANI	And immediate with A	1	1	1	0	0	1	1	0	7
XRI	Exclusive Or immediate with A	1	1	1	0	1	1	1	0	7
ORI	Or immediate with A	1	1	1	1	0	1	1	0	7
CPI	Compare immediate with A	1	1	1	1	1	1	1	0	7
RLC	Rotate A left	0	0	0	0	0	1	1	1	4
RRC	Rotate A right	0	0	0	0	1	1	1	1	4
RAL	Rotate A left through carry	0	0	0	1	0	1	1	1	4
RAR	Rotate A right through carry	0	0	0	1	1	1	1	1	4
JMP	Jump unconditional	1	1	0	0	0	0	1	1	10
JC	Jump on carry	1	1	0	1	1	0	1	0	10
JNC	Jump on no carry	1	1	0	1	0	0	1	0	10
JZ	Jump on zero	1	1	0	0	1	0	1	0	10
JNZ	Jump on no zero	1	1	0	0	0	0	1	0	10
JP	Jump on positive	1	1	1	1	0	0	1	0	10
JM	Jump on minus	1	1	1	1	1	0	1	0	10
JPE	Jump on parity even	1	1	1	0	1	0	1	0	10
JPO	Jump on parity odd	1	1	1	0	0	0	1	0	10
CALL	Call unconditional	1	1	0	0	1	1	0	1	17
CC	Call on carry	1	1	0	1	1	1	0	0	11/17
CNC	Call on no carry	1	1	0	1	0	1	0	0	11/17
CZ	Call on zero	1	1	0	0	1	1	0	0	11/17
CNZ	Call on no zero	1	1	0	0	0	1	0	0	11/17
CP	Call on positive	1	1	1	1	0	1	0	0	11/17
CM	Call on minus	1	1	1	1	1	1	0	0	11/17
CPE	Call on parity even	1	1	1	0	1	1	0	0	11/17
CPO	Call on parity odd	1	1	1	0	0	1	0	0	11/17
RET	Return	1	1	0	0	1	0	0	1	10
RC	Return on carry	1	1	0	1	1	0	0	0	5/11
RNC	Return on no carry	1	1	0	1	0	0	0	0	5/11
RZ	Return on zero	1	1	0	0	1	0	0	0	5/11
RNZ	Return on no zero	1	1	0	0	0	0	0	0	5/11
RP	Return on positive	1	1	1	1	0	0	0	0	5/11
RM	Return on minus	1	1	1	1	1	0	0	0	5/11
RPE	Return on parity even	1	1	1	0	1	0	0	0	5/11
RPO	Return on parity odd	1	1	1	0	0	0	0	0	5/11
RST	Restart	1	1	A	A	A	1	1	1	11
IN	Input	1	1	0	1	1	0	1	1	10
OUT	Output	1	1	0	1	0	0	1	1	10
LXI B	Load immediate register Pair B & C	0	0	0	0	0	0	0	1	10
LXI D	Load immediate register Pair D & E	0	0	0	1	0	0	0	1	10
LXI H	Load immediate register Pair H & L	0	0	1	0	0	0	0	1	10
LXI SP	Load immediate stack pointer	0	0	1	1	0	0	0	1	10
PUSH B	Push register Pair B & C on stack	1	1	0	0	0	1	0	1	11
PUSH D	Push register Pair D & E on stack	1	1	0	1	0	1	0	1	11
PUSH H	Push register Pair H & L on stack	1	1	1	0	0	1	0	1	11
PUSH PSW	Push A and Flags on stack	1	1	1	1	0	1	0	1	11
POP B	Pop register pair B & C off stack	1	1	0	0	0	0	0	1	10
POP D	Pop register pair D & E off stack	1	1	0	1	0	0	0	1	10
POP H	Pop register pair H & L off stack	1	1	1	0	0	0	0	1	10
POP PSW	Pop A and Flags off stack	1	1	1	1	0	0	0	1	10
STA	Store A direct	0	0	1	1	0	0	1	0	13
LDA	Load A direct	0	0	1	1	1	0	1	0	13
XCHG	Exchange D & E, H & L Registers	1	1	1	0	1	0	1	1	4
XTHL	Exchange top of stack H & L	1	1	1	0	0	0	1	1	18
SPHL	H & L to stack pointer	1	1	1	1	1	0	0	1	5
PCHL	H & L to program counter	1	1	1	0	1	0	0	1	5
DAD B	Add B & C to H & L	0	0	0	0	1	0	0	1	10
DAD D	Add D & E to H & L	0	0	0	1	1	0	0	1	10
DAD H	Add H & L to H & L	0	0	1	0	1	0	0	1	10
DAD SP	Add stack pointer to H & L	0	0	1	1	1	0	0	1	10
STAX B	Store A indirect	0	0	0	0	0	0	1	0	7
STAX D	Store A indirect	0	0	0	1	0	0	1	0	7
LDAX B	Load A indirect	0	0	0	0	1	0	1	0	7
LDAX D	Load A indirect	0	0	0	1	1	0	1	0	7
INX B	Increment B & C registers	0	0	0	0	0	0	1	1	5
INX D	Increment D & E registers	0	0	0	1	0	0	1	1	5
INX H	Increment H & L registers	0	0	1	0	0	0	1	1	5
INX SP	Increment stack pointer	0	0	1	1	0	0	1	1	5
DCX B	Decrement B & C	0	0	0	0	1	0	1	1	5
DCX D	Decrement D & E	0	0	0	1	1	0	1	1	5
DCX H	Decrement H & L	0	0	1	0	1	0	1	1	5
DCX SP	Decrement stack pointer	0	0	1	1	1	0	1	1	5
CMA	Complement A	0	0	1	0	1	1	1	1	4
STC	Set carry	0	0	1	1	0	1	1	1	4
CMC	Complement carry	0	0	1	1	1	1	1	1	4
DAA	Decimal adjust A	0	0	1	0	0	1	1	1	4
SHLD	Store H & L direct	0	0	1	0	0	0	1	0	16
LHLD	Load H & L direct	0	0	1	0	1	0	1	0	16
EI	Enable interrupts	1	1	1	1	1	0	1	1	4
DI	Disable interrupt	1	1	1	1	0	0	1	1	4
NOP	No-operation	0	0	0	0	0	0	0	0	4

NOTES: 1. DDD or SSS – 000 B – 001 C – 010 D – 011 E – 100 H – 101 L – 110 Memory – 111 A.
2. Two possible cycle times, (5/11) indicate instruction cycles dependent on condition flags.

M8080A FUNCTIONAL PIN DEFINITION

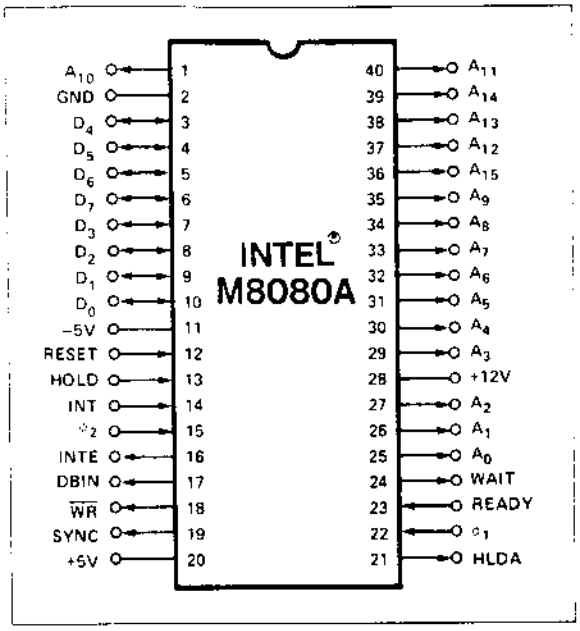
The following describes the function of all of the M8080A I/O pins. Several of the descriptions refer to internal timing periods.

A_{15}-A_0 (output three-state)
ADDRESS BUS; the address bus provides the address to memory (up to 64K 8-bit words) or denotes the I/O device number for up to 256 input and 256 output devices. A_0 is the least significant address bit.

D_7-D_0 (input/output three-state)
DATA BUS; the data bus provides bi-directional communication between the CPU, memory, and I/O devices for instructions and data transfers. Also, during the first clock cycle of each machine cycle, the M8080A outputs a status word on the data bus that describes the current machine cycle. D_0 is the least significant bit.

SYNC (output)
SYNCHRONIZING SIGNAL; the SYNC pin provides a signal to indicate the beginning of each machine cycle.

DBIN (output)
DATA BUS IN; the DBIN signal indicates to external circuits that the data bus is in the input mode. This signal should be used to enable the gating of data onto the M8080A data bus from memory or I/O.



Pin Configuration

READY (input)
READY; the READY signal indicates to the M8080A that valid memory or input data is available on the M8080A data bus. This signal is used to synchronize the CPU with slower memory or I/O devices. If after sending an address out the M8080A does not receive a READY input, the M8080A will enter a WAIT state for as long as the READY line is low. READY can also be used to single step the CPU.

WAIT (output)
WAIT; the WAIT signal acknowledges that the CPU is in a WAIT state.

WR (output)
WRITE; the $\overline{WR}$ signal is used for memory WRITE or I/O output control. The data on the data bus is stable while the $\overline{WR}$ signal is active low ($\overline{WR}$ = 0).

HOLD (input)
HOLD; the HOLD signal requests the CPU to enter the HOLD state. The HOLD state allows an external device to gain control of the M8080A address and data bus as soon as the M8080A has completed its use of these buses for the current machine cycle. It is recognized under the following conditions:

- the CPU is in the HALT state.
- the CPU is in the T2 or TW state and the READY signal is active.

As a result of entering the HOLD state the CPU ADDRESS BUS (A_{15}-A_0) and DATA BUS (D_7-D_0) will be in their high impedance state. The CPU acknowledges its state with the HOLD ACKNOWLEDGE (HLDA) pin.

HLDA (output)
HOLD ACKNOWLEDGE; the HLDA signal appears in response to the HOLD signal and indicates that the data and address bus will go to the high impedance state. The HLDA signal begins at:

- T3 for READ memory or input.
- The Clock Period following T3 for WRITE memory or OUTPUT operation.

In either case, the HLDA signal appears after the rising edge of ϕ_1 and high impedance occurs after the rising edge of ϕ_2.

INTE (output)
INTERRUPT ENABLE; indicates the content of the internal interrupt enable flip/flop. This flip/flop may be set or reset by the Enable and Disable Interrupt instructions and inhibits interrupts from being accepted by the CPU when it is reset. It is automatically reset (disabling further interrupts) at time T1 of the instruction fetch cycle (M1) when an interrupt is accepted and is also reset by the RESET signal.

INT (input)
INTERRUPT REQUEST; the CPU recognizes an interrupt request on this line at the end of the current instruction or while halted. If the CPU is in the HOLD state or if the Interrupt Enable flip/flop is reset it will not honor the request.

RESET (input)[1]
RESET; while the RESET signal is activated, the content of the program counter is cleared. After RESET, the program will start at location 0 in memory. The INTE and HLDA flip/flops are also reset. Note that the flags, accumulator, stack pointer, and registers are not cleared.

V_{SS}	Ground Reference
V_{DD}	+12 Volts ±10%.
V_{CC}	+5 Volts ±10%.
V_{BB}	-5 Volts ±10%.
ϕ_1, ϕ_2	2 externally supplied clock phases. (non TTL compatible)

ABSOLUTE MAXIMUM RATINGS*

Temperature Under Bias	-55°C to +125°C
Storage Temperature	-65°C to +150°C
All Input or Output Voltages With Respect to V_{BB}	-0.3V to +20V
V_{CC}, V_{DD} and V_{SS} With Respect to V_{BB}	-0.3V to +20V
Power Dissipation	1.7W

**COMMENT: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.*

D.C. CHARACTERISTICS

T_A = -55°C to +125°C, V_{DD} = +12V ±10%, V_{CC} = +5V ±10%, V_{BB} = -5V ±10%, V_{SS} = 0V, Unless Otherwise Noted.

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Condition
V_{ILC}	Clock Input Low Voltage	V_{SS}-1		V_{SS}+0.8	V	
V_{IHC}	Clock Input High Voltage	8.5		V_{DD}+1	V	
V_{IL}	Input Low Voltage	V_{SS}-1		V_{SS}+0.8	V	
V_{IH}	Input High Voltage	3.0		V_{CC}+1	V	
V_{OL}	Output Low Voltage			0.45	V	I_{OL} = 1.9mA on all outputs, I_{OH} = 150μA.
V_{OH}	Output High Voltage	3.7			V	
$I_{DD(AV)}$	Avg. Power Supply Current (V_{DD})		50	80	mA	Operation T_{CY} = .48 μsec
$I_{CC(AV)}$	Avg. Power Supply Current (V_{CC})		60	100	mA	
$I_{BB(AV)}$	Avg. Power Supply Current (V_{BB})		.01	1	mA	
I_{IL}	Input Leakage			±10	μA	$V_{SS} \leq V_{IN} \leq V_{CC}$
I_{CL}	Clock Leakage			±10	μA	$V_{SS} \leq V_{CLOCK} \leq V_{DD}$
I_{DL} [2]	Data Bus Leakage in Input Mode			-100 -2.0	μA mA	$V_{SS} \leq V_{IN} \leq V_{SS}$ +0.8V V_{SS} +0.8V $\leq V_{IN} \leq V_{CC}$
I_{FL}	Address and Data Bus Leakage During HOLD			+10 -100	μA	$V_{ADDR/DATA} = V_{CC}$ $V_{ADDR/DATA} = V_{SS}$ + 0.45V

CAPACITANCE

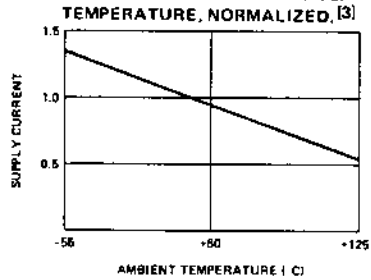
T_A = 25°C $V_{CC} = V_{DD} = V_{SS}$ = 0V, V_{BB} = -5V

Symbol	Parameter	Typ.	Max.	Unit	Test Condition
C_ϕ	Clock Capacitance	17	25	pf	f_c = 1 MHz
C_{IN}	Input Capacitance	6	10	pf	Unmeasured Pins
C_{OUT}	Output Capacitance	10	20	pf	Returned to V_{SS}

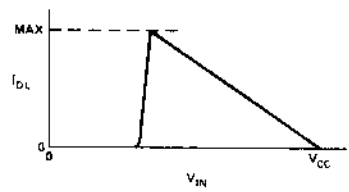
NOTES:

1. The RESET signal must be active for a minimum of 3 clock cycles.
2. When DBIN is high and $V_{IN} > V_{IH}$ an internal active pull up will be switched onto the Data Bus.
3. ΔI supply / ΔT_A = -0.45%/°C.

TYPICAL SUPPLY CURRENT VS. TEMPERATURE, NORMALIZED. [3]



DATA BUS CHARACTERISTIC DURING DBIN



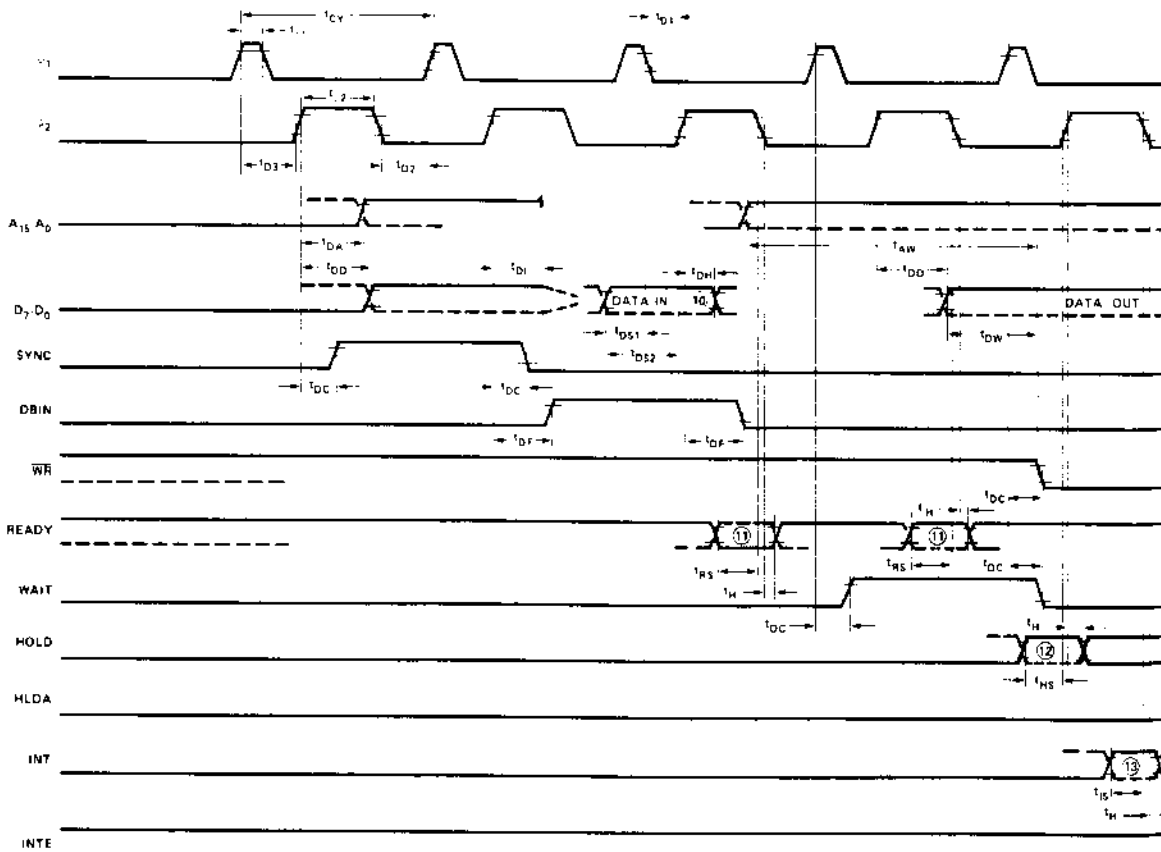
A.C. CHARACTERISTICS

T_A = -55°C to +125°C, V_{DD} = +12V ±10%, V_{CC} = +5V ±10%, V_{BB} = -5V ±10%, V_{SS} = 0V, Unless Otherwise Noted.

Symbol	Parameter	Min.	Max.	Unit	Test Condition
t_{CY}[3]	Clock Period	0.48	2.0	μsec	
t_r, t_f	Clock Rise and Fall Time	0	50	nsec	
$t_{\phi 1}$	ϕ_1 Pulse Width	60		nsec	
$t_{\phi 2}$	ϕ_2 Pulse Width	220		nsec	
t_{D1}	Delay ϕ_1 to ϕ_2	0		nsec	
t_{D2}	Delay ϕ_2 to ϕ_1	80		nsec	
t_{D3}	Delay ϕ_1 to ϕ_2 Leading Edges	80		nsec	
t_{DA} [2]	Address Output Delay From ϕ_2		200	nsec	C_L = 50pf
t_{DD} [2]	Data Output Delay From ϕ_2		220	nsec	
t_{DC} [2]	Signal Output Delay From ϕ_1, or ϕ_2 (SYNC, $\overline{WR}$,WAIT, HLDA)		140	nsec	
t_{DF} [2]	DBIN Delay From ϕ_2	25	150	nsec	
t_{DI} [1]	Delay for Input Bus to Enter Input Mode		t_{DF}	nsec	
t_{DS1}	Data Setup Time During ϕ_1 and DBIN	30		nsec	

TIMING WAVEFORMS [14]

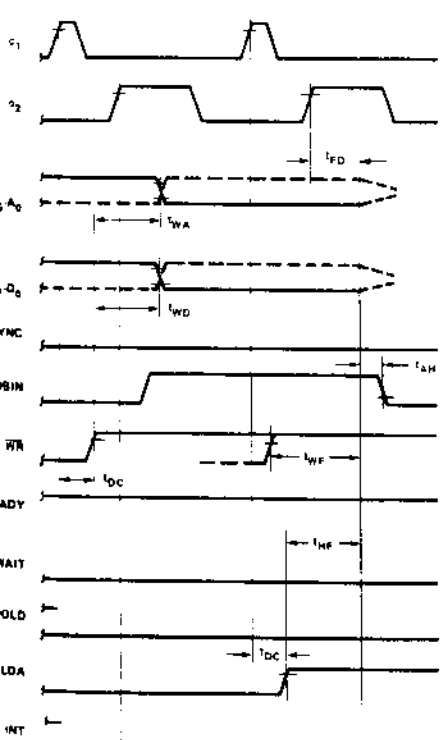
(Note: Timing measurements are made at the following reference voltages: CLOCK "1" = 7.0V, "0" = 1.0V; INPUTS "1" = 3.0V, "0" = 0.8V; OUTPUTS "1" = 2.0V, "0" = 0.8V.)



A.C. CHARACTERISTICS (Continued)

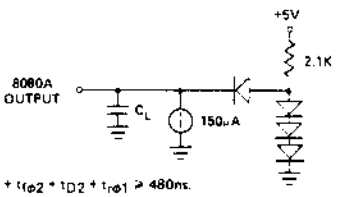
T_A = -55°C to +125°C, V_{DD} = +12V ±10%, V_{CC} = +5V ±10%, V_{BB} = -5V ±10%, V_{SS} = 0V, Unless Otherwise Noted.

Symbol	Parameter	Min.	Max.	Unit	Test Condition
t_{DS2}	Data Setup Time to ϕ_2 During DBIN	130		nsec	
t_{DH} [1]	Data Hold Time From ϕ_2 During DBIN	50		nsec	
t_{IE} [2]	INTE Output Delay From ϕ_2		200	nsec	C_L = 50pf
t_{RS}	READY Setup Time During ϕ_2	120		nsec	
t_{HS}	HOLD Setup Time to ϕ_2	140		nsec	
t_{IS}	INT Setup Time During ϕ_2 (During ϕ_1 in Halt Mode)	120		nsec	
t_H	Hold Time From ϕ_2 (READY, INT, HOLD)	0		nsec	
t_{FD}	Delay to Float During Hold (Address and Data Bus)		130	nsec	
t_{AW} [2]	Address Stable Prior to $\overline{WR}$	[5]		nsec	C_L = 50pf
t_{DW} [2]	Output Data Stable Prior to $\overline{WR}$	[6]		nsec	
t_{WD} [2]	Output Data Stable From $\overline{WR}$	[7]		nsec	
t_{WA} [2]	Address Stable From $\overline{WR}$	[7]		nsec	
t_{HF} [2]	HLDA to Float Delay	[8]		nsec	
t_{WF} [2]	$\overline{WR}$ to Float Delay	[9]		nsec	
t_{AH} [2]	Address Hold Time After DBIN During HLDA	-20		nsec	



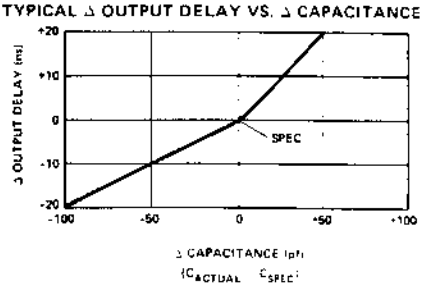
NOTES:

1. Data input should be enabled with DBIN status. No bus conflict can then occur and data hold time is assured. t_{DH} = 50 ns or t_{DF}, whichever is less.
2. Load Circuit.



3. $t_{CY} = t_{D3} + t_{r\phi2} + t_{\phi2} + t_{f\phi2} + t_{D2} + t_{r\phi1} \geq 480$ns.

TYPICAL Δ OUTPUT DELAY VS. Δ CAPACITANCE

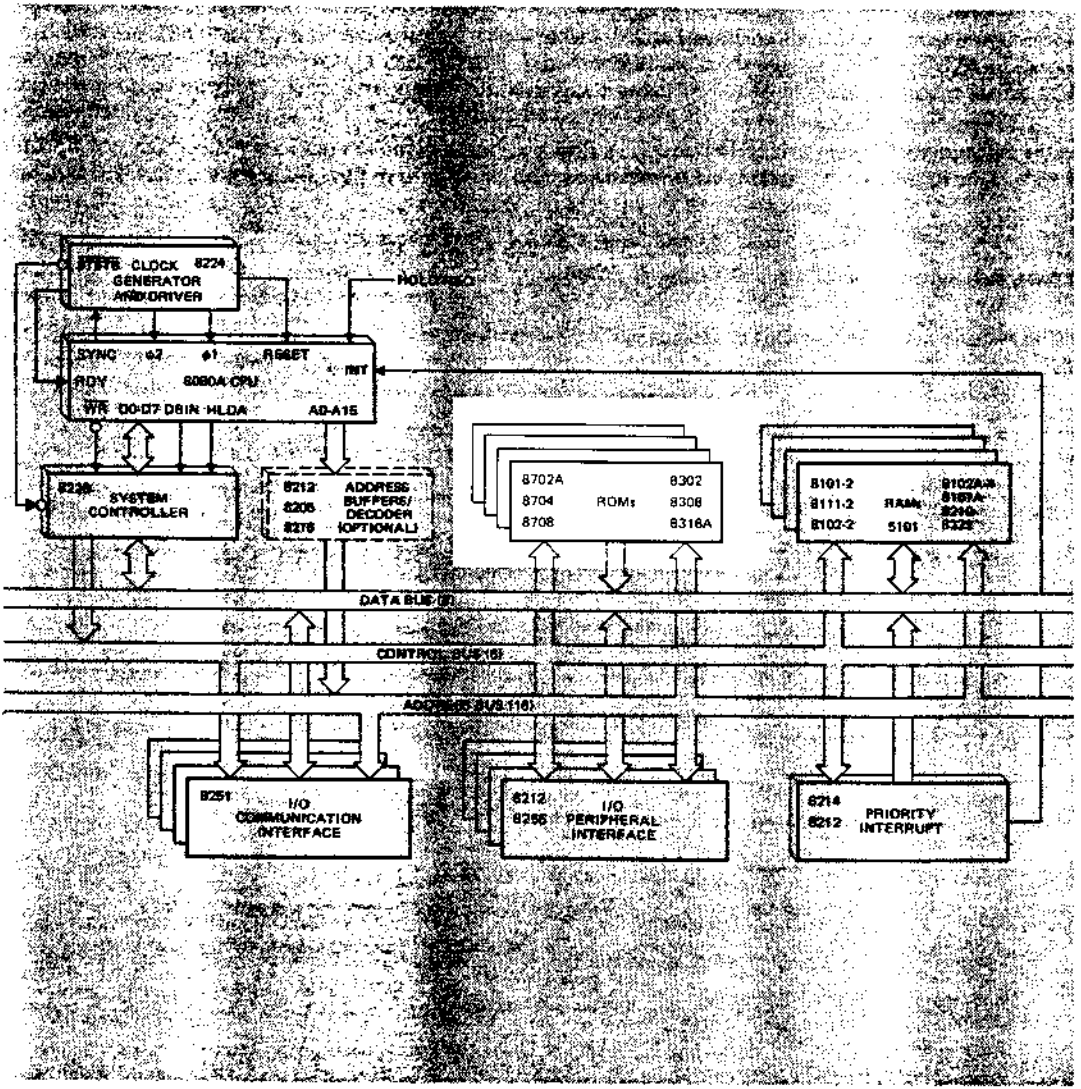


4. The following are relevant when interfacing the M8080A to devices having V_{IH} = 3.3V
   a) Maximum output rise time from .8V to 3.3V = 100ns @ C_L = SPEC
   b) Output delay when measured to 3.0V = SPEC +80ns @ C_L = SPEC.
   c) If $C_L \neq$ SPEC, add .6ns/pF if $C_L > C_{SPEC}$, subtract .3ns/pF if $C_L < C_{SPEC}$
5. $t_{AW} = 2\,t_{CY} - t_{D3} - t_{r\phi2} - 140$nsec.
6. $t_{DW} = t_{CY} - t_{D3} - t_{r\phi2} + 70$nsec
7. If not HLDA, $t_{WD} = t_{WA} + t_{D3} + t_{r\phi2} + 10$ns. If HLDA, $t_{WD} = t_{WA} + t_{WF}$
8. $t_{HF} = t_{D3} + t_{f\phi2} - 50$ns.
9. $t_{WF} = t_{D3} + t_{r\phi2} - 10$ns
10. Data in must be stable for this period during DBIN (T_3). Both t_{DS1} and t_{DS2} must be satisfied.
11. Ready signal must be stable for this period during T_2 or T_W. (Must be externally synchronized.)
12. Hold signal must be stable for this period during T_2 or T_W when entering hold mode and during T_3, T_4, T_5 and T_{WH} when in hold mode. (External synchronization is not required.)
13. Interrupt signal must be stable during this period of the last clock cycle of any instruction in order to be recognized on the following instruction. (External synchronization is not required.)
14. This timing diagram shows timing relationships only; it does not represent any specific machine cycle

intel®
Microcomputer Systems

ROMs

8702A 8302
8704 8308
8708 8316A



Silicon Gate MOS **8702A**

2048 BIT ERASABLE AND ELECTRICALLY REPROGRAMMABLE READ ONLY MEMORY

- **Access Time — 1.3 μsec Max.**
- **Fast Programming — 2 Minutes for All 2048 Bits**
- **Fully Decoded, 256 x 8 Organization**
- **Static MOS — No Clocks Required**
- **Inputs and Outputs TTL Compatible**
- **Three-State Output — OR-Tie Capability**
- **Simple Memory Expansion Chip Select Input Lead**

The 8702A is a 256 word by 8 bit electrically programmable ROM ideally suited for microcomputer system development where fast turn-around and pattern experimentation are important. The 8702A undergoes complete programming and functional testing on each bit position prior to shipment, thus insuring 100% programmability.

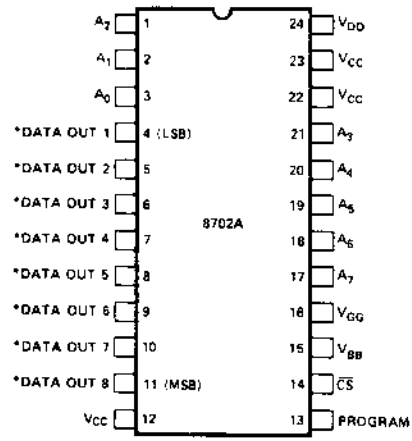
The 8702A is packaged in a 24 pin dual-in line package with a transparent quartz lid. The transparent quartz lid allows the user to expose the chip to ultraviolet light to erase the bit pattern. A new pattern can then be written into the device. This procedure can be repeated as many times as required.

The circuitry of the 8702A is entirely static; no clocks are required.

A pin-for-pin metal mask programmed ROM, the Intel 8302, is ideal for large volume production runs of systems initially using the 8702A.

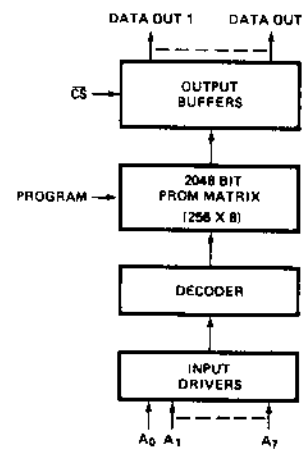
The 8702A is fabricated with silicon gate technology. This low threshold technology allows the design and production of higher performance MOS circuits and provides a higher functional density on a monolithic chip than conventional MOS technologies.

PIN CONFIGURATION



*THIS PIN IS THE DATA INPUT LEAD DURING PROGRAMMING.

BLOCK DIAGRAM



PIN NAMES

A_0-A_7	ADDRESS INPUTS
$\overline{CS}$	CHIP SELECT INPUT
DO_1- DO_2	DATA OUTPUTS

PIN CONNECTIONS

The external lead connections to the 8702A differ, depending on whether the device is being programmed[1] or used in read mode. (See following table.)

MODE \ PIN	12 (V_{CC})	13 (Program)	14 ($\overline{CS}$)	15 (V_{BB})	16 (V_{GG})	22 (V_{CC})	23 (V_{CC})
Read	V_{CC}	V_{CC}	GND	V_{CC}	V_{GG}	V_{CC}	V_{CC}
Programming	GND	Program Pulse	GND	V_{BB}	Pulsed V_{GG} (V_{IL4P})	GND	GND

ABSOLUTE MAXIMUM RATINGS*

Ambient Temperature Under Bias . . . . . 0°C to +70°C
Storage Temperature . . . . . −65°C to +125°C
Soldering Temperature of Leads (10 sec) . . . . . +300°C
Power Dissipation . . . . . 2 Watts
Read Operation: Input Voltages and Supply Voltages with respect to V_{CC} . . . . . +0.5V to −20V
Program Operation: Input Voltages and Supply Voltages with respect to V_{CC} . . . . . −48V

*COMMENT

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or at any other condition above those indicated in the operational sections of this specification is not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

READ OPERATION

D.C. AND OPERATING CHARACTERISTICS

T_A = 0°C to 70°C, V_{CC} = +5V±5%, V_{DD} = −9V±5%, $V_{GG}^{(2)}$ = −9V±5%, unless otherwise noted.

SYMBOL	TEST	MIN.	TYP[3]	MAX.	UNIT	CONDITIONS
I_{LI}	Address and Chip Select Input Load Current			10	µA	V_{IN} = 0.0V
I_{LO}	Output Leakage Current			10	µA	V_{OUT} = 0.0V, $\overline{CS}$ = V_{CC} −2
I_{DDO}	Power Supply Current		5	10	mA	V_{GG} = V_{CC}, $\overline{CS}$ = V_{CC} −2, I_{OL} = 0.0mA, T_A = 25°C
I_{DD1}	Power Supply Current		35	50	mA	$\overline{CS}$ = V_{CC} −2, I_{OL} = 0.0mA, T_A = 25°C
I_{DD2}	Power Supply Current		32	46	mA	$\overline{CS}$ = 0.0, I_{OL} = 0.0mA, T_A = 25°C
I_{DD3}	Power Supply Current		38.5	60	mA	$\overline{CS}$ = V_{CC} −2, I_{OL} = 0.0mA, T_A = 0°C
I_{CF1}	Output Clamp Current		8	14	mA	V_{OUT} = −1.0V, T_A = 0°C
I_{CF2}	Output Clamp Current			13	mA	V_{OUT} = −1.0V, T_A = 25°C
						Continuous Operation
I_{GG}	Gate Supply Current			10	µA	
V_{IL1}	Input Low Voltage for TTL Interface	−1.0		0.65	V	
V_{IL2}	Input Low Voltage for MOS Interface	V_{DD}		V_{CC} −6	V	
V_{IH}	Address and Chip Select Input High Voltage	V_{CC} −2		V_{CC} +0.3	V	
I_{OL}	Output Sink Current	1.6	4		mA	V_{OUT} = 0.45V
V_{OL}	Output Low Voltage			0.45	V	I_{OL} = 1.6mA
V_{OH}	Output High Voltage	3.5			V	I_{OH} = −200 µA

Note 1: In the programming mode, the data inputs 1–8 are pins 4–11 respectively. $\overline{CS}$ = GND.
Note 2: V_{GG} may be clocked to reduce power dissipation. In this mode average I_{DD} increases in proportion to V_{GG} duty cycle. (See p. 5)
Note 3: Typical values are at nominal voltages and T_A = 25°C.

A.C. CHARACTERISTICS

T_A = 0°C to +70°C, V_{CC} = +5V ±5%, V_{DD} = −9V ±5%, V_{GG} = −9V ±5% unless otherwise noted

SYMBOL	TEST	MINIMUM	TYPICAL	MAXIMUM	UNIT
Freq.	Repetition Rate			1	MHz
t_{OH}	Previous read data valid			100	ns
t_{ACC}	Address to output delay			1.3	µs
t_{DVGG}	Clocked V_{GG} set up	1.0			µs
t_{CS}	Chip select delay			400	ns
t_{CO}	Output delay from $\overline{CS}$			900	ns
t_{OD}	Output deselect			400	ns
t_{OHC}	Data out hold in clocked V_{GG} mode (Note 1)			5	µs

Note 1. The output will remain valid for t_{OHC} as long as clocked V_{GG} is at V_{CC}. An address change may occur as soon as the output is sensed (clocked V_{GG} may still be at V_{CC}). Data becomes invalid for the old address when clocked V_{GG} is returned to V_{GG}.

CAPACITANCE* T_A = 25°C

SYMBOL	TEST	MINIMUM	TYPICAL	MAXIMUM	UNIT	CONDITIONS
C_{IN}	Input Capacitance		8	15	pF	V_{IN} = V_{CC}, $\overline{CS}$ = V_{CC}, V_{OUT} = V_{CC}, V_{GG} = V_{CC} — All unused pins are at A.C. ground
C_{OUT}	Output Capacitance		10	15	pF	
$C_{V_{GG}}$	V_{GG} Capacitance (Clocked V_{GG} Mode)			30	pF	

*This parameter is periodically sampled and is not 100% tested.

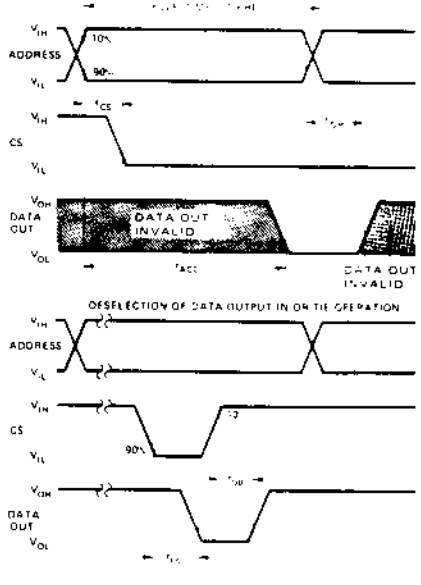
SWITCHING CHARACTERISTICS

Conditions of Test:

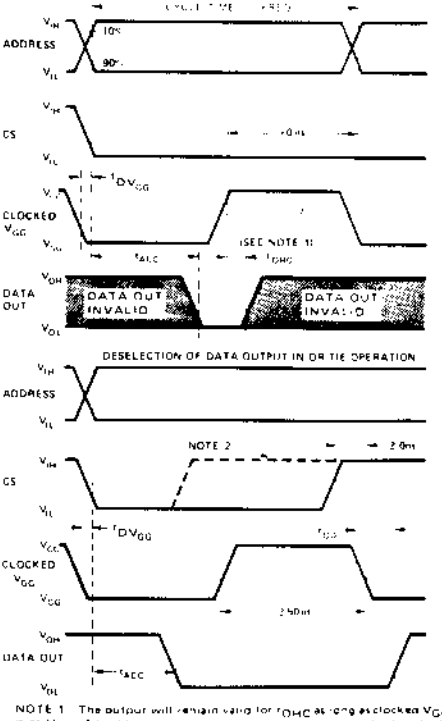
Input pulse amplitudes: 0 to 4V, t_R, t_F ≤ 50 ns

Output load is 1 TTL gate, measurements made at output of TTL gate (t_{PD} ≤ 15 ns)

A) Constant V_{GG} Operation



B) Clocked V_{GG} Operation

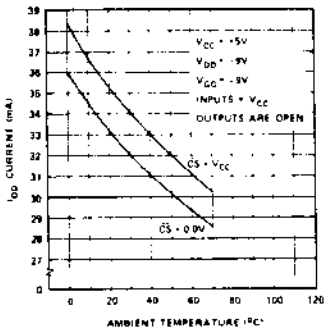


NOTE 1. The output will remain valid for t_{OHC} as long as clocked V_{GG} is at V_{CC}. An address change may occur as soon as the output is sensed (clocked V_{GG} may still be at V_{CC}). Data becomes invalid for the old address when clocked V_{GG} is returned to V_{GG}.

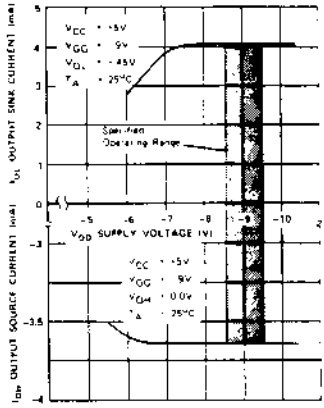
NOTE 2. If $\overline{CS}$ makes a transition from V_{IL} to V_{IH} while clocked V_{GG} is at V_{GG}, then deselection of output occurs at t_{OD} as shown in static operation with constant V_{GG}.

TYPICAL CHARACTERISTICS

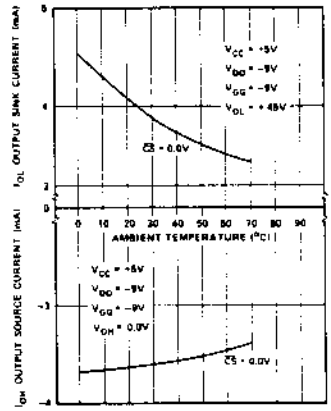
I_{DD} CURRENT VS. TEMPERATURE



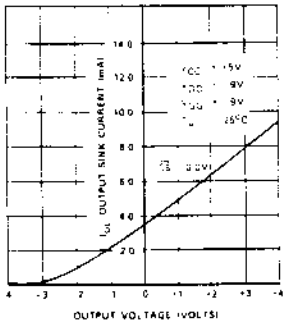
OUTPUT CURRENT VS. V_{DD} SUPPLY VOLTAGE



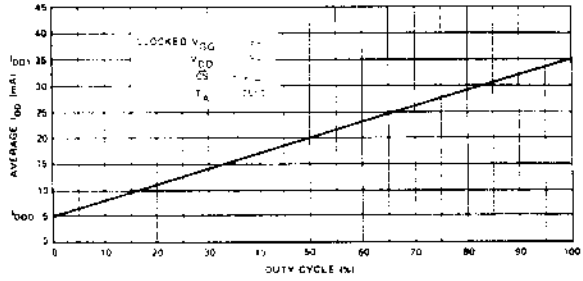
OUTPUT CURRENT VS. TEMPERATURE



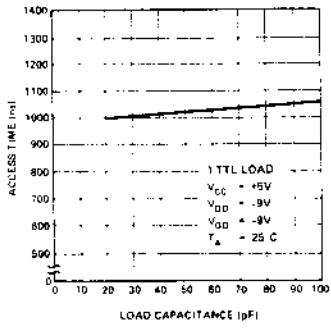
OUTPUT SINK CURRENT VS. OUTPUT VOLTAGE



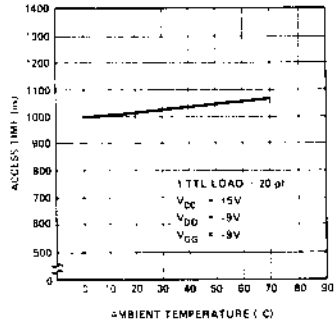
AVERAGE CURRENT VS. DUTY CYCLE FOR CLOCKED V_{GG}



ACCESS TIME VS. LOAD CAPACITANCE



ACCESS TIME VS. TEMPERATURE



PROGRAMMING OPERATION

D.C. AND OPERATING CHARACTERISTICS FOR PROGRAMMING OPERATION

$T_A = 25°C$, $V_{CC} = 0V$, $V_{BB} = +12V \pm 10\%$, $\overline{CS} = 0V$ unless otherwise noted

SYMBOL	TEST	MIN.	TYP.	MAX.	UNIT	CONDITIONS
I_{LI1P}	Address and Data Input Load Current			10	mA	$V_{IN} = -48V$
I_{LI2P}	Program and V_{GG} Load Current			10	mA	$V_{IN} = -48V$
I_{BB}	V_{BB} Supply Load Current		.05		mA	
I_{DDP} (1)	Peak I_{DD} Supply Load Current		200		mA	$V_{DD} = V_{prog} = -48V$ $V_{GG} = -35V$
V_{IHP}	Input High Voltage			0.3	V	
V_{IL1P}	Pulsed Data Input Low Voltage	−46		−48	V	
V_{IL2P}	Address Input Low Voltage	−40		−48	V	
V_{IL3P}	Pulsed Input Low V_{DD} and Program Voltage	−46		−48	V	
V_{IL4P}	Pulsed Input Low V_{GG} Voltage	−35		−40	V	

Note 1: I_{DDP} flows only during V_{DD}, V_{GG} on time. I_{DDP} should not be allowed to exceed 300 mA for greater than 100 μsec. Average power supply current I_{DDP} is typically 40 mA at 20% duty cycle.

A.C. CHARACTERISTICS FOR PROGRAMMING OPERATION

$T_{AMBIENT} = 25°C$, $V_{CC} = 0V$, $V_{BB} = +12V \pm 10\%$, $\overline{CS} = 0V$ unless otherwise noted

SYMBOL	TEST	MIN.	TYP.	MAX.	UNIT	CONDITIONS
	Duty Cycle (V_{DD}, V_{GG})			20	%	
t_{OPW}	Program Pulse Width			3	ms	$V_{GG} = -35V$, $V_{DD} = V_{prog} = -48V$
t_{DW}	Data Set Up Time	25			μs	
t_{DH}	Data Hold Time	10			μs	
t_{VW}	V_{DD}, V_{GG} Set Up	100			μs	
t_{VD}	V_{DD}, V_{GG} Hold	10		100	μs	
t_{ACW} (2)	Address Complement Set Up	25			μs	
t_{ACH} (2)	Address Complement Hold	25			μs	
t_{ATW}	Address True Set Up	10			μs	
t_{ATH}	Address True Hold	10			μs	

Note 2. All 8 address bits must be in the complement state when pulsed V_{DD} and V_{GG} move to their negative levels. The addresses (0 through 255) must be programmed as shown in the timing diagram for a minimum of 32 times.

SWITCHING CHARACTERISTICS FOR PROGRAMMING OPERATION

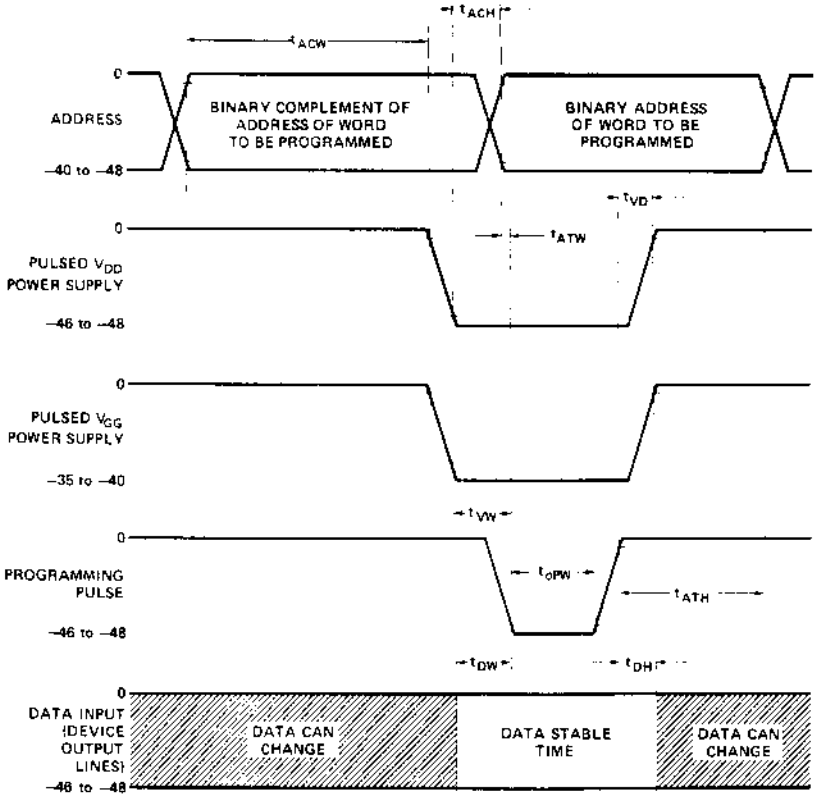
PROGRAM OPERATION

Conditions of Test:

Input pulse rise and fall times $\leq 1\mu$sec

$\overline{CS}$ = 0V

PROGRAM WAVEFORMS



PROGRAMMING OPERATION OF THE 8702A

When the Data Input for the Program Mode is:	Then the Data Output during the Read Mode is:
V_{ILP} = ~ −48V pulsed	Logic 1 = V_{OH} = 'P' on tape
V_{IHP} = ~ 0V	Logic 0 = V_{OL} = 'N' on tape

WORD	ADDRESS A_7	A_6	A_5	A_4	A_3	A_2	A_1	A_0
0	0	0	0	0	0	0	0	0
1	0	0	0	0	0	0	0	1
|	|	|	|	|	|	|	|	|
|	|	|	|	|	|	|	|	|
255	1	1	1	1	1	1	1	1

Address Logic Level During Read Mode: Logic 0 = V_{IL} (~.3V) Logic 1 = V_{IH} (~3V)

Address Logic Level During Program Mode: Logic 0 = V_{IL2P} (~ −40V) Logic 1 = V_{IHP} (~0V)

PROGRAMMING INSTRUCTIONS FOR THE 8702A

I. Operation of the 8702A in Program Mode

Initially, all 2048 bits of the ROM are in the "0" state (output low). Information is introduced by selectively programming "1"s (output high) in the proper bit locations.

Word address selection is done by the same decoding circuitry used in the READ mode (see table on page 6 for logic levels). All 8 address bits must be in the binary complement state when pulsed V_{DD} and V_{GG} move to their negative levels. The addresses must be held in their binary complement state for a minimum of 25 μsec after V_{CC} and V_{GG} have moved to their negative levels. The addresses must then make the transition to their true state a minimum of 10 μsec before the program pulse is applied. The addresses should be programmed in the sequence 0 through 255 for a minimum of 32 times. The eight output terminals are used as data inputs to determine the information pattern in the eight bits of each word. A low data input level (-48V) will program a "1" and a high data input level (ground) will leave a "0" (see table on page 6). All eight bits of one word are programmed simultaneously by setting the desired bit information patterns on the data input terminals.

During the programming, V_{GG}, V_{CC} and the Program Pulse are pulsed signals.

II. Programming of the 8702A Using Intel® Microcomputers

Intel provides low cost program development systems which may be used to program its electrically programmable ROMs. Note that the programming specifications that apply to the 8702A are identical to those for Intel's 1702A.

A. Intellec®

The Intellec series of program development systems, the Intellec 8/Mod 8 and Intellec 8/Mod 80, are used as program development tools for the 8008 and 8080 microprocessors respectively. As such, they are equipped with a PROM programmer card and may be used to program Intel's electrically programmable and ultraviolet erasable ROMs.

An ASR-33 teletype terminal is used as the input device. Through use of the Intellec software system monitor, programs to be loaded into PROM may be typed in directly or loaded through the paper tape reader. The system monitor allows the program to be reviewed or altered at will prior to actually programming the PROM. For more complete information on these program development systems, refer to the Intel Microcomputer Catalog or the Intellec Specifications.

B. Users of the SIM8 microcomputer programming systems may also program the 8702A using the MP7-03 programmer card and the appropriate control ROMs:
SIM8 system—Control ROMs A0860, A0861 and A0863.

III. 8702A Erasing Procedure

The 8702A may be erased by exposure to high intensity short-wave ultraviolet light at a wavelength of 2537A. The recommended integrated dose (i.e., UV intensity x exposure time) is 6W-sec/cm^2. Examples of ultraviolet sources which can erase the 8702A in 10 to 20 minutes are the Model UVS-54 and Model S-52 short-wave ultraviolet lamps manufactured by Ultra-Violet Products, Inc. (5114 Walnut Grove Avenue, San Gabriel, California). The lamps should be used without short-wave filters, and the 8702A to be erased should be placed about one inch away from the lamp tubes.

Silicon Gate MOS 8708/8704

8192/4096 BIT ERASABLE AND ELECTRICALLY REPROGRAMMABLE READ ONLY MEMORY

- 8708 1024x8 Organization
- 8704 512x8 Organization

- Fast Programming — Typ. 100 sec. For All 8K Bits
- Low Power During Programming
- Access Time — 450 ns
- Standard Power Supplies — +12V, ±5V
- Static — No Clocks Required
- Inputs and Outputs TTL Compatible During Both Read and Program Modes
- Three-State Output — OR-Tie Capability

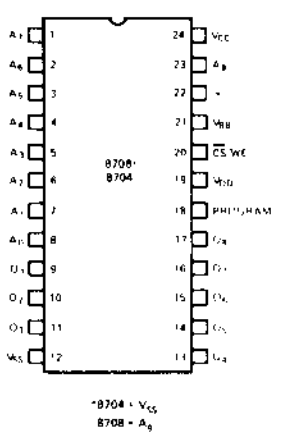
The Intel® 8708/8704 are high speed 8192/4096 bit erasable and electrically reprogrammable ROM's (EPROM) ideally suited where fast turn around and pattern experimentation are important requirements.

The 8708/8704 are packaged in a 24 pin dual-in-line package with transparent lid. The transparent lid allows the user to expose the chip to ultraviolet light to erase the bit pattern. A new pattern can then be written into the devices.

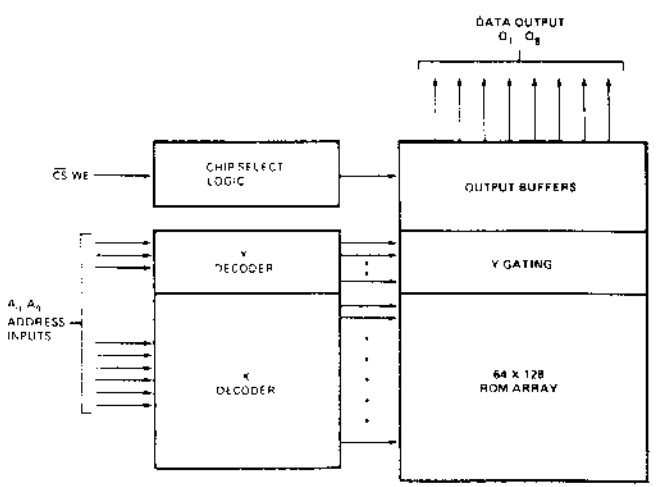
A pin for pin mask programmed ROM, the Intel® 8308, is available for large volume production runs of systems initially using the 8708.

The 8708/8704 is fabricated with the time proven N-channel silicon gate technology.

PIN CONFIGURATIONS



BLOCK DIAGRAM



PIN NAMES

A_0 A_9	ADDRESS INPUTS
O_1-O_8	DATA OUTPUTS
$\overline{CS}$/WE	CHIP SELECT/WRITE ENABLE INPUT

Absolute Maximum Ratings*

Temperature Under Bias . . . . . -25°C to +85°C
Storage Temperature . . . . . -65°C to +125°C
All Input or Output Voltages with Respect to V_{BB} (except Program) . . . . . +15V to -0.3V
Program Input to V_{BB} . . . . . +35V to -0.3V
Supply Voltages V_{CC} and V_{SS} with Respect to V_{BB} . . . . . +15V to -0.3V
V_{DD} with Respect to V_{BB} . . . . . +20V to -0.3V
Power Dissipation 1.5W

*COMMENT

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

READ OPERATION

D.C. and Operating Characteristics

T_A = 0°C to 70°C, V_{CC} = +5V ±5%, V_{DD} = +12V ±5%, V_{BB} = -5V ±5%, V_{SS} = 0V, Unless Otherwise Noted.

Symbol	Parameter	Min.	Typ.[1]	Max.	Unit	Conditions
I_{LI}	Address and Chip Select Input Load Current			10	µA	V_{IN} = 5.25V
I_{LO}	Output Leakage Current			10	µA	V_{OUT} = 5.25V, $\overline{CS}$/WE = 5V
I_{DD}	V_{DD} Supply Current		50	65	mA	Worst Case Supply Currents:
I_{CC}	V_{CC} Supply Current		6	10	mA	All Inputs High
I_{BB}	V_{BB} Supply Current		30	45	mA	$\overline{CS}$/WE = 5V; T_A = 0°C
V_{IL}	Input Low Voltage	V_{SS}		0.65	V	
V_{IH}	Input High Voltage	3.0		V_{CC}+1	V	
V_{OL}	Output Low Voltage			0.45	V	I_{OL} = 1.6mA
V_{OH1}	Output High Voltage	3.7			V	I_{OH} = -100µA
V_{OH2}	Output High Voltage	2.4			V	I_{OH} = -1mA
P_D	Power Dissipation			800	mW	T_A = 70°C

NOTES: 1. Typical values are for T_A = 25°C and nominal supply voltages.
2. The program input (Pin 18) may be tied to V_{SS} or V_{CC} during the read mode.

A.C. Characteristics

$T_A = 0°C$ to $70°C$, $V_{CC} = +5V \pm 5\%$, $V_{DD} = -12V \pm 5\%$, $V_{BB} = -5V \pm 5\%$, $V_{SS} = 0V$, Unless Otherwise Noted.

Symbol	Parameter	Min.	Typ.	Max.	Unit
t_{ACC}	Address to Output Delay		280	450	ns
$t_{\overline{CO}}$	Chip Select to Output Delay			120	ns
t_{DF}	Chip De-Select to Output Float	0		120	ns
t_{OH}	Address to Output Hold	0			ns

Capacitance[1] $T_A = 25°C$, f = 1MHz

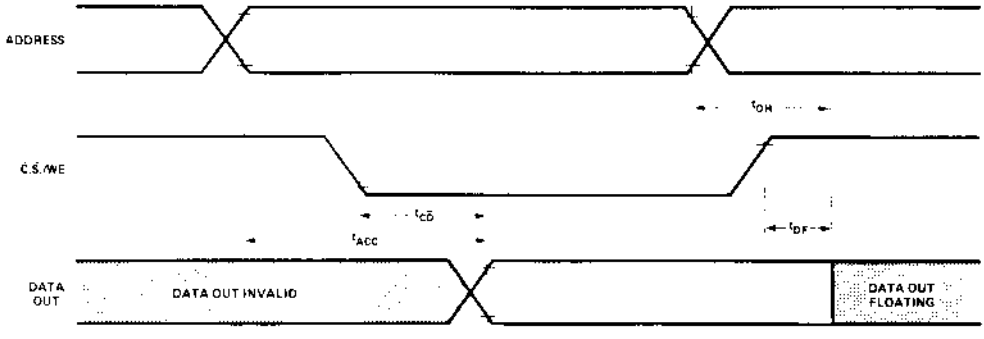
Symbol	Parameter	Typ.	Max.	Unit	Conditions
C_{IN}	Input Capacitance	4	6	pF	$V_{IN}=0V$
C_{OUT}	Output Capacitance	8	12	pF	$V_{OUT}=0V$

Note 1. This parameter is periodically sampled and not 100% tested.

A.C. Test Conditions:

Output Load: 1 TTL gate and C_L = 100pF
Input Rise and Fall Times: ≤20ns
Timing Measurement Reference Levels: 0.8V and 2.8V for inputs; 0.8V and 2.4V for outputs
Input Pulse Levels: 0.65V to 3.0V

Waveforms



PROGRAMMING OPERATION

Description

Initially, and after each erasure, all bits of the 8708/8704 are in the "1" state (Output High). Information is introduced by selectively programming "0" into the desired bit locations.

The circuit is set up for programming operation by raising the $\overline{CS}$/WE input (Pin 20) to +12V. The word address is selected in the same manner as in the read mode. Data to be programmed are presented, 8-bits in parallel, to the data output lines (O_1-O_8). Logic levels for address and data lines and the supply voltages are the same as for the read mode. After address and data set up one program pulse (V_P) per address is applied to the program input (Pin 18). One pass through all addresses to be programmed is defined as a program loop. The number of loops (N) required is a function of the program pulse width (t_{PW}) according to $N \times t_{PW} \geq 100$ ms.

For program verification, program loops and read loops may be alternated as shown in waveform B.

Program Characteristics

$T_A = 25°C$, $V_{CC} = +5V \pm 5\%$, $V_{DD} = +12V \pm 5\%$, $V_{BB} = -5V \pm 5\%$, $V_{SS} = 0V$, $\overline{CS}$/WE = +12V, Unless Otherwise Noted.

Symbol	Parameter	Min.	Typ.	Max.	Units
t_{AS}	Address Setup Time	10			μs
t_{CSS}	$\overline{CS}$/WE Setup Time	10			μs
t_{DS}	Data Setup Time	10			μs
t_{AH}	Address Hold Time	1			μs
t_{CH}	$\overline{CS}$/WE Hold Time	.5			μs
t_{DH}	Data Hold Time	1			μs
t_{DF}	Chip Deselect to Output Float Delay	0		120	ns
t_{DPR}	Program To Read Delay			10	μs
t_{PW}	Program Pulse Width	.1		1.0	ms
t_{PR}	Program Pulse Rise Time	.5		2.0	μs
t_{PF}	Program Pulse Fall Time	.5		2.0	μs
I_P	Programming Current		10	20	mA
V_P	Program Pulse Amplitude	25		27	V

NOTE: Intel's standard product warranty applies only to devices programmed to specifications described herein.

Erasing Procedure

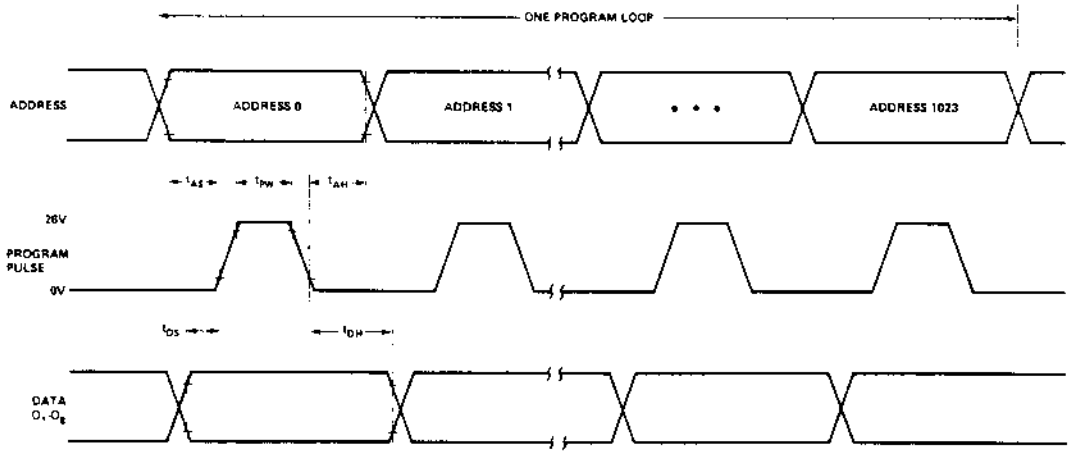
The 8708/8704 may be erased by exposure to high intensity short-wave ultraviolet light at a wavelength of 2537Å. The recommended integrated dose. (i.e., UV intensity x exposure time) is 10W-sec/cm^2. Examples of ultraviolet sources which can erase the 8708/8704 in 20 to 30 minutes are the Model UVS-54 and Model S-52 short-wave ultraviolet lamps manufactured by Ultra-Violet Products, Inc. (5114 Walnut Grove Avenue, San Gabriel, California). The lamps should be used without short-wave filters, and the 8708/8704 to be erased should be placed about one inch away from the lamp tubes.

Waveforms

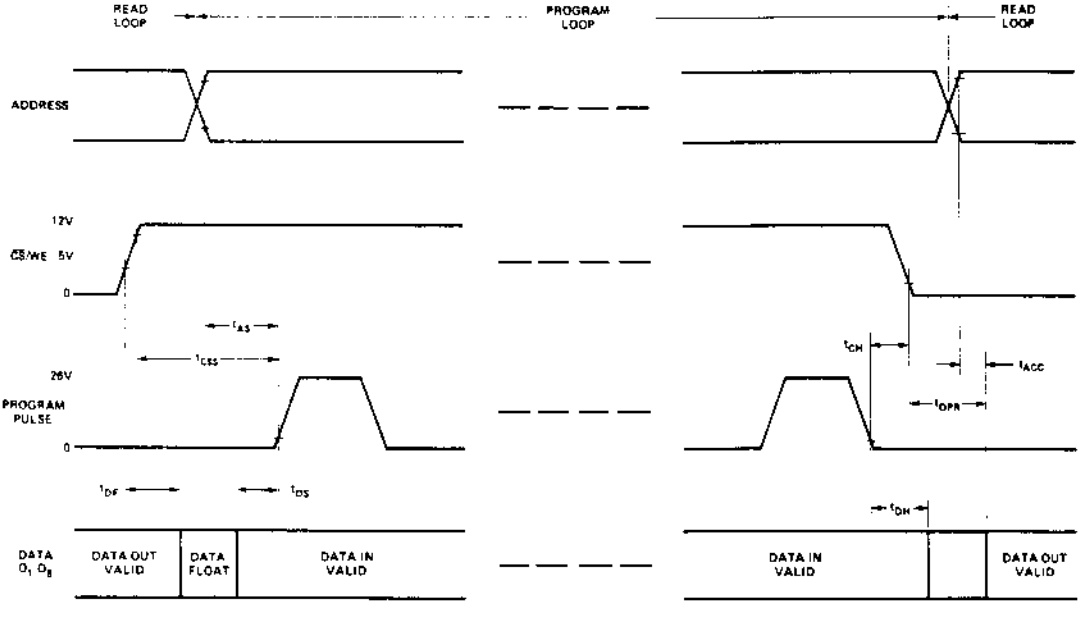
(Logic levels and timing reference levels same as in the Read Mode unless noted otherwise.)

A) Program Mode

$\overline{CS}/WE$ = +12V

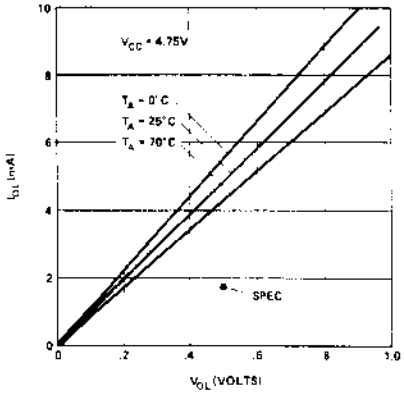


B) Read/Program/Read Transitions

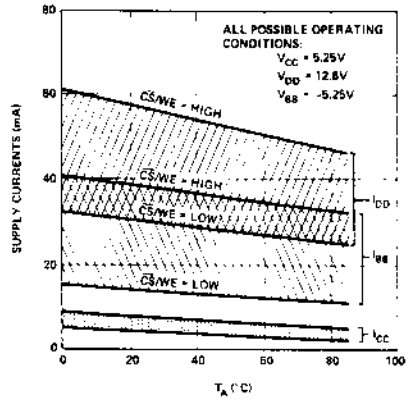


Typical Characteristics (Nominal supply voltages unless otherwise noted):

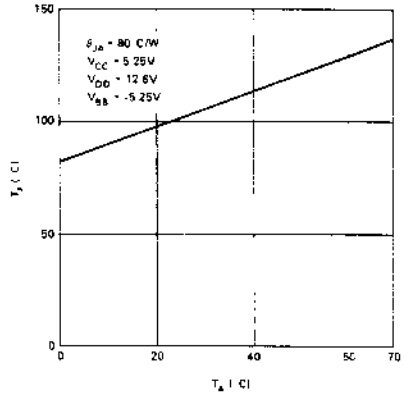
OUTPUT SINK CURRENT
VS. OUTPUT VOLTAGE



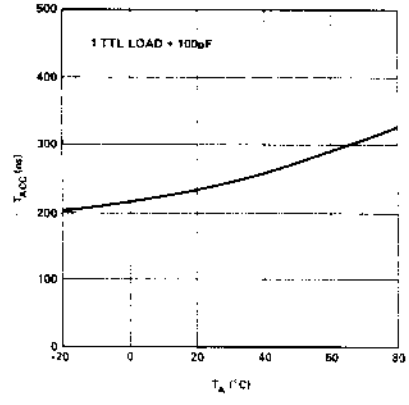
RANGE OF SUPPLY CURRENTS
VS. TEMPERATURE



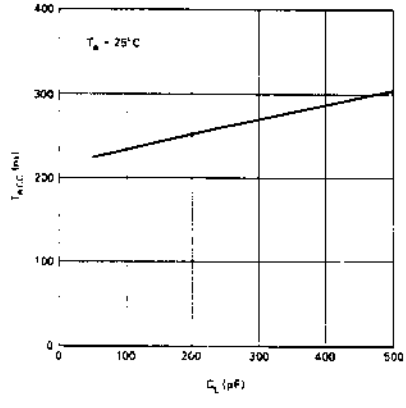
MAXIMUM JUNCTION TEMPERATURE
VS. AMBIENT TEMPERATURE



ACCESS TIME VS. TEMPERATURE



ACCESS TIME
VS. LOAD CAPACITANCE



Silicon Gate MOS 8302

2048 BIT MASK PROGRAMMABLE READ ONLY MEMORY

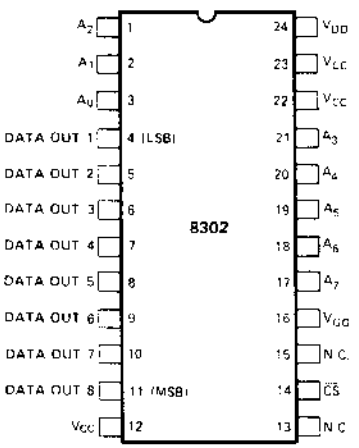
- **Access Time — 1 μsec Max.**
- **Fully Decoded, 256 x 8 Organization**
- **Inputs and Outputs TTL Compatible**
- **Three-State Output — OR-Tie Capability**
- **Static MOS — No Clocks Required**
- **Simple Memory Expansion — Chip Select Input Lead**
- **24-Pin Dual-In-Line Hermetically Sealed Ceramic Package**

The Intel® 8302 is a fully decoded 256 word by 8 bit metal mask ROM. It is ideal for large volume production runs of microcomputer systems initially using the 8702A erasable and electrically programmable ROM. The 8302 has the same pinning as the 8702A.

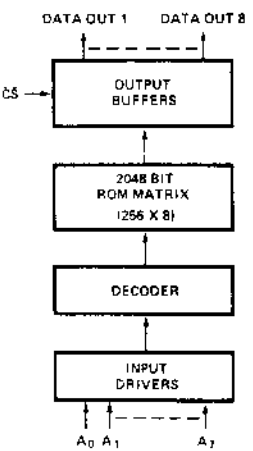
The 8302 is entirely static — no clocks are required. Inputs and outputs of the 8302 are TTL compatible. The output is three-state for OR-tie capability. A separate chip select input allows easy memory expansion. The 8302 is packaged in a 24 pin dual-in-line hermetically sealed ceramic package.

The 8302 is fabricated with p-channel silicon gate technology. This low threshold allows the design and production of higher performance MOS circuits and provides a higher functional density on a monolithic chip than conventional MOS technologies.

PIN CONFIGURATION



BLOCK DIAGRAM



PIN NAMES

A_0-A_7	ADDRESS INPUTS
$\overline{CS}$	CHIP SELECT INPUT
DO_1-DO_8	DATA OUTPUTS

Absolute Maximum Ratings *

Ambient Temperature Under Bias	0°C to +70°C
Storage Temperature	−65°C to +125°C
Soldering Temperature of Leads (10 sec)	+300°C
Power Dissipation	2 Watts
Input Voltages and Supply Voltages with respect to V_{CC}	+0.5V to −20V

*COMMENT

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or at any other condition above those indicated in the operational sections of this specification is not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

READ OPERATION

D.C. and Operating Characteristics

T_A = 0°C to 70°C, V_{CC} = +5V±5%, V_{DD} = −9V±5%, $V_{GG}^{(1)}$ = −9V±5%, unless otherwise noted.

SYMBOL	TEST	MIN.	TYP(2)	MAX.	UNIT	CONDITIONS
I_{IL}	Address and Chip Select Input Load Current			1	µA	V_{IN} = 0.0V
I_{LO}	Output Leakage Current			1	µA	V_{OUT} = 0.0V, $\overline{CS}$ = V_{CC} −2
I_{DDO}	Power Supply Current		5	10	mA	V_{GG} = V_{CC}, $\overline{CS}$ = V_{CC} −2, I_{OL} = 0.0mA, T_A = 25°C
I_{DD1}	Power Supply Current		35	50	mA	$\overline{CS}$ = V_{CC} −2, I_{OL} = 0.0mA, T_A = 25°C
I_{DD2}	Power Supply Current		32	46	mA	$\overline{CS}$ = 0.0, I_{OL} = 0.0mA, T_A = 25°C
I_{DD3}	Power Supply Current		38.5	60	mA	$\overline{CS}$ = V_{CC} −2, I_{OL} = 0.0mA, T_A = 0°C
I_{CF1}	Output Clamp Current		8	14	mA	V_{OUT} = −1.0V, T_A = 0°C
I_{CF2}	Output Clamp Current			13	mA	V_{OUT} = −1.0V, T_A = 25°C
I_{GG}	Gate Supply Current			1	µA	
V_{IL1}	Input Low Voltage for TTL Interface	−1.0		0.65	V	
V_{IL2}	Input Low Voltage for MOS Interface	V_{DD}		V_{CC} −6	V	
V_{IH}	Address and Chip Select Input High Voltage	V_{CC} −2		V_{CC} +0.3	V	
I_{OL}	Output Sink Current	1.6	4		mA	V_{OUT} = 0.45V
I_{OH}	Output Source Current	−2.0			mA	V_{OUT} = 0.0V
V_{OL}	Output Low Voltage		−.7	0.45	V	I_{OL} = 1.6mA
V_{OH}	Output High Voltage	3.5	4.5		V	I_{OH} = −100 µA

Continuous Operation

Note 1. V_{GG} may be clocked to reduce power dissipation. In this mode average I_{DD} increases in proportion to V_{GG} duty cycle.
Note 2. Typical values are at nominal voltages and T_A = 25°C.

A.C. Characteristics

T_A = 0°C to +70°C, V_{CC} = +5V ±5%, V_{DD} = −9V ±5%, V_{GG} = −9V ±5% unless otherwise noted

SYMBOL	TEST	MINIMUM	TYPICAL	MAXIMUM	UNIT
Freq.	Repetition Rate			1	MHz
t_{OH}	Previous read data valid			100	ns
t_{ACC}	Address to output delay		.700	1	µs
t_{DVGG}	Clocked V_{GG} set up	1			µs
t_{CS}	Chip select delay			200	ns
t_{CO}	Output delay from $\overline{CS}$			500	ns
t_{OD}	Output deselect			300	ns
t_{OHC}	Data out hold in clocked V_{GG} mode (Note 1)			5	µs

Note 1. The output will remain valid for t_{OHC} as long as clocked V_{GG} is at V_{CC}. An address change may occur as soon as the output is sensed (clocked V_{GG} may still be at V_{CC}). Data becomes invalid for the old address when clocked V_{GG} is returned to V_{GG}.

Capacitance* T_A = 25°C

SYMBOL	TEST	MINIMUM	TYPICAL	MAXIMUM	UNIT	CONDITIONS
C_{IN}	Input Capacitance		5	10	pF	$V_{IN} = V_{CC}$, $\overline{CS} = V_{CC}$, $V_{OUT} = V_{CC}$, $V_{GG} = V_{CC}$ — All unused pins are at A.C. ground
C_{OUT}	Output Capacitance		5	10	pF	
$C_{V_{GG}}$	V_{GG} Capacitance (Clocked V_{GG} Mode)			30	pF	

*This parameter is periodically sampled and is not 100% tested.

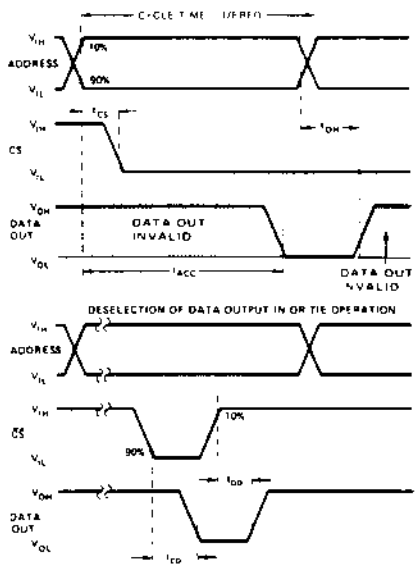
Switching Characteristics

Conditions of Test:

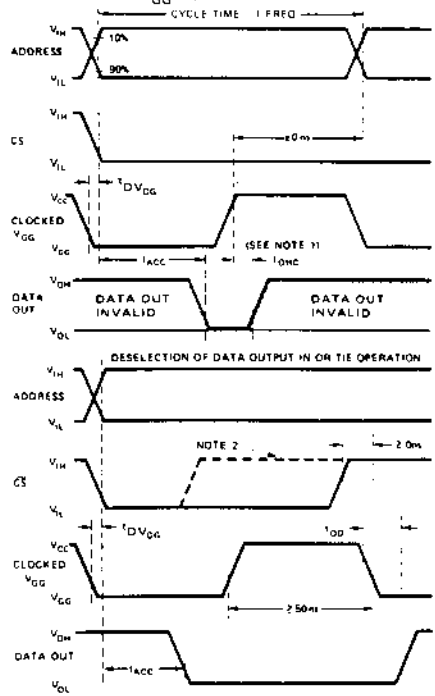
Input pulse amplitudes: 0 to 4V; t_R, t_F ≤ 50 ns

Output load is 1 TTL gate; measurements made at output of TTL gate (t_{PD} ≤ 15 ns)

A) Constant V_{GG} Operation



B) Clocked V_{GG} Operation

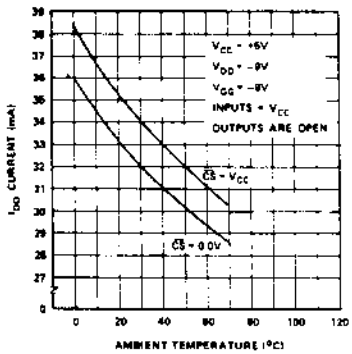


NOTE 1: The output will remain valid for t_{OHC} as long as clocked V_{GG} is at V_{CC}. An address change may occur as soon as the output is sensed (clocked V_{GG} may still be at V_{CC}). Data becomes invalid for the old address when clocked V_{GG} is returned to V_{GG}.

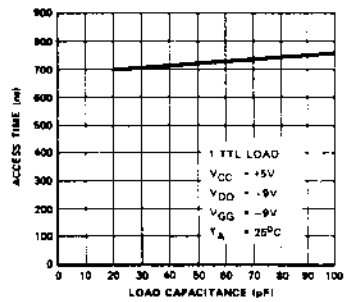
NOTE 2: If $\overline{CS}$ makes a transition from V_{IL} to V_{IH} while clocked V_{GG} is at V_{GG}, then deselection of output occurs at t_{OD} as shown in static operation with constant V_{GG}.

Typical Characteristics

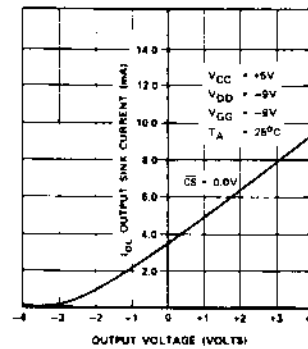
I_{DD} CURRENT VS. TEMPERATURE



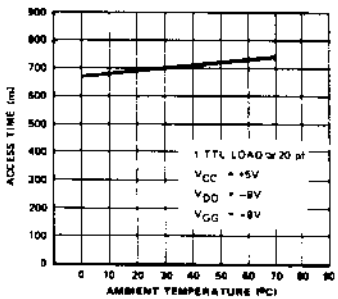
ACCESS TIME VS. LOAD CAPACITANCE



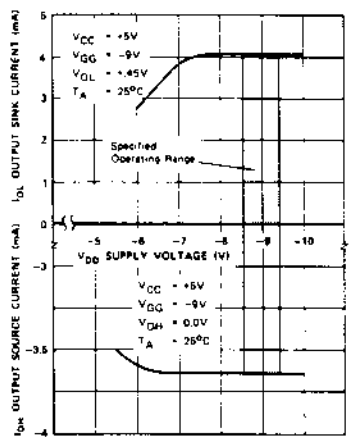
OUTPUT SINK CURRENT VS. OUTPUT VOLTAGE



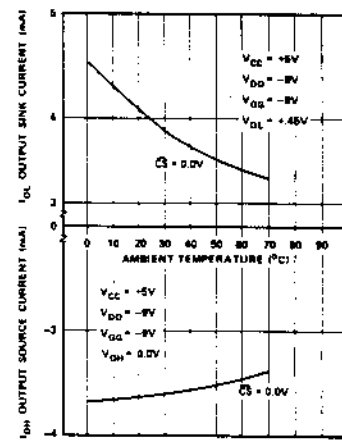
ACCESS TIME VS. TEMPERATURE



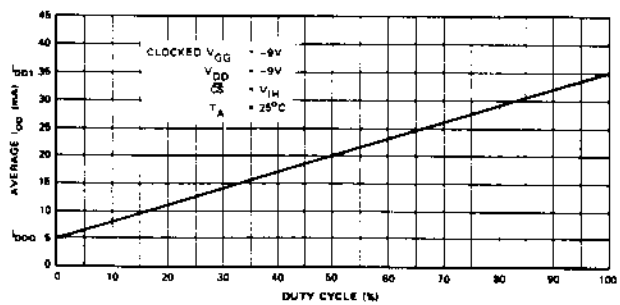
OUTPUT CURRENT VS. V_{DD} SUPPLY VOLTAGE



OUTPUT CURRENT VS. TEMPERATURE



AVERAGE CURRENT VS. DUTY CYCLE FOR CLOCKED V_{GG}



Silicon Gate MOS 8308

8192 BIT STATIC MOS READ ONLY MEMORY
Organization -- 1024 Words x 8 Bits

- Fast Access – 450 ns
- Directly Compatible with 8080 CPU at Maximum Processor Speed
- Two Chip Select Inputs for Easy Memory Expansion
- Directly TTL Compatible – All Inputs and Outputs
- Three State Output – OR-Tie Capability
- Fully Decoded
- Standard Power Supplies +12V DC, ±5V DC

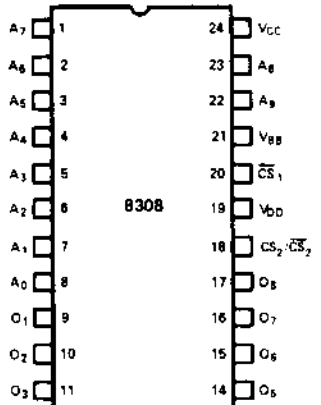
The Intel® 8308 is an 8,192 bit static MOS mask programmable Read Only Memory organized as 1024 words by 8-bits. This ROM is designed for 8080 microcomputer system applications where high performance, large bit storage, and simple interfacing are important design objectives. The inputs and outputs are fully TTL compatible.

A pin for pin compatible electrically programmed erasable ROM, the Intel® 8708, is available for system development and small quantity production use.

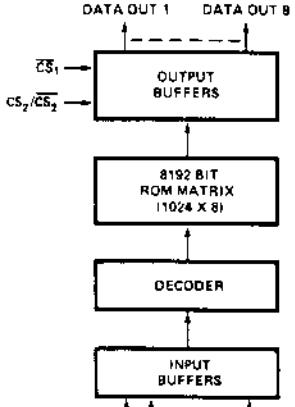
Two Chip Selects are provided – $\overline{CS}_1$ which is negative true, and $CS_2/\overline{CS}_2$ which may be programmed either negative or positive true at the mask level.

The 8308 read only memory is fabricated with N-channel silicon gate technology. This technology provides the designer with high performance, easy-to-use MOS circuits.

PIN CONFIGURATION



BLOCK DIAGRAM



PIN NAMES

A_0-A_9	ADDRESS INPUTS
O_1-O_8	DATA OUTPUTS
$\overline{CS}_1$, CS_2	CHIP SELECT INPUTS

Absolute Maximum Ratings*

Ambient Temperature Under Bias . . . . . -25°C to +85°C
Storage Temperature . . . . . -65°C to +150°C
Voltage On Any Pin With Respect
To V_{BB} . . . . . -0.3V to 20V
Power Dissipation . . . . . 1.0 Watt

*COMMENT

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

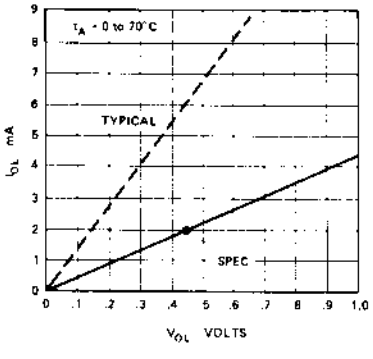
D.C. and Operating Characteristics

T_A = 0°C to +70°C, V_{CC} = 5V ±5%; V_{DD} = 12V ±5%, V_{BB} = -5V ±5%, V_{SS} = 0V Unless Otherwise Specified.

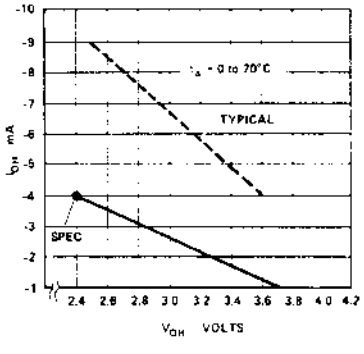
Symbol	Parameter	Limits			Unit	Test Conditions
		Min.	Typ.[1]	Max.		
I_{LI}	Input Load Current (All Input Pins Except $\overline{CS}_1$)			10	µA	V_{IN} = 0 to 5.25V
I_{LCL}	Input Load Current on $\overline{CS}_1$			1.6	mA	V_{IN} = 0.45V
I_{LPC}	Input Peak Load Current on $\overline{CS}_1$			4	mA	V_{IN} = 0.8V to 3.3V
I_{LKC}	Input Leakage Current on $\overline{CS}_1$			10	µA	V_{IN} = 3.3V to 5.25V
I_{LO}	Output Leakage Current			10	µA	Chip Deselected
V_{IL}	Input "Low" Voltage	V_{SS}-1		0.8V	V	
V_{IH}	Input "High" Voltage	3.3		V_{CC}+1.0	V	
V_{OL}	Output "Low" Voltage			0.45	V	I_{OL} = 2mA
V_{OH1}	Output "High" Voltage	2.4			V	I_{OH} = -4mA
V_{OH2}	Output "High" Voltage	3.7			V	I_{OH} = -1mA
I_{CC}	Power Supply Current V_{CC}		.8	2	mA	
I_{DD}	Power Supply Current V_{DD}		32	60	mA	
I_{BB}	Power Supply Current V_{BB}		10µA	1	mA	
P_D	Power Dissipation			775	mW	

NOTE 1: Typical values for T_A = 25°C and nominal supply voltage

D.C. OUTPUT CHARACTERISTICS



D.C. OUTPUT CHARACTERISTICS



A.C. Characteristics

T_A = 0°C to +70°C, V_{CC} = +5V ±5%, V_{DD} = +12V ±5%, V_{BB} = −5V ±5%, V_{SS} = 0V, Unless Otherwise Specified.

Symbol	Parameter	Limits[2]			Unit
		Min.	Typ.	Max.	
t_{ACC}	Address to Output Delay Time		200	450	ns
t_{CO_1}	Chip Select 1 to Output Delay Time		85	160	ns
t_{CO_2}	Chip Select 2 to Output Delay Time		125	220	ns
t_{DF}	Chip Deselect to Output Data Float Time		125	220	ns

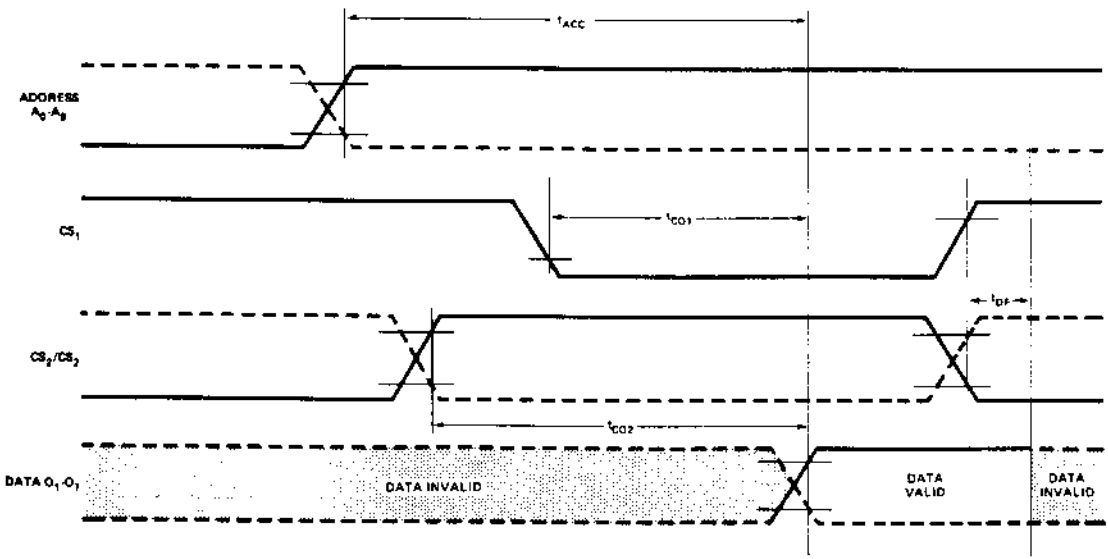
NOTE 2: Refer to conditions of Test for A.C. Characteristics. Add 50 nanoseconds (worst case) to specified values at V_{OH} = 3.7V @ I_{OH} = −1mA, C_L = 100pF.

CONDITIONS OF TEST FOR A.C. CHARACTERISTICS

Output Load . . . . . 1 TTL Gate, and C_{LOAD} = 100pF
Input Pulse Levels . . . . . .65V to 3.3V
Input Pulse Rise and Fall Times . . . . . 20 nsec
Timing Measurement Reference Level
. . . . . 2.4V V_{IH}, V_{OH}; 0.8V V_{IL}, V_{OL}

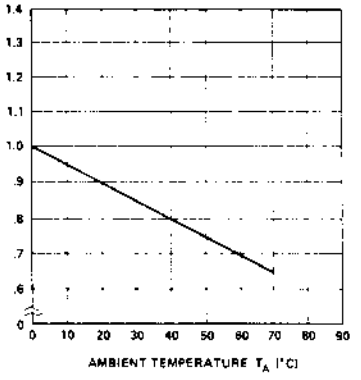
CAPACITANCE T_A = 25°C, f = 1 MHz, V_{BB} = −5V, V_{DD}, V_{CC} and all other pins tied to V_{SS}.

Symbol	Test	Limits	
		Typ.	Max.
C_{IN}	Input Capacitance		6pF
C_{OUT}	Output Capacitance		12pF

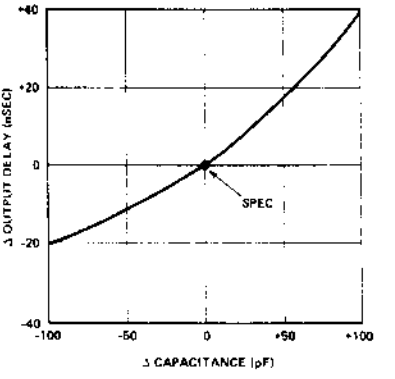


Typical Characteristics (Nominal supply voltages unless otherwise noted.)

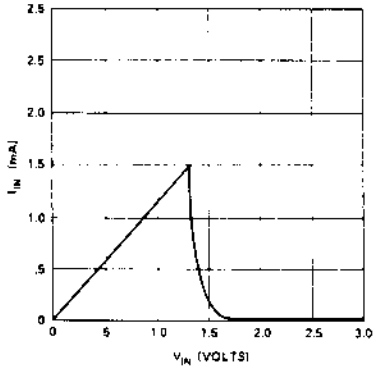
I_{DD} VS. TEMPERATURE (NORMALIZED)



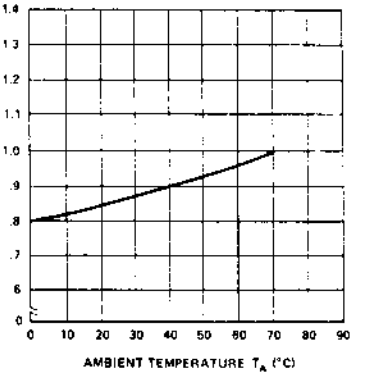
Δ OUTPUT CAPACITANCE VS. Δ OUTPUT DELAY



$\overline{CS_1}$ INPUT CHARACTERISTICS



T_{ACC} VS. TEMPERATURE (NORMALIZED)



MCS™ CUSTOM ROM ORDER FORM

8308 ROM

CUSTOMER _____

P.O. NUMBER _____

DATE _____

For Intel use only

S# _____ PPPP _____

STD _____ ZZ _____

_____ DD _____

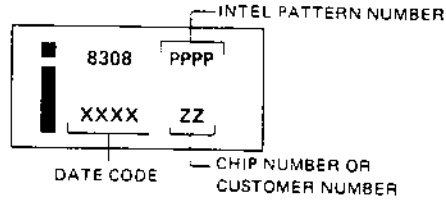
APP _____ DATE _____

All custom 8308 ROM orders must be submitted on this form. Programming information should be sent in the form of computer punched cards or punched paper tape per the formats designated on this order form. Additional forms are available from Intel.

MARKING

The marking as shown at the right must contain the Intel logo, the product type (P8308), the 4-digit Intel pattern number (PPPP), a date code (XXXX), and the 2-digit chip number (DD). An optional customer identification number may be substituted for the chip number (ZZ). Optional Customer Number (maximum 9 characters or spaces).

CUSTOMER NUMBER _____



MASK OPTION SPECIFICATIONS

A. CHIP NUMBER (CHIP SELECT OPTION)

Must be specified 0 or 1.

The chip number will be coded in terms of positive logic where a logic "1" is high level input.

Chip Select Truth Table

Chip Number	$\overline{CS1}$	CS2	Selected
0	0	0	Yes
1	0	1	Yes
0	1	0	No
1	1	1	No

Chip Number _____

B. ROM Truth Table Format

Programming information should be sent in the form of computer punched cards or punched paper tape. In either case, a printout of the truth table should be accompanied with the order.

The following general format is applicable to the programming information sent to Intel:

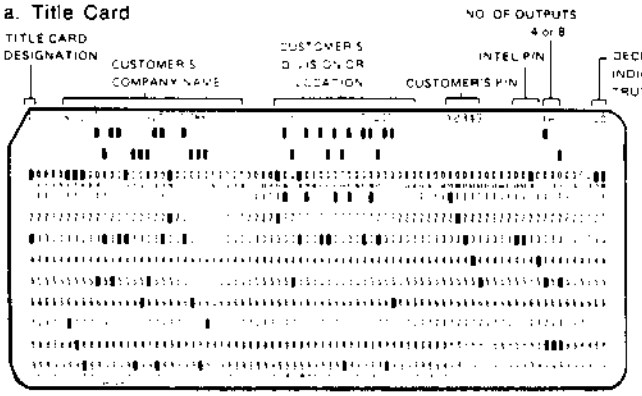
- Data fields should be ordered beginning with the least significant address (0000) and ending with the most significant address (1023).
- A data field should start with the most significant bit and end with the least significant bit.
- The data field should consist of P's and N's. A P is to indicate a high level output (most positive) and an N a low level output (most negative). In terms of positive logic, a P is defined as a logic "1" and an N is defined as a logic "0". If the programming information is sent on a punched paper tape, then a start character, B, and an end character, F, must be used in the data field. See paragraph 2.

1. Punched Card Format

An 80-column Hollerith card (preferably interpreted) punched by an IBM 026 or 029 keypunch should be submitted. The first card will be a title card; the format is as follows:

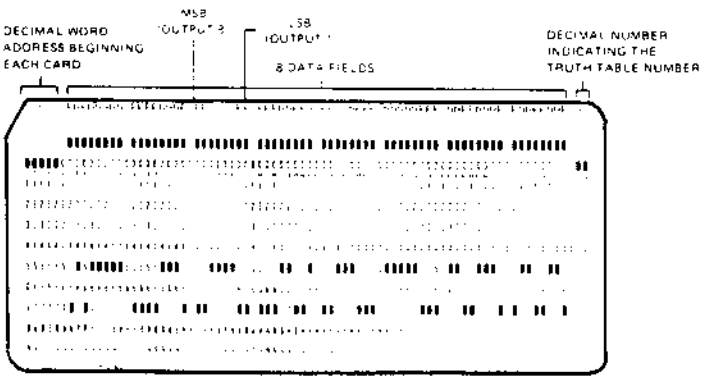
MCS™ CUSTOM ROM ORDER FORM 8308

a. Title Card



Column	Data
1	Punch a T
2–5	Blank
6–30	Customer Company Name
31–34	Blank
35–54	Customer's Company Division or location
55–57	Blank
58–66	Customer Part Number
67	Blank
68–75	Punch the Intel 4-digit basic part number and in ( ) the number of output bits e.g., 8308(8).
76–78	Blank
79–80	Punch a 2-digit decimal number to identify the truth table number (mask programmed chip select number).

b. For a 1024 word X 8-bit organization only, cards 2 and the following cards should be punched as shown.



Column	Data
1–5	Punch the 5-digit decimal equivalent of the binary coded location which begins each card. The address is right justified, i.e., 00000, 00008, 00016 etc.
6	Blank
7–14	Data Field
15	Blank
16–23	Data Field
33	Blank
34–41	Data Field
42	Blank
43–50	Data Field
51	Blank
52–59	Data Field
60	Blank
61–68	Data Field
69	Blank
70–77	Data Field
78	Blank
79–80	Punch same 2-digit decimal number as in title card.

2. Paper Tape Format

1" wide paper tape using 7- or 8-bit ASCII code, such as a model 33 ASR teletype produces, or the 11/16" wide paper tape using a 5-bit Baudot code, such as a Telex produces.

The format requirements are as follows:

a. All word fields are to be punched in consecutive order, starting with word field 0 (all addresses low). There must be exactly 1024 word fields for the 1024 X 8 ROM organization.

b. Each word field must begin with the start character B and end with the stop character F. There must be exactly 8 data characters between the B and F.

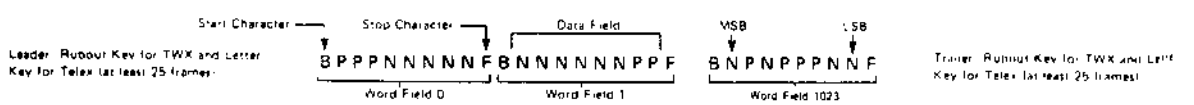
NO OTHER CHARACTERS, SUCH AS RUBOUTS, ARE ALLOWED ANYWHERE IN A WORD FIELD. If in preparing a tape an error is made, the entire word field, including the B and F, must be rubbed out. Within the word field, a P results in a high level output and an N results in a low level output.

c. Preceding the first word field and following the last word field, there must be a leader/trailer length of *at least 25 characters. This should consist of rubout or null punches (letter key for Telex tapes).*

d. Between word fields, comments not containing B's or F's may be inserted. Carriage return and line feed characters should be inserted as a "comment") just before each word field (or at least between every four word fields). When these carriage returns, etc., are inserted, the tape may be easily listed on the teletype for purposes of error checking. The customer may also find it helpful to insert the word number (as a comment) at least every four word fields.

e. Included in the tape before the leader should be the customer's complete Telex or TWX number and, if more than one pattern is being transmitted, the ROM pattern number.

f. MSB and LSB are the most and least significant bit of the device outputs. Refer to the data sheet for the pin numbers.



Silicon Gate MOS ROM **8316A**

16,384 BIT STATIC MOS READ ONLY MEMORY
Organization—2048 Words x 8 Bits
Access Time-850 ns max

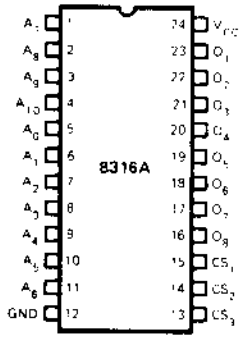
- **Single +5 Volts Power Supply Voltage**
- **Directly TTL Compatible — All Inputs and Outputs**
- **Low Power Dissipation of 31.4 μW/Bit Maximum**
- **Three Programmable Chip Select Inputs for Easy Memory Expansion**
- **Three-State Output — OR-Tie Capability**
- **Fully Decoded — On Chip Address Decode**
- **Inputs Protected — All Inputs Have Protection Against Static Charge**

The Intel® 8316A is a 16,384-bit static MOS read only memory organized as 2048 words by 8 bits. This ROM is designed for microcomputer memory applications where high performance, large bit storage, and simple interfacing are important design objectives.

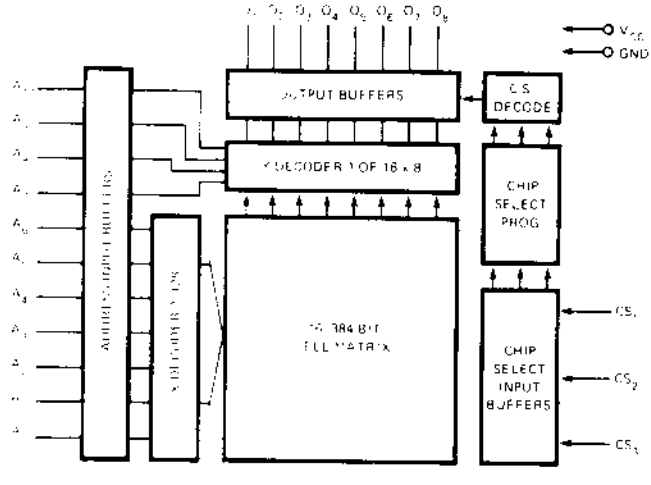
The inputs and outputs are fully TTL compatible. This device operates with a single +5V power supply. The three chip select inputs are programmable. Any combination of active high or low level chip select inputs can be defined and the desired chip select code is fixed during the masking process. These three programmable chip select inputs, as well as OR-tie compatibility on the outputs, facilitate easy memory expansion.

The 8316A read only memory is fabricated with N-channel silicon gate technology. This technology provides the designer with high performance, easy-to-use MOS circuits. Only a single +5V power supply is needed and all devices are directly TTL compatible.

PIN CONFIGURATION



BLOCK DIAGRAM



PIN NAMES

A_0 A_{10}	ADDRESS INPUTS
O_1 O_8	DATA OUTPUTS
CS_1 CS_3	PROGRAMMABLE CHIP SELECT INPUTS

ABSOLUTE MAXIMUM RATINGS*

Ambient Temperature Under Bias . . . . . 0°C to 70°C
Storage Temperature . . . . . -65°C to +150°C
Voltage On Any Pin With Respect To Ground . . . . . -0.5V to +7V
Power Dissipation . . . . . 1.0 Watt

*COMMENT: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

D.C. AND OPERATING CHARACTERISTICS

T_A = 0°C to +70°C, V_{CC} = 5V ±5% unless otherwise specified

SYMBOL	PARAMETER	LIMITS MIN.	LIMITS TYP.[1]	LIMITS MAX.	UNIT	TEST CONDITIONS
I_{LI}	Input Load Current (All Input Pins)			10	μA	V_{IN} = 0 to 5.25V
I_{LOH}	Output Leakage Current			10	μA	CS = 2.2V, V_{OUT} = 4.0V
I_{LOL}	Output Leakage Current			-20	μA	CS = 2.2V, V_{OUT} = 0.45V
I_{CC}	Power Supply Current		40	98	mA	All inputs 5.25V Data Out Open
V_{IL}	Input "Low" Voltage	-0.5		0.8	V	
V_{IH}	Input "High" Voltage	2.0		V_{CC}+1.0V	V	
V_{OL}	Output "Low" Voltage			0.45	V	I_{OL} = 2.0 mA
V_{OH}	Output "High" Voltage	2.2			V	I_{OH} = -100 μA

[1] Typical values for T_A = 25°C and nominal supply voltage.

A.C. CHARACTERISTICS

T_A = 0°C to +70°C, V_{CC} = +5V ±5% unless otherwise specified

SYMBOL	PARAMETER	LIMITS MIN.	LIMITS TYP.[1]	LIMITS MAX.	UNIT
t_A	Address to Output Delay Time		400	850	nS
t_{CO}	Chip Select to Output Enable Delay Time			300	nS
t_{DF}	Chip Deselect to Output Data Float Delay Time	0		300	nS

CONDITIONS OF TEST FOR A.C. CHARACTERISTICS

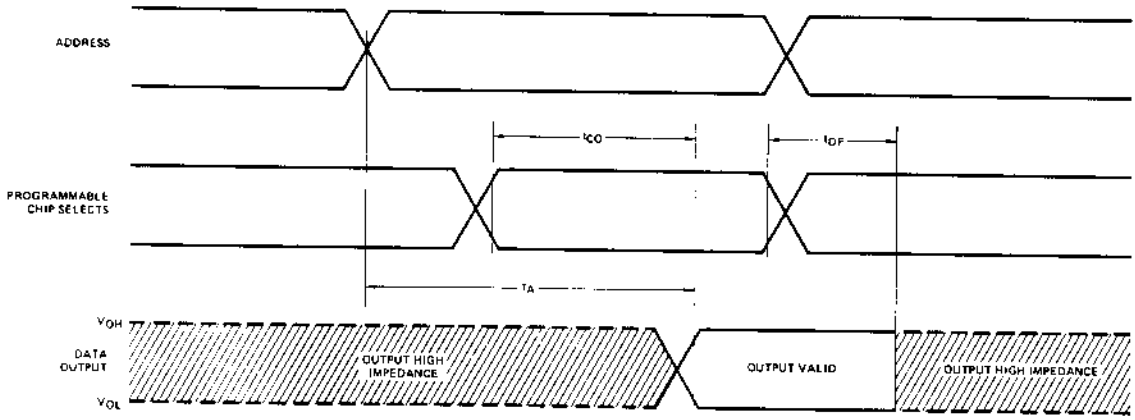
Output Load . . . 1 TTL Gate, and C_{LOAD} = 100 pF
Input Pulse Levels . . . . . 0.8 to 2.0V
Input Pulse Rise and Fall Times . (10% to 90%) 20 nS
Timing Measurement Reference Level
Input 1.5V
Output . . . . . 0.45V to 2.2V

CAPACITANCE[2] T_A = 25°C, f = 1 MHz

SYMBOL	TEST	LIMITS TYP.	LIMITS MAX.
C_{IN}	All Pins Except Pin Under Test Tied to AC Ground	4 pF	10 pF
C_{OUT}	All Pins Except Pin Under Test Tied to AC Ground	8 pF	15 pF

[2] This parameter is periodically sampled and is not 100% tested.

WAVEFORMS

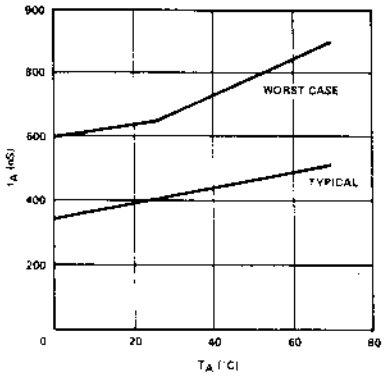


16K ROM PROTOTYPING

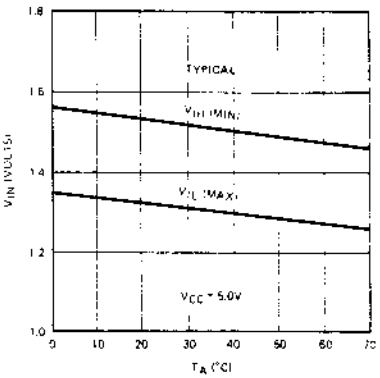
ROM systems may be developed and programs may be verified using Intel's 1702A or 2708 PROMs.

TYPICAL D.C. CHARACTERISTICS

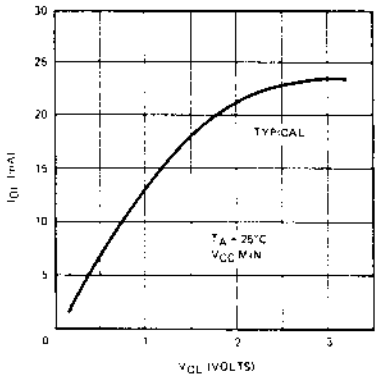
ACCESS TIME VS. AMBIENT TEMPERATURE



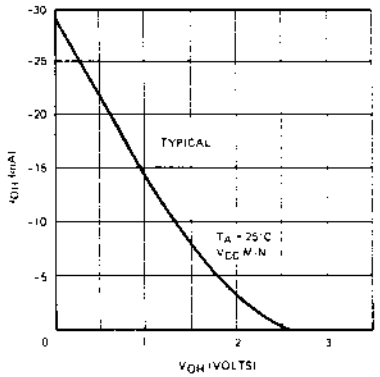
V_{IN} LIMITS VS. TEMPERATURE



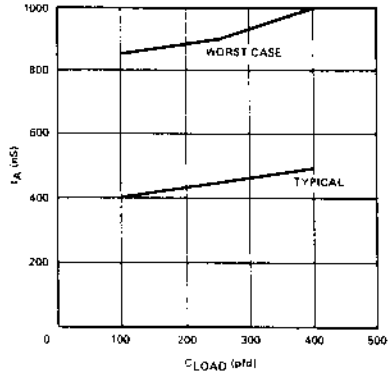
OUTPUT SINK CURRENT VS. OUTPUT VOLTAGE



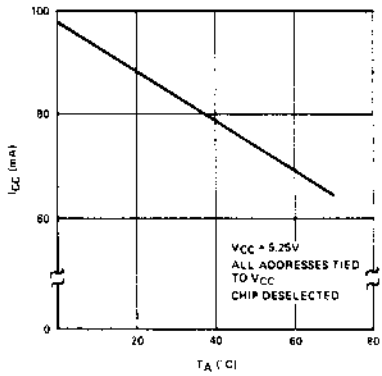
OUTPUT SOURCE CURRENT VS. OUTPUT VOLTAGE



ACCESS TIME VS. LOAD CAPACITANCE



STATIC I_{CC} VS. AMBIENT TEMPERATURE WORST CASE



MCS™ CUSTOM ROM ORDER FORM

8316A ROM

CUSTOMER _____

P.O. NUMBER _____

DATE _____

For Intel use only

S# _____ PPPP _____

STD _____ ZZ _____

_____ DD _____

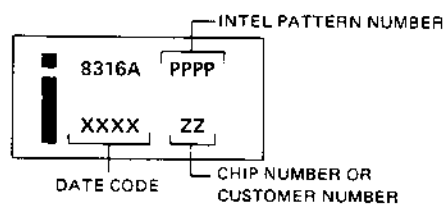
APP _____ DATE _____

All custom 8316A ROM orders must be submitted on this form. Programming information should be sent in the form of computer punched cards or punched paper tape per the formats designated on this order form. Additional forms are available from Intel.

MARKING

The marking as shown at the right must contain the Intel® logo, the product type (P8316A), the 4-digit Intel pattern number (PPPP), a date code (XXXX), and the 2-digit chip number (DD). An optional customer identification number may be substituted for the chip number (ZZ). Optional Customer Number (maximum 9 characters or spaces).

CUSTOMER NUMBER _____



MASK OPTION SPECIFICATIONS

A. CHIP NUMBER _____ (Must be specified—any number from 0 through 7—DD).

The chip number will be coded in terms of positive logic where a logic "1" is a high level input.

Chip Number	CS3	CS2	CS1
0	0	0	0
1	0	0	1
2	0	1	0
3	0	1	1
4	1	0	0
5	1	0	1
6	1	1	0
7	1	1	1

B. ROM Truth Table Format

Programming information should be sent in the form of computer punched cards or punched paper tape. In either case, a printout of the truth table should be accompanied with the order.

The following general format is applicable to the programming information sent to Intel:

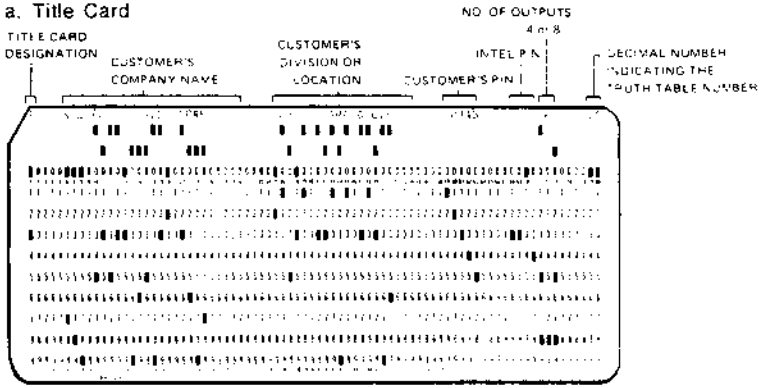
- Data fields should be ordered beginning with the least significant address (0000) and ending with the most significant address (2047).
- A data field should start with the most significant bit and end with the least significant bit.
- The data field should consist of P's and N's. A P is to indicate a high level output (most positive) and an N a low level output (most negative). In terms of positive logic, a P is defined as a logic "1" and an N is defined as a logic "0". If the programming information is sent on a punched paper tape, then a start character, B, and an end character, F, must be used in the data field.

1. Punched Card Format

An 80-column Hollerith card (preferably interpreted) punched by an IBM 026 or 029 keypunch should be submitted. The first card will be a title card; the format is as follows:

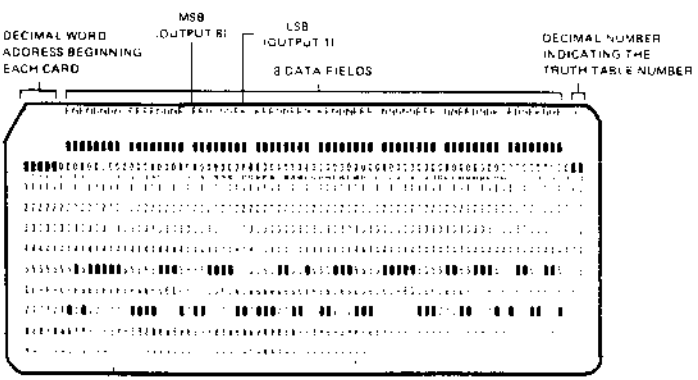
MCS™ CUSTOM ROM ORDER FORM

a. Title Card



Column	Data
1	Punch a T
2–5	Blank
6–30	Customer Company Name
31–34	Blank
35–54	Customer's Company Division or location
55–57	Blank
58–66	Customer Part Number
67	Blank
68–75	Punch the Intel 4-digit basic part number and in ( ) the number of output bits, e.g., 8316A(8).
76–78	Blank
79–80	Punch a 2-digit decimal number to identify the truth table number (mask programmed chip select number).

b. For a 2048 word X 8-bit organization only, cards 2 and the following cards should be punched as shown.



Column	Data
1–5	Punch the 5-digit decimal equivalent of the binary coded location which begins each card. The address is right justified, i.e., 00000, 00008, 00016, etc.
6	Blank
7–14	Data Field
15	Blank
16–23	Data Field
33	Blank
34–41	Data Field
42	Blank
43–50	Data Field
51	Blank
52–59	Data Field
60	Blank
61–68	Data Field
69	Blank
70–77	Data Field
78	Blank
79–80	Punch same 2-digit decimal number as in title card.

2. Paper Tape Format

1" wide paper tape using 7- or 8-bit ASCII code, such as a model 33 ASR teletype produces, or the 11/16" wide paper tape using a 5-bit Baudot code, such as a Telex produces.

The format requirements are as follows:

a. All word fields are to be punched in consecutive order, starting with word field 0 (all addresses low). There must be exactly 2048 word fields for the 2048 X 8 ROM organization.

b. Each word field must begin with the start character B and end with the stop character F. There must be exactly 8 data characters between the B and F.

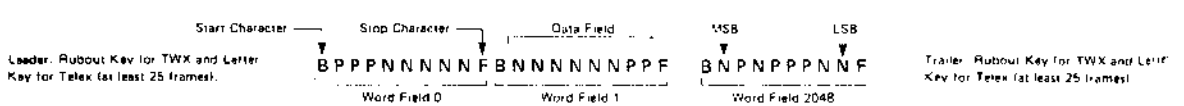
NO OTHER CHARACTERS, SUCH AS RUBOUTS, ARE ALLOWED ANYWHERE IN A WORD FIELD. If in preparing a tape an error is made, the entire word field, including the B and F, must be rubbed out. Within the word field, a P results in a high level output and an N results in a low level output.

c. Preceding the first word field and following the last word field, there must be a leader/trailer length of *at least 25 characters. This should consist of rubout or null punches (letter key for Telex tapes).*

d. Between word fields, comments not containing B's or F's may be inserted. Carriage return and line feed characters should be inserted as a "comment") just before each word field (or at least between every four word fields). When these carriage returns, etc., are inserted, the tape may be easily listed on the teletype for purposes of error checking. The customer may also find it helpful to insert the word number (as a comment) at least every four word fields.

e. Included in the tape before the leader should be the customer's complete Telex or TWX number and, if more than one pattern is being transmitted, the ROM pattern number.

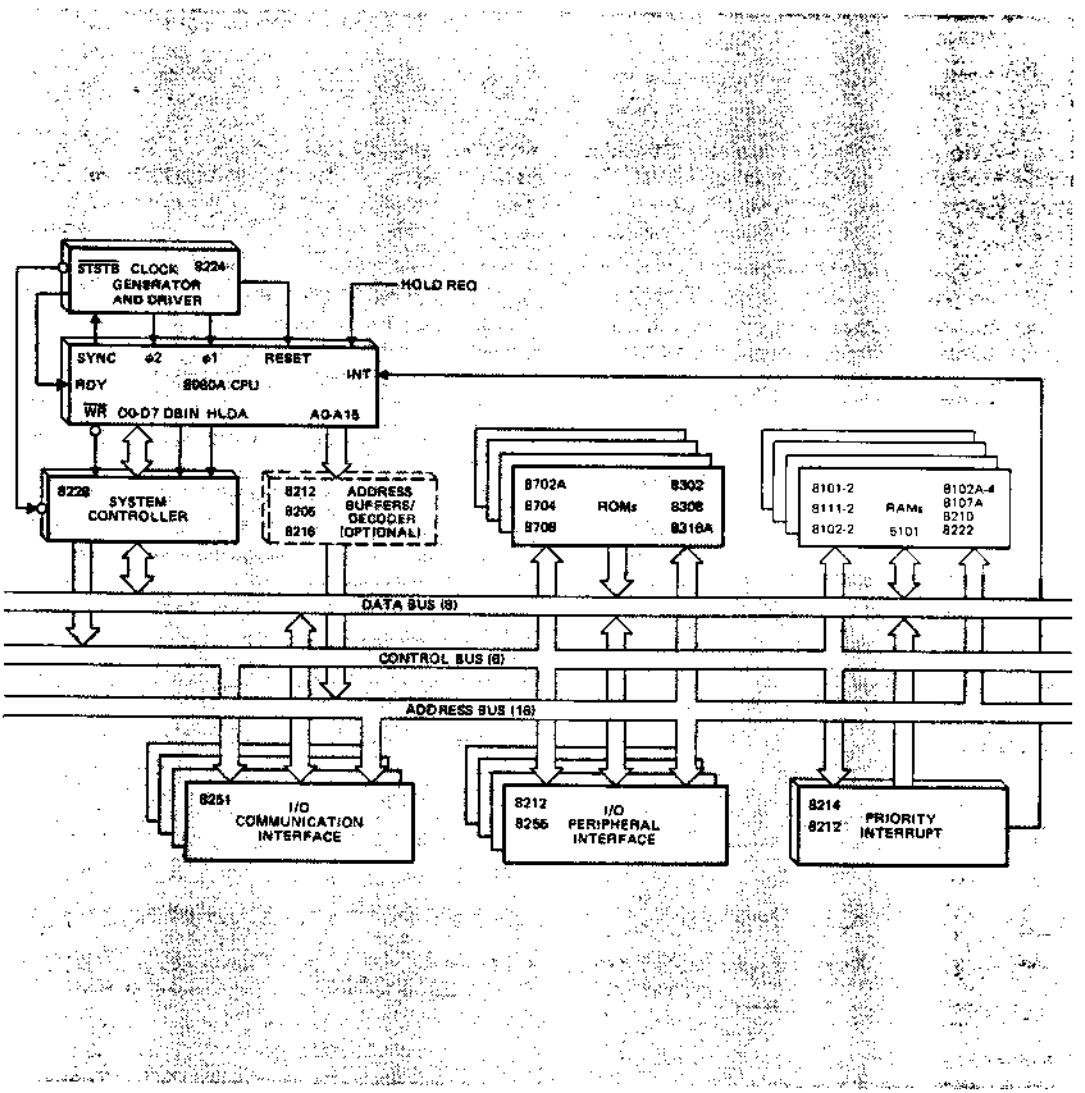
f. MSB and LSB are the most and least significant bit of the device outputs. Refer to the data sheet for the pin numbers.



intel® Microcomputer Systems

RAMs

8102-2 5101
8101-2 8102A-4 8210
8111-2 8107B-4 8222



Silicon Gate MOS **8101-2**

1024 BIT (256 x 4) STATIC MOS RAM WITH SEPARATE I/O

- **256 x 4 Organization to Meet Needs for Small System Memories**
- **Access Time — 850 nsec Max.**
- **Single +5V Supply Voltage**
- **Directly TTL Compatible — All Inputs and Output**
- **Static MOS — No Clocks or Refreshing Required**
- **Simple Memory Expansion — Chip Enable Input**
- **Inputs Protected — All Inputs Have Protection Against Static Charge**
- **Low Cost Packaging — 22 Pin Plastic Dual-In-Line Configuration**
- **Low Power — Typically 150 mW**
- **Three-State Output — OR-Tie Capability**
- **Output Disable Provided for Ease of Use in Common Data Bus Systems**

The Intel® 8101-2 is a 256 word by 4 bit static random access memory element using normally off N-channel MOS devices integrated on a monolithic array. It uses fully DC stable (static) circuitry and therefore requires no clocks or refreshing to operate. The data is read out nondestructively and has the same polarity as the input data.

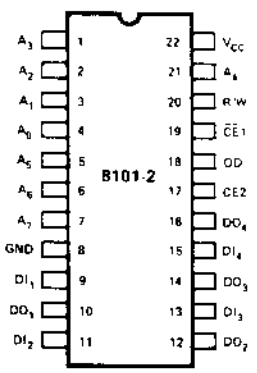
The 8101-2 is designed for memory applications where high performance, low cost, large bit storage, and simple interfacing are important design objectives.

It is directly TTL compatible in all respects: inputs, outputs, and a single +5V supply. Two chip-enables allow easy selection of an individual package when outputs are OR-tied. An output disable is provided so that data inputs and outputs can be tied for common I/O systems. Output disable is then used to eliminate any bidirectional logic.

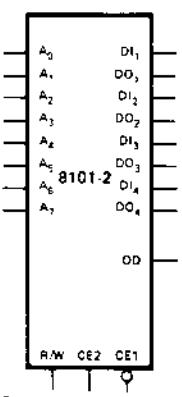
The Intel® 8101-2 is fabricated with N-channel silicon gate technology. This technology allows the design and production of high performance, easy-to-use MOS circuits and provides a higher functional density on a monolithic chip than either conventional MOS technology or P-channel silicon gate technology.

Intel's silicon gate technology also provides excellent protection against contamination. This permits the use of low cost silicone packaging.

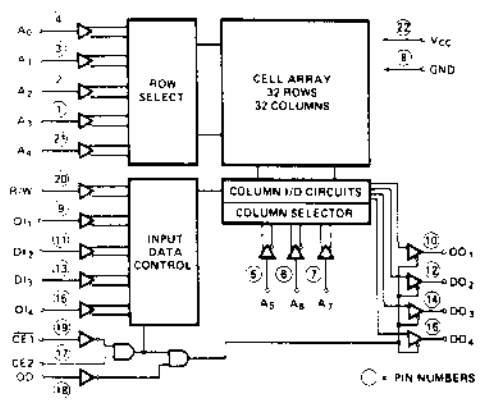
PIN CONFIGURATION



LOGIC SYMBOL



BLOCK DIAGRAM



PIN NAMES

D_{IN}	DATA INPUT	OD	OUTPUT DISABLE
$A_0 - A_7$	ADDRESS INPUTS	D_{OUT}	DATA OUTPUT
R/W	READ/WRITE INPUT	V_{CC}	POWER (+5V)
CE1 CE2	CHIP ENABLE		

Absolute Maximum Ratings*

Ambient Temperature Under Bias . . . . . 0°C to 70°C

Storage Temperature . . . . . -65°C to +150°C

Voltage On Any Pin
With Respect to Ground . . . . . -0.5V to +7V

Power Dissipation . . . . . 1 Watt

*COMMENT:

Stresses above those listed under "Absolute Maximum Rating" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or at any other condition above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

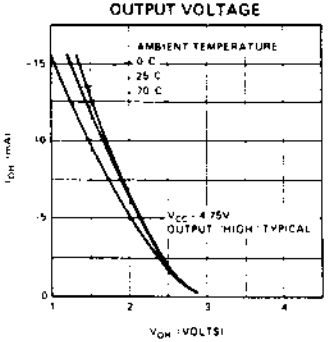
D.C. and Operating Characteristics

T_A = 0°C to 70°C, V_{CC} = 5V ±5% unless otherwise specified.

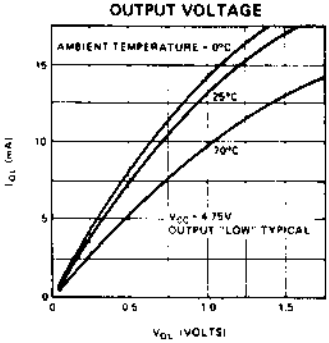
Symbol	Parameter	Min.	Typ.[1]	Max.	Unit	Test Conditions
I_{LI}	Input Current			10	μA	V_{IN} = 0 to 5.25V
I_{LOH}	I/O Leakage Current[2]			15	μA	$\overline{CE}$ = 2.2V, V_{OUT} = 4.0V
I_{LOL}	I/O Leakage Current[2]			-50	μA	$\overline{CE}$ = 2.2V, V_{OUT} = 0.45V
I_{CC1}	Power Supply Current		30	60	mA	V_{IN} = 5.25V, I_O = 0mA T_A = 25°C
I_{CC2}	Power Supply Current			70	mA	V_{IN} = 5.25V, I_O = 0mA T_A = 0°C
V_{IL}	Input "Low" Voltage	-0.5		+0.65	V	
V_{IH}	Input "High" Voltage	2.2		V_{CC}	V	
V_{OL}	Output "Low" Voltage			+0.45	V	I_{OL} = 2.0mA
V_{OH}	Output "High" Voltage	2.2			V	I_{OH} = -150 μA

NOTE: 1. Typical values are for T_A = 25°C and nominal supply voltage.
2. Input and Output tied together.

OUTPUT SOURCE CURRENT VS. OUTPUT VOLTAGE



OUTPUT SINK CURRENT VS. OUTPUT VOLTAGE



A.C. Characteristics

READ CYCLE $T_A = 0°C$ to $70°C$, $V_{CC} = 5V \pm 5\%$, unless otherwise specified.

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
t_{RCY}	Read Cycle	850			ns	(See below)
t_A	Access Time			850	ns	
t_{CO}	Chip Enable To Output			650	ns	
t_{OD}	Output Disable To Output			550	ns	
t_{DF} [1]	Data Output to High Z State	0		200	ns	
t_{OH}	Previous Data Read Valid after change of Address	0			ns	

WRITE CYCLE

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
t_{WCY}	Write Cycle	850			ns	(See below)
t_{AW}	Write Delay	150			ns	
t_{CW}	Chip Enable To Write	750			ns	
t_{DW}	Data Setup	500			ns	
t_{DH}	Data Hold	100			ns	
t_{WP}	Write Pulse	630			ns	
t_{WR}	Write Recovery	50			ns	

A. C. CONDITIONS OF TEST

Input Pulse Levels: +0.65 Volt to 2.2 Volt

Input Pulse Rise and Fall Times: 20nsec

Timing Measurement Reference Level: 1.5 Volt

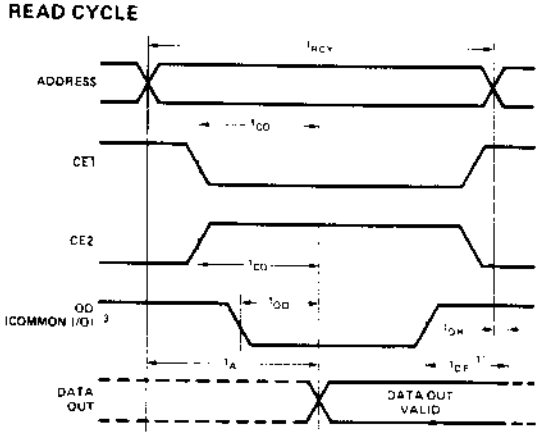
Output Load: 1 TTL Gate and C_L = 100pF

Capacitance $T_A = 25°C$, f = 1MHz

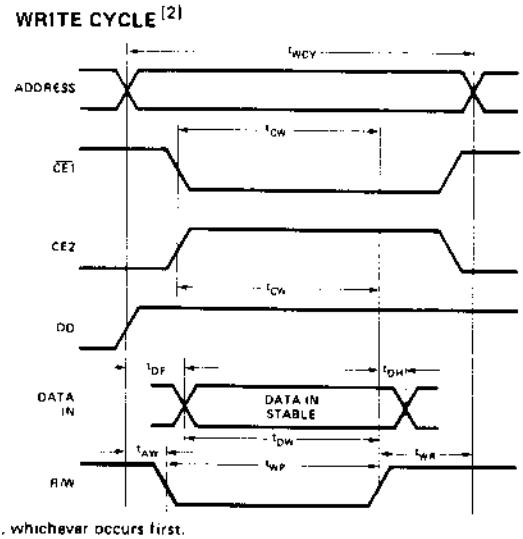
Symbol	Test	Limits (pF)	
		Typ.	Max.
C_{IN}	Input Capacitance (All Input Pins) $V_{IN} = 0V$	4	8
C_{OUT}	Output Capacitance $V_{OUT} = 0V$	8	12

Waveforms

READ CYCLE



WRITE CYCLE [2]



NOTES: 1. t_{DF} is with respect to the trailing edge of $\overline{CE1}$, CE2, or OD, whichever occurs first.
2. During the write cycle, OD is a logical 1 for common I/O and "don't care" for separate I/O operation.
3. OD should be tied low for separate I/O operation.

1024 BIT (256 x 4) STATIC MOS RAM WITH COMMON I/O AND OUTPUT DISABLE

- **Organization 256 Words by 4 Bits**
- **Access Time — 850 nsec Max.**
- **Common Data Input and Output**
- **Single +5V Supply Voltage**
- **Directly TTL Compatible — All Inputs and Output**
- **Static MOS — No Clocks or Refreshing Required**
- **Simple Memory Expansion — Chip Enable Input**
- **Fully Decoded — On Chip Address Decode**
- **Inputs Protected — All Inputs Have Protection Against Static Charge**
- **Low Cost Packaging — 18 Pin Plastic Dual-In-Line Configuration**
- **Low Power — Typically 150 mW**
- **Three-State Output — OR-Tie Capability**

The Intel®8111-2 is a 256 word by 4 bit static random access memory element using normally off N-channel MOS devices integrated on a monolithic array. It uses fully DC stable (static) circuitry and therefore requires no clocks or refreshing to operate. The data is read out nondestructively and has the same polarity as the input data. Common input/output pins are provided.

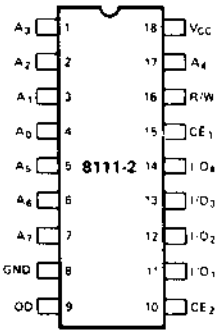
The 8111-2 is designed for memory applications in small systems where high performance, low cost, large bit storage, and simple interfacing are important design objectives.

It is directly TTL compatible in all respects: inputs, outputs, and a single +5V supply. Separate chip enable ($\overline{CE}$) leads allow easy selection of an individual package when outputs are OR-tied.

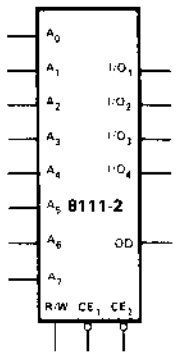
The Intel®8111-2 is fabricated with N-channel silicon gate technology. This technology allows the design and production of high performance, easy-to-use MOS circuits and provides a higher functional density on a monolithic chip than either conventional MOS technology or P-channel silicon gate technology.

Intel's silicon gate technology also provides excellent protection against contamination. This permits the use of low cost silicone packaging.

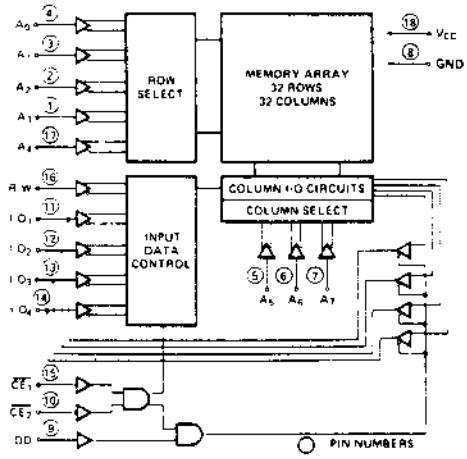
PIN CONFIGURATION



LOGIC SYMBOL



BLOCK DIAGRAM



PIN NAMES

A_0-A_7	ADDRESS INPUTS
OD	OUTPUT DISABLE
R/W	READ/WRITE INPUT
$\overline{CE}_1$	CHIP ENABLE 1
$\overline{CE}_2$	CHIP ENABLE 2
I/O_1-I/O_4	DATA INPUT/OUTPUT

Absolute Maximum Ratings*

Ambient Temperature Under Bias . . . . . 0°C to 70°C

Storage Temperature . . . . . -65°C to +150°C

Voltage On Any Pin
With Respect to Ground . . . . . -0.5V to +7V

Power Dissipation . . . . . 1 Watt

*COMMENT:

Stresses above those listed under "Absolute Maximum Rating" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or at any other condition above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

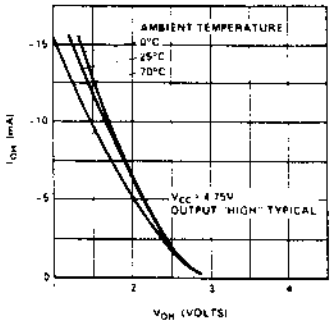
D.C. and Operating Characteristics

T_A = 0°C to 70°C, V_{CC} = 5V ±5% , unless otherwise specified.

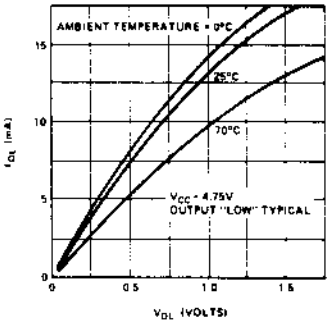
Symbol	Parameter	Min.	Typ.[1]	Max.	Unit	Test Conditions
I_{LI}	Input Load Current			10	μA	V_{IN} = 0 to 5.25V
I_{LOH}	I/O Leakage Current			15	μA	$\overline{CE}$ = 2.2V, $V_{I/O}$ = 4.0V
I_{LOL}	I/O Leakage Current			-50	μA	$\overline{CE}$ = 2.2V, $V_{I/O}$ = 0.45V
I_{CC1}	Power Supply Current		30	60	mA	V_{IN} = 5.25V $I_{I/O}$ = 0mA, T_A = 25°C
I_{CC2}	Power Supply Current			70	mA	V_{IN} = 5.25V $I_{I/O}$ = 0mA, T_A = 0°C
V_{IL}	Input Low Voltage	-0.5		+0.65	V	
V_{IH}	Input High Voltage	2.2		V_{CC}	V	
V_{OL}	Output Low Voltage			0.45	V	I_{OL} = 2.0mA
V_{OH}	Output High Voltage	2.2			V	I_{OH} = -150 μA

NOTES. 1. Typical values are for T_A = 25°C and nominal supply voltage.

OUTPUT SOURCE CURRENT VS. OUTPUT VOLTAGE



OUTPUT SINK CURRENT VS. OUTPUT VOLTAGE



A.C. Characteristics

READ CYCLE $T_A = 0°C$ to $70°C$, $V_{CC} = 5V \pm 5\%$, unless otherwise specified.

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
t_{RCY}	Read Cycle	850			ns	(See below)
t_A	Access Time			850	ns	
t_{CO}	Chip Enable To Output			650	ns	
t_{OD}	Output Disable To Output			550	ns	
t_{DF} [1]	Data Output to High Z State	0		200	ns	
t_{OH}	Previous Data Read Valid after change of Address	0			ns	

WRITE CYCLE

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
t_{WCY}	Write Cycle	850			ns	(See below)
t_{AW}	Write Delay	150			ns	
t_{CW}	Chip Enable To Write	750			ns	
t_{DW}	Data Setup	500			ns	
t_{DH}	Data Hold	100			ns	
t_{WP}	Write Pulse	630			ns	
t_{WR}	Write Recovery	50			ns	

A. C. CONDITIONS OF TEST

Input Pulse Levels: +0.65 Volt to 2.2 Volt

Input Pulse Rise and Fall Times: 20nsec

Timing Measurement Reference Level: 1.5 Volt

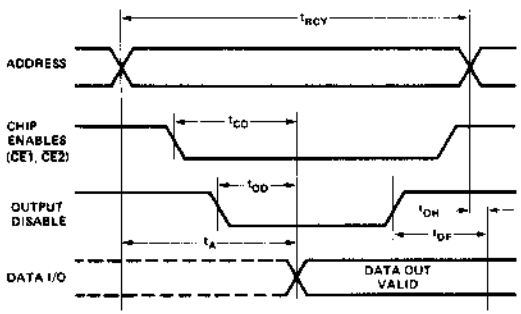
Output Load: 1 TTL Gate and $C_L = 100pF$

Capacitance $T_A = 25°C$, f = 1 MHz

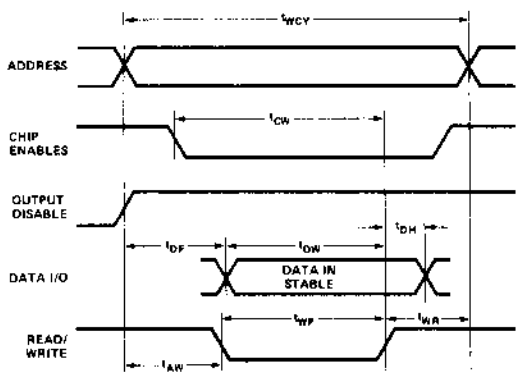
Symbol	Test	Limits (pF)	
		Typ.	Max.
C_{IN}	Input Capacitance (All Input Pins) $V_{IN} = 0V$	4	8
C_{OUT}	Output Capacitance $V_{OUT} = 0V$	10	15

Waveforms

READ CYCLE



WRITE CYCLE



NOTE: 1. t_{DF} is with respect to the trailing edge of $\overline{CE1}$, $\overline{CE2}$, or OD, whichever occurs first.